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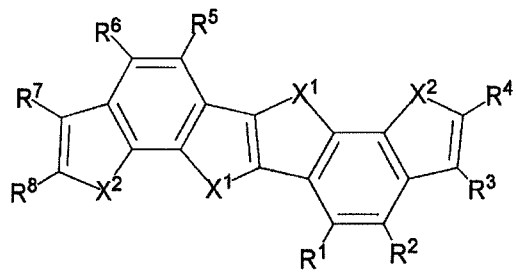
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(54) **ORGANIC TRANSISTOR, COMPOUND, ORGANIC SEMICONDUCTOR MATERIAL FOR NON-LIGHT-EMITTING ORGANIC SEMICONDUCTOR DEVICES, MATERIAL FOR ORGANIC TRANSISTORS, COATING SOLUTION FOR NON-LIGHT-EMITTING ORGANIC SEMICONDUCTOR DEVICES, AND ORGANIC SEMICONDUCTOR FILM FOR NON-LIGHT-EMITTING ORGANIC SEMICONDUCTOR DEVICES**

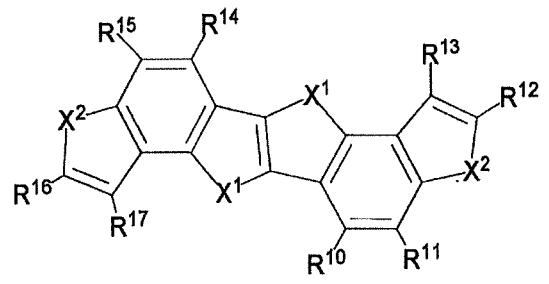
(57) Provided are an organic transistor having high carrier mobility that contains a compound represented by Formula (1-1) or (1-2) in a semiconductor active layer; a compound; an organic semiconductor material for a non-light-emitting organic semiconductor device; a material for an organic transistor; a coating solution for a non-light-emitting organic semiconductor device; and an organic semiconductor film for a non-light-emitting organic semiconductor device (X¹ represents S, O, Se, or NR⁹; X² represents S, O, or Se; each of R¹ to R⁹ represents a hydrogen atom or a substituent; at least one of R¹, R², R³, R⁴, R⁵, R⁶, R⁷, R⁸, and R⁹ represents -L-R; each of R⁹ to R¹⁷ represents a hydrogen atom or a substituent; at least one of R⁹, R¹⁰, R¹¹, R¹², R¹³, R¹⁴, R¹⁵, R¹⁶, and R¹⁷ represents -L-R; L represents a specific divalent linking group; and R represents an alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group, a siloxane group, an oligosiloxane group, or a trialkylsilyl group).

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Formula (1-1)



Formula (1-2)



Description**BACKGROUND OF THE INVENTION**

1. Field of the Invention

[0001] The present invention relates to an organic transistor, an organic semiconductor film, an organic semiconductor material, and the like. Specifically, the present invention relates to a compound having a skeletal structure of condensed rings, an organic transistor containing the compound, an organic semiconductor material for a non-light-emitting organic semiconductor device that contains the compound, a material for an organic transistor that contains the compound, a coating solution for a non-light-emitting organic semiconductor device that contains the compound, an organic semiconductor film for a non-light-emitting organic semiconductor device that contains the compound, and a compound which is an intermediate for synthesizing the aforementioned compound.

2. Description of the Related Art

[0002] The devices using organic semiconductor materials are drawing great attention because they are expected to be superior in various aspects to the devices using inorganic semiconductor materials of the related art such as silicon. Examples of the devices using organic semiconductor materials include a photoelectric conversion element such as an organic solar cell or a solid-state imaging element using organic semiconductor materials as photoelectric conversion materials, an organic transistor (referred to as an organic thin-film transistor in some cases) having non-light-emitting properties (in the present specification, "non-light-emitting" refers to properties by which a luminous efficiency of equal to or less than 1 m/W is obtained in a case where electric currents are applied to a device at a current density of 0.1 mW/cm² at room temperature in the atmosphere; non-light-emitting organic semiconductor devices mean organic semiconductor devices excluding light-emitting organic semiconductor devices such as organic electroluminescence elements), and the like. The devices using organic semiconductor materials are likely to make it possible to prepare large area elements at lower temperature and lower costs compared to the devices using inorganic semiconductor materials. Furthermore, the characteristics of the materials can be easily changed by varying the molecular structure thereof. Therefore, the materials show a wide variation and can realize functions or elements that cannot be obtained by inorganic semiconductor materials.

[0003] For example, WO2013/078407A discloses the use of a compound, which has a pyrrole ring on both terminals or one terminal, as an organic transistor.

[0004] Furthermore, US2008/0142792A1 discloses the use of a heteroacene compound consisting of 6 rings as an organic transistor.

SUMMARY OF THE INVENTION

[0005] Under the circumstances described above, the inventors of the present invention conducted investigation regarding the use of the compounds described in WO2013/078407A and US2008/0142792A1 in a semiconductor active layer of an organic transistor. As a result, the inventors found that the carrier mobility is low in most cases.

[0006] Through the investigation performed by the inventors of the present invention, it was confirmed that in the compounds disclosed in WO2013/078407A and US2008/0142792A1, overlapping of HOMO does not sufficiently occur, and accordingly, only a crystal structure that is undesirable as a transistor material is obtained, and thus the carrier mobility is lowered.

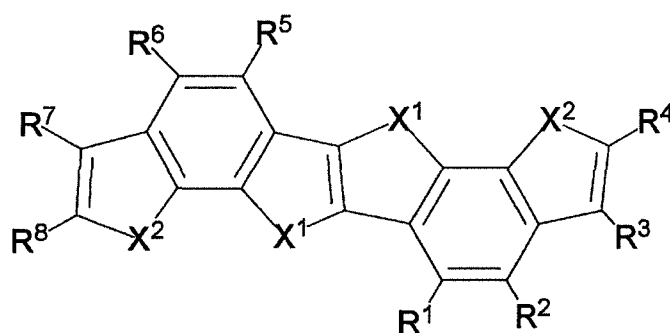
[0007] Therefore, in order to solve the above problems of the related art, the inventors of the present invention continued investigation. Objects of the present invention are to provide an organic transistor having high carrier mobility and to provide a compound which makes it possible to obtain an organic transistor having high carrier mobility by being used in a semiconductor active layer.

[0008] As a result of conducting thorough investigation for achieving the above objects, the inventors obtained knowledge that by condensing 2 heterocyclic rings with 2 thiophene rings, furan rings, or selenophene rings in specific positions, and substituting the resulting compound with a group represented by Formula (W), overlapping of HOMO occurs, the crystallinity is improved, and an organic transistor having high carrier mobility can be obtained. Based on the knowledge, the inventors accomplished the present invention.

[0009] The present invention as specific means for achieving the aforementioned objects is constituted as below.

[1] An organic transistor comprising a compound represented by the following Formula (1-1) or (1-2) in a semiconductor active layer:

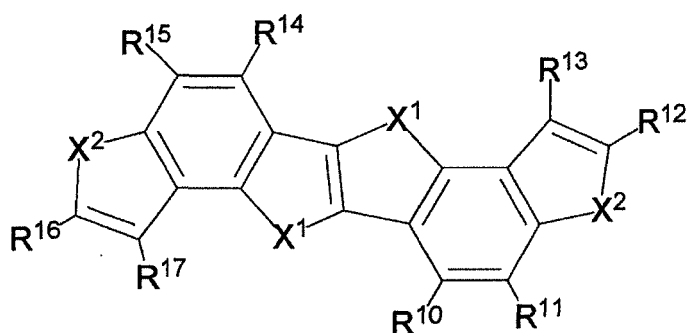
Formula (1-1)



in Formula (1-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R⁹ independently represents a hydrogen atom or a substituent, and at least one of R¹, R², R³,
 R⁴, R⁵, R⁶, R⁷, R⁸, or R⁹ is a substituent represented by the following Formula (W);

Formula (1-2)



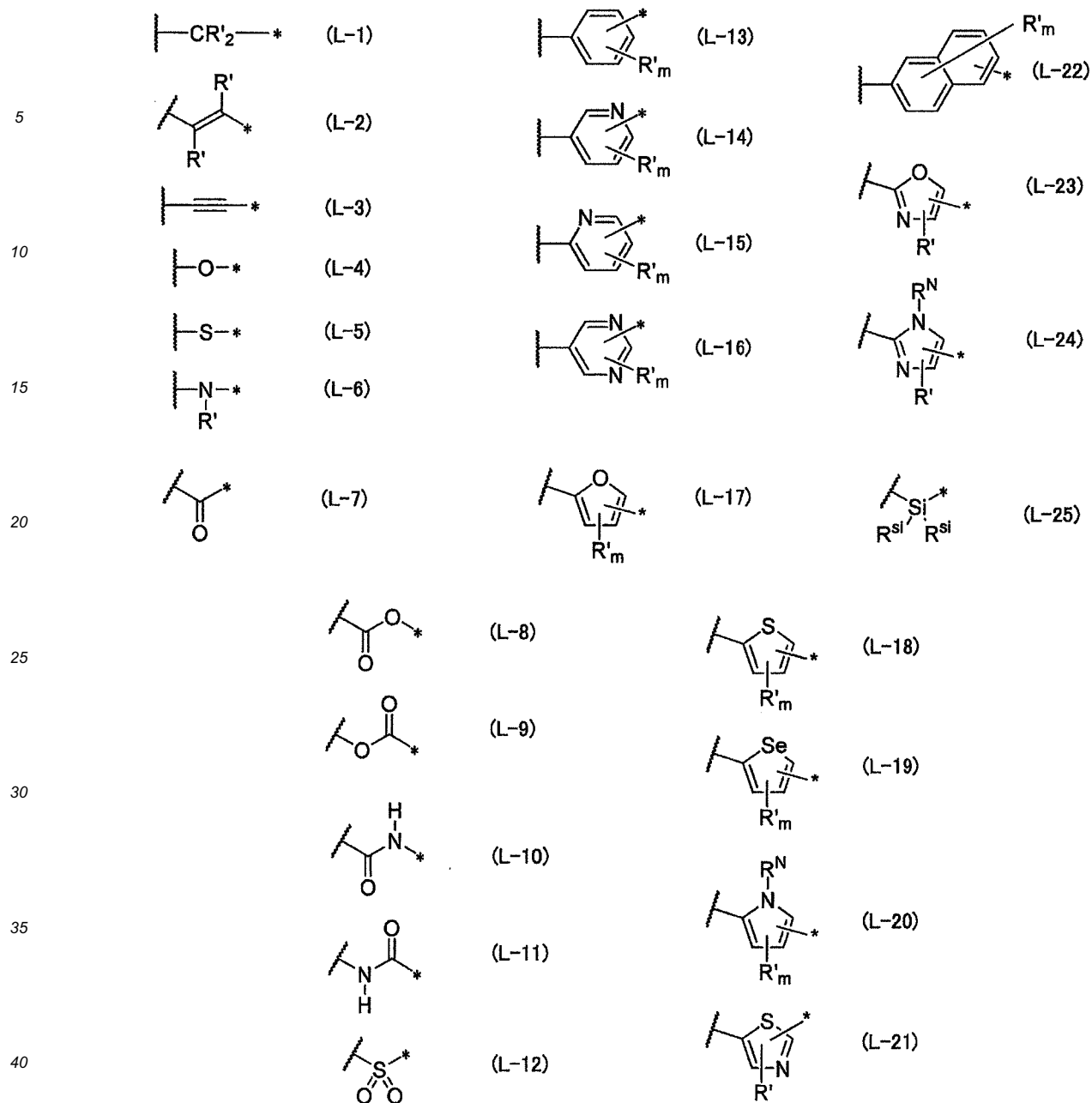
in Formula (1-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R⁹ to R¹⁷ independently represents a hydrogen atom or a substituent, and at least one of R⁹, R¹⁰, R¹¹,
 R¹², R¹³, R¹⁴, R¹⁵, R¹⁶, or R¹⁷ is a substituent represented by the following Formula (W);

-L-R Formula (W)

in Formula (W), L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and

R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

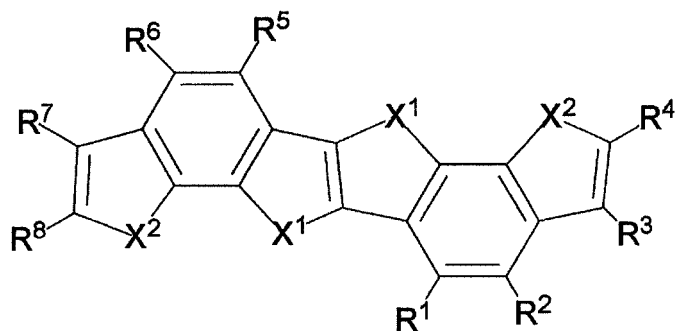


in Formulae (L-1) to (L-25),

the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
 m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6,
 each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent,
 R^N represents a hydrogen atom or a substituent, and
 each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[2] The organic transistor described in [1], in which the compound represented by Formula (1-1) is preferably a compound represented by the following Formula (1-1A):

Formula (1-1A)



in Formula (1-1A),

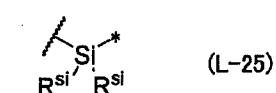
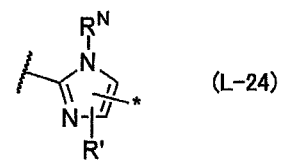
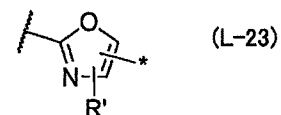
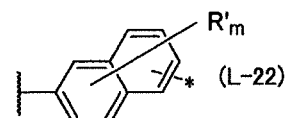
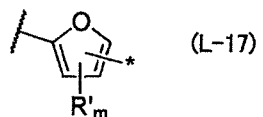
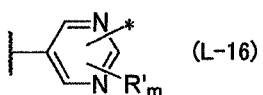
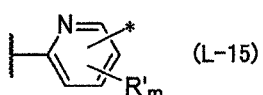
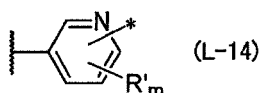
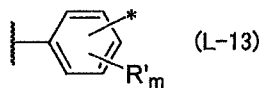
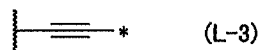
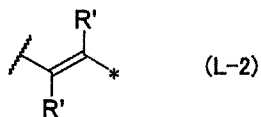
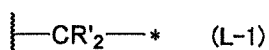
each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R⁹ independently represents a hydrogen atom or a substituent, and at least one of R³, R⁴, R⁷, or R⁸ is a substituent represented by the following Formula (W):

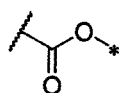
-L-R Formula (W)

in Formula (W),

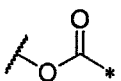
L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and

R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

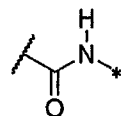




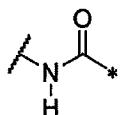
(L-8)



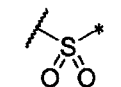
(L-9)



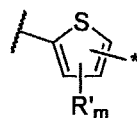
(L-10)



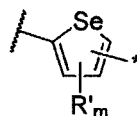
(L-11)



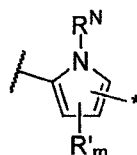
(L-12)



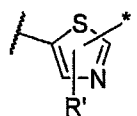
(L-18)



(L-19)



(L-20)



(L-21)

in Formulae (L-1) to (L-25),

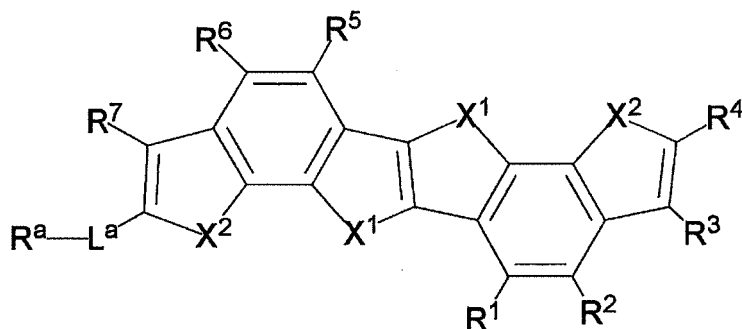
the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6,
each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent,

R^N represents a hydrogen atom or a substituent, and

each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[3] The organic transistor described in [1] or [2], in which the compound represented by Formula (1-1) or (1-1A) is preferably a compound represented by the following Formula (2-1-1) or (2-1-2), and the compound represented by Formula (1-2) is preferably a compound represented by the following Formula (2-2-1) or (2-2-2):

Formula (2-1-1)



in Formula (2-1-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,

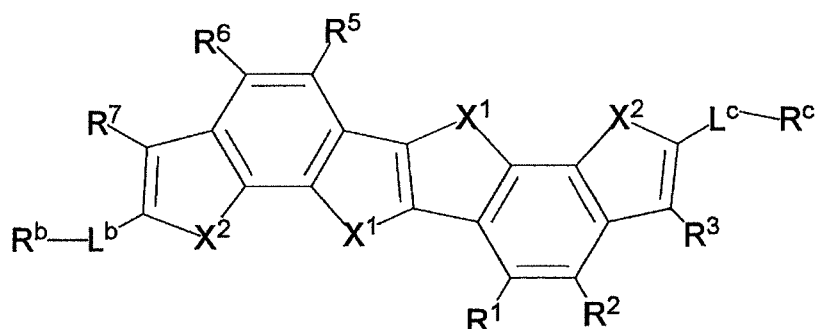
each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,

each of R¹ to R⁷ and R⁹ independently represents a hydrogen atom or a substituent, R⁴ is not a group represented by -L^a-R^a,

L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and

R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

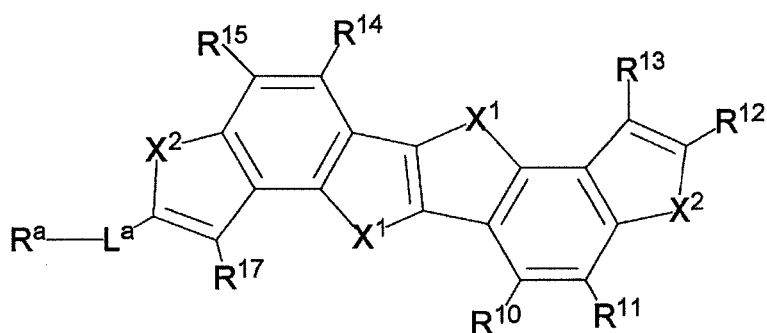
Formula (2-1-2)



in Formula (2-1-2),

each X^1 independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR^9 ,
 each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R^1 to R^3 , R^5 to R^7 , and R^9 independently represents a hydrogen atom or a substituent,
 each of L^b and L^c independently represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
 each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

Formula (2-2-1)

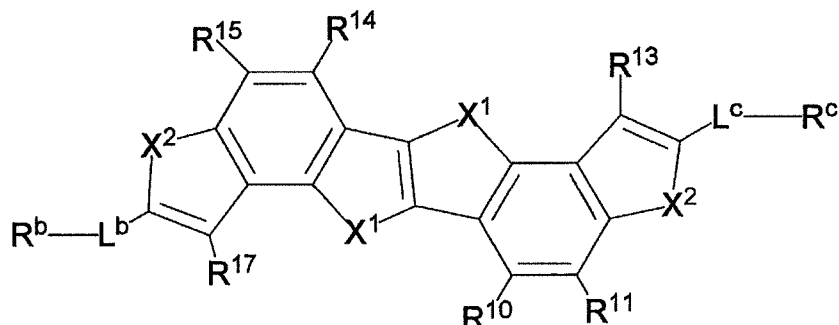


in Formula (2-2-1),

each X^1 independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR^9 ,
 each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R^{10} , R^{12} to R^{15} , and R^{17} independently represents a hydrogen atom or a substituent, R^{12} is not a group represented by $-L^a-R^a$,
 L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
 R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an

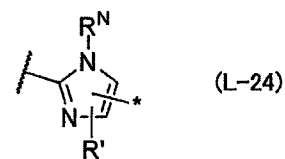
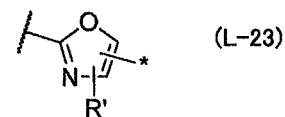
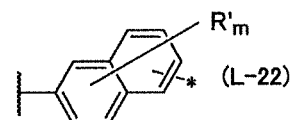
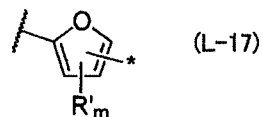
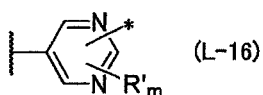
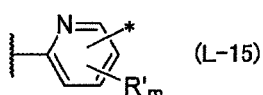
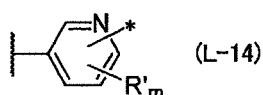
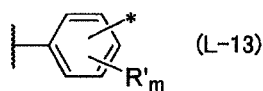
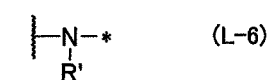
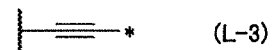
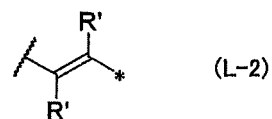
oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

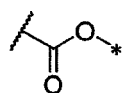
Formula (2-2-2)



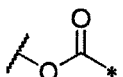
in Formula (2-2-2),

each X^1 independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR^9
 each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R^{10} , R^{11} , R^{13} to R^{15} , and R^{17} independently represents a hydrogen atom or a substituent,
 each of L^b and L^c independently represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
 each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

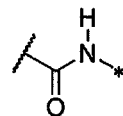




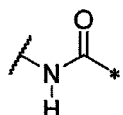
(L-8)



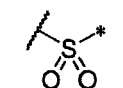
(L-9)



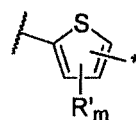
(L-10)



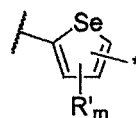
(L-11)



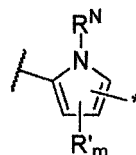
(L-12)



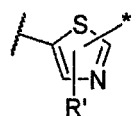
(L-18)



(L-19)



(L-20)



(L-21)

in Formulae (L-1) to (L-25),

the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6,
each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent,

R^N represents a hydrogen atom or a substituent, and

each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[4] The organic transistor described in any one of [1] to [3], in which in Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of L, L^a, L^b, and L^c is preferably independently a divalent linking group represented by any of Formulae (L-1) to (L-5), (L-13), (L-17), and (L-18) or a divalent linking group in which two or more divalent linking groups represented by any of Formulae (L-1) to (L-5), (L-13), (L-17), and (L-18) are bonded to each other.

[5] The organic transistor described in any one of [1] to [4], in which in Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of L, L^a, L^b, and L^c is preferably independently a divalent linking group represented by any of Formulae (L-1), (L-3), (L-13), and (L-18) or a divalent linking group in which a divalent linking group represented by any one of Formulae (L-3), (L-13), and (L-18) is bonded to a divalent linking group represented by Formula (L-1).

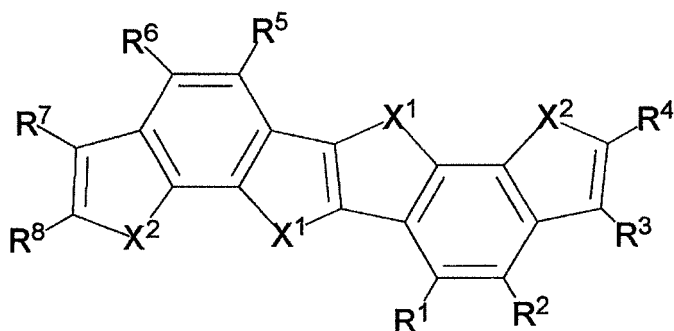
[6] The organic transistor described in any one of [1] to [5], in which in Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of R, R^a, R^b, and R^c is preferably independently a substituted or unsubstituted alkyl group.

[7] The organic transistor described in any one of [1] to [6], in which in Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of R, R^a, R^b, and R^c is preferably independently a linear alkyl group.

[8] The organic transistor described in any one of [1] to [7], in which in Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), both of X¹ and X² are preferably a sulfur atom.

[9] A compound represented by the following Formula (1-1A) or (1-2):

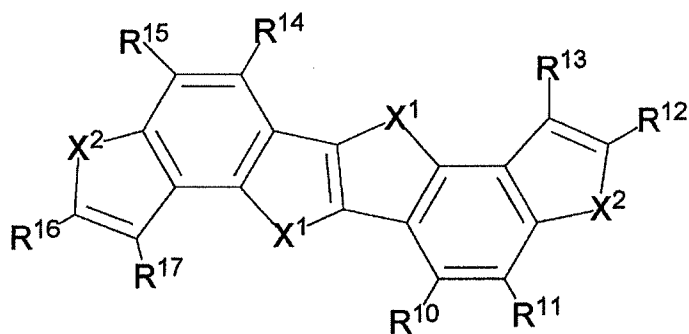
Formula (1-1A)



in Formula (1-1A),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R⁹ independently represents a hydrogen atom or a substituent, and at least one of R³, R⁴, R⁷, or R⁸ is a substituent represented by the following Formula (W);

Formula (1-2)



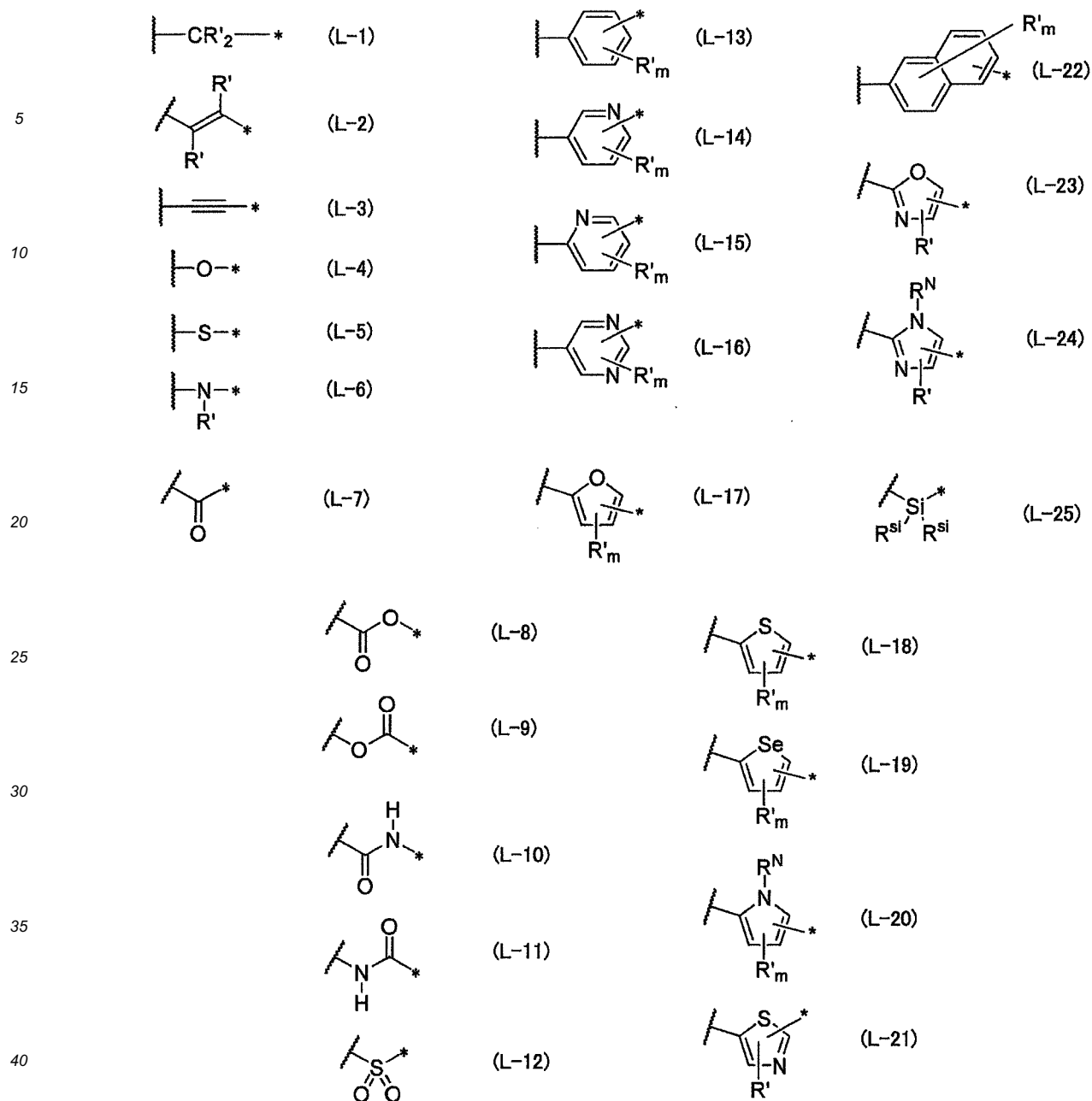
in Formula (1-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R⁹ to R¹⁷ independently represents a hydrogen atom or a substituent, and at least one of R⁹, R¹⁰, R¹¹, R¹², R¹³, R¹⁴, R¹⁵, R¹⁶, or R¹⁷ is a substituent represented by the following Formula (W);

-L-R Formula (W)

in Formula (W), L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and

R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group.



In Formulae (L-1) to (L-25),

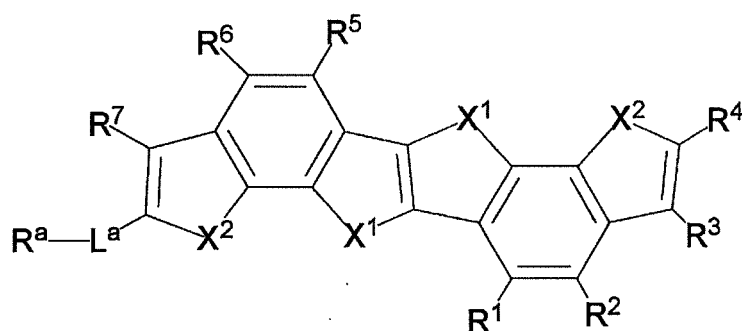
the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
 m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6,
 each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent,

R^N represents a hydrogen atom or a substituent, and

each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[10] The compound described in [9], in which the compound represented by Formula (1-1A) or (1-2) is preferably a compound represented by any of the following Formulae (2-1-1) to (2-2-2):

Formula (2-1-1)



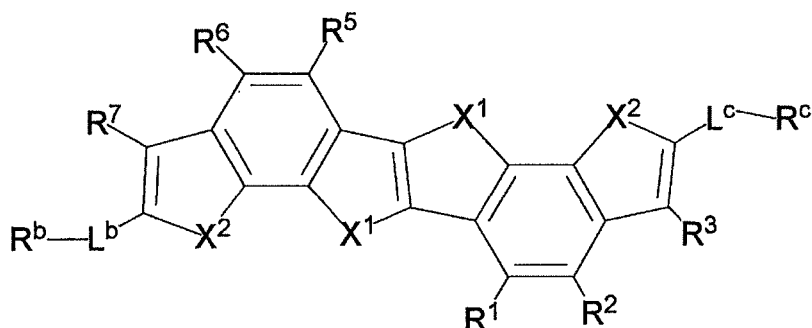
in Formula (2-1-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R⁷ and R⁹ independently represents a hydrogen atom or a substituent, R⁴ is not a group represented by -L^a-R^a,

L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and

R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

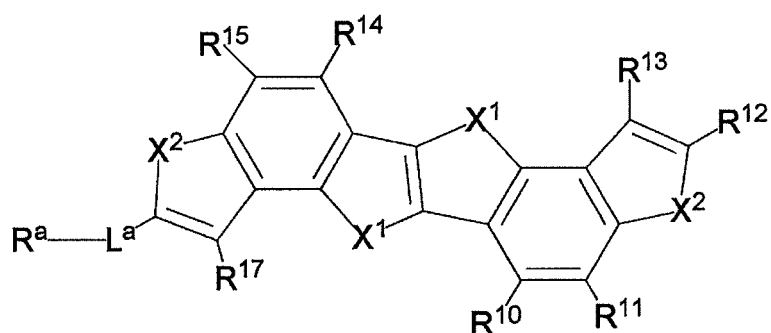
Formula (2-1-2)



in Formula (2-1-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R³, R⁵ to R⁷, and R⁹ independently represents a hydrogen atom or a substituent,
 each of L^b and L^c independently represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
 each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

Formula (2-2-1)



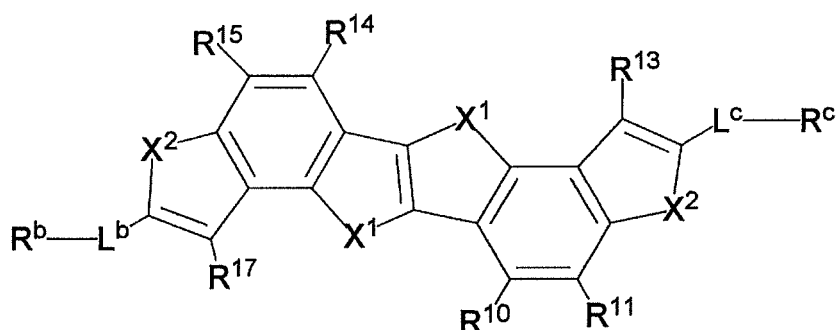
in Formula (2-2-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹⁰, R¹² to R¹⁵, and R¹⁷ independently represents a hydrogen atom or a substituent, R¹² is not a group
 represented by -L^a-R^a,

L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent
 linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1)
 to (L-25) are bonded to each other, and

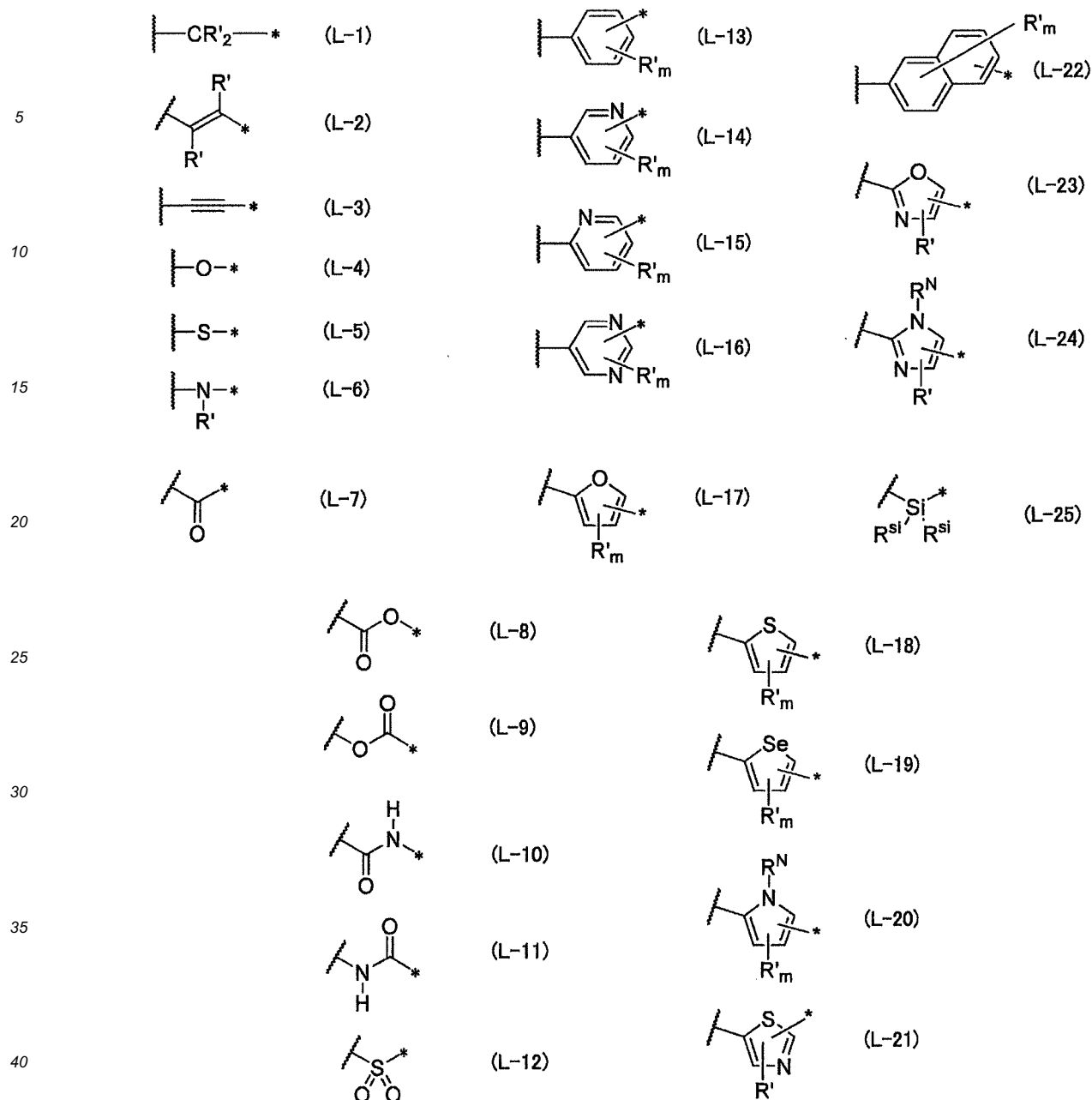
R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an
 oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal
 to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted
 or unsubstituted trialkylsilyl group;

Formula (2-2-2)



in Formula (2-2-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹⁰, R¹¹, R¹³ to R¹⁵, and R¹⁷ independently represents a hydrogen atom or a substituent,
 each of L^b and L^c independently represents a divalent linking group represented by any of the following Formulae
 (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the
 following Formulae (L-1) to (L-25) are bonded to each other, and
 each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl
 group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of
 an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more
 silicon atoms, or a substituted or unsubstituted trialkylsilyl group;



in Formulae (L-1) to (L-25),

the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
 m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6,
 each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent,
 R^N represents a hydrogen atom or a substituent, and
 each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[11] The compound described in [9] or [10], in which in Formulae (1-1), (1-2), (1-A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of L, L^a, L^b, and L^c is preferably independently a divalent linking group represented by any of Formulae (L-1) to (L-5), (L-13), (L-17), and (L-18) or a divalent linking group in which two or more divalent linking groups represented by any of Formulae (L-1) to (L-5), (L-13), (L-17), and (L-18) are bonded to each other.

[12] The compound described in any one of [9] to [11], in which in Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of L, L^a, L^b, and L^c is preferably independently a divalent linking group represented by

any of Formulae (L-1), (L-3), (L-13), and (L-18) or a divalent linking group in which a divalent linking group represented by any of Formulae (L-3), (L-13), and (L-18) is bonded to a divalent linking group represented by Formula (L-1).

[13] The compound described in any one of [9] to [12], in which in Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of R, R^a, R^b, and R^c is preferably independently a substituted or unsubstituted alkyl group.

[14] The compound described in any one of [9] to [13], in which in Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of R, R^a, R^b, and R^c is preferably independently a linear alkyl group.

[15] The compound described in any one of [9] to [14], in which in Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), both of X¹ and X² are preferably a sulfur atom.

[16] An organic semiconductor material for a non-light-emitting organic semiconductor device, comprising the compound represented by Formula (1-1) or (1-2) described in any one of [1] to [8].

[17] A material for an organic transistor, comprising the compound represented by Formula (1-1) or (1-2) described in any one of [1] to [8].

[18] A coating solution for a non-light-emitting organic semiconductor device, comprising the compound represented by Formula (1-1) or (1-2) described in any one of [1] to [8].

[19] A coating solution for a non-light-emitting organic semiconductor device, comprising the compound represented by Formula (1-1) or (1-2) described in any one of [1] to [8] and a polymer binder.

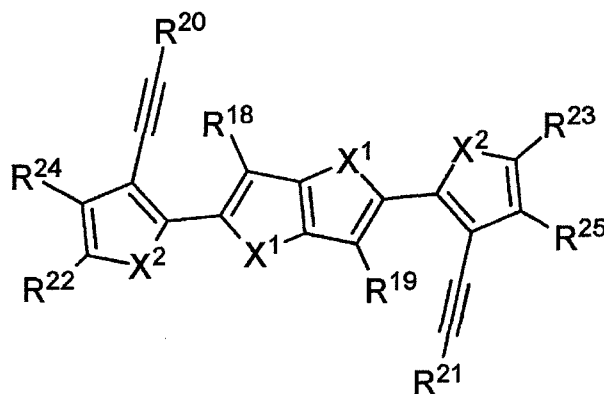
[20] An organic semiconductor film for a non-light-emitting organic semiconductor device, comprising the compound represented by Formula (1-1) or (1-2) described in any one of [1] to [8].

[21] An organic semiconductor film for a non-light-emitting organic semiconductor device, comprising the compound represented by Formula (1-1) or (1-2) described in any one of [1] to [8] and a polymer binder.

[22] The organic semiconductor film for a non-light-emitting organic semiconductor device described in [20] or [21] that is preferably prepared by a solution coating method.

[23] A compound represented by the following Formula (3-1) or (3-2):

Formula (3-1)



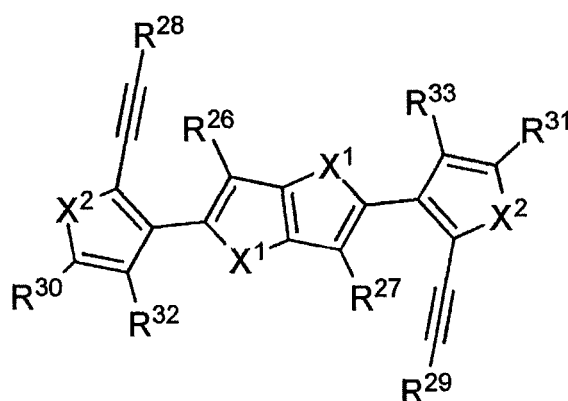
in Formula (3-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,

each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,

each of R⁹ and R¹⁸ to R²⁵ independently represents a hydrogen atom or a substituent, and at least one of R²² or R²³ represents an alkyl group, an alkenyl group, an alkynyl group, a substituted or unsubstituted aryl group, a substituted or unsubstituted heteroaryl group, an alkylcarbonyl group, or a substituted or unsubstituted arylcarbonyl group;

Formula (3-2)



in Formula (3-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R⁹ and R²⁶ to R³³ independently represents a hydrogen atom or a substituent, and at least one of R³⁰
 or R³¹ represents an alkyl group, an alkenyl group, an alkynyl group, a substituted or unsubstituted aryl group,
 a substituted or unsubstituted heteroaryl group, an alkylcarbonyl group, or a substituted or unsubstituted aryl-
 carbonyl group.

[24] The compound described in [23] that is preferably an intermediate compound of the compound represented by
 Formula (1-1) or (1-2) described in any one of [1] to [8].

[0010] According to the present invention, it is possible to provide an organic transistor having high carrier mobility.

BRIEF DESCRIPTION OF THE DRAWINGS

[0011]

Fig. 1 is a schematic view showing a section of an exemplary structure of an organic transistor of the present invention.
 Fig. 2 is a schematic view showing a section of a structure of the organic transistor manufactured as a substrate for
 measuring FET characteristics in examples of the present invention.
 Fig. 3 is a ¹H-NMR chart of a compound g.
 Fig. 4 is a ¹H-NMR chart of a compound 1.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

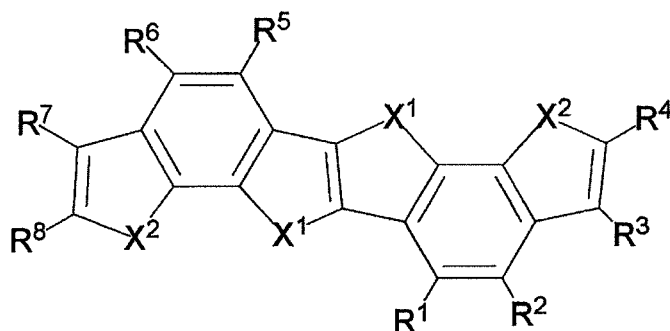
[0012] Hereinafter, the present invention will be specifically described. The constituents described below will be ex-
 plained based on representative embodiments or specific examples in some cases, but the present invention is not
 limited to the embodiments. In the present specification, a range of numerical values described using "to" means a range
 including the numerical values listed before and after "to" as a lower limit and an upper limit respectively.

[0013] In the present invention, unless otherwise specified, a hydrogen atom used in the description of each formula
 represents a hydrogen atom including an isotope (deuterium atom or the like). Furthermore, an atom constituting a
 substituent represents an atom including an isotope thereof.

[Organic transistor]

[0014] An organic transistor of the present invention contains a compound represented by the following Formula (1-1)
 or (1-2) in a semiconductor active layer.

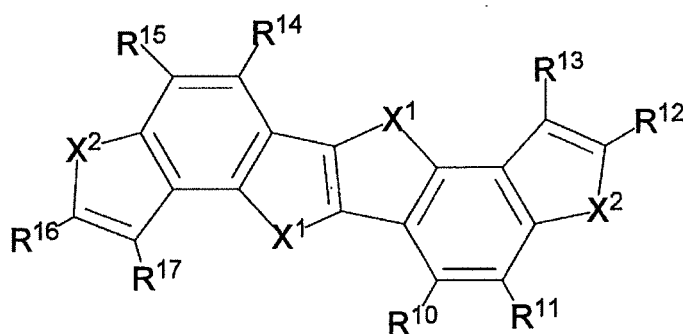
Formula (1-1)



In Formula (1-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R⁹ independently represents a hydrogen atom or a substituent, and at least one of R¹, R², R³, R⁴, R⁵,
 R⁶, R⁷, R⁸, or R⁹ is a substituent represented by the following Formula (W);

Formula (1-2)



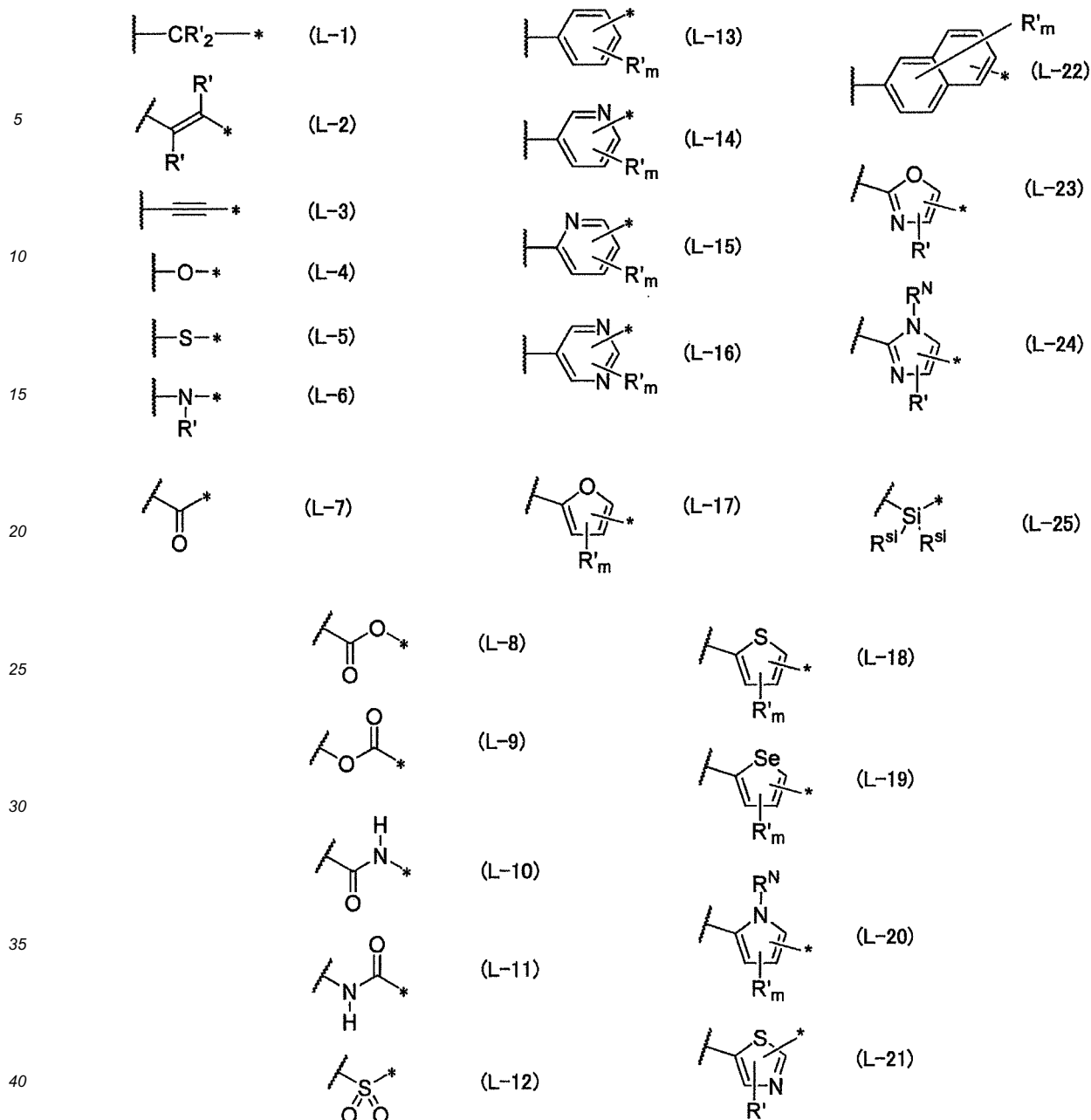
in Formula (1-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R⁹ to R¹⁷ independently represents a hydrogen atom or a substituent, and at least one of R⁹, R¹⁰, R¹¹, R¹²,
 R¹³, R¹⁴, R¹⁵, R¹⁶, or R¹⁷ is a substituent represented by the following Formula (W);

-L-R Formula (W)

in Formula (W), L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25)
 or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae
 (L-1) to (L-25) are bonded to each other, and

R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene
 group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than
 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted
 trialkylsilyl group;



in Formulae (L-1) to (L-25),

the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton, m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6, each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent, R^N represents a hydrogen atom or a substituent, and each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[0015] The compound represented by Formula (1-1) and the compound represented by Formula (1-2) having the structure described above exhibit high solubility in an organic solvent. By containing the compound represented by Formula (1-1) or (1-2) in the semiconductor active layer, the organic transistor of the present invention has high carrier mobility.

[0016] Herein, WO2013/078407A describes an organic semiconductor compound having a polycyclic condensed structure whose structure seems to be similar to that of the compound of the present invention. However, due to the influence of the substituent on N, the intermolecular distance is increased in this compound, and as a result, overlapping

of HOMO does not occur, and high carrier mobility is not obtained.

[0017] Furthermore, the compound described in US2008/0142792A1 differs from the compound of the present invention in terms of the position in which the heterocyclic ring is condensed on the terminal. Therefore, in the compound, the effect resulting from the interaction between heteroatoms is weak, overlapping of HOMO does not occur, and thus high carrier mobility is not obtained.

[0018] In contrast, each of the compounds of the present invention represented by Formulae (1-1) and (1-2) has a heterocyclic ring at the center and is condensed with two thiophene rings, furan rings, or selenophene rings in specific positions on the terminal. As a result, overlapping of HOMO occurs, and the crystallinity is improved. Therefore, by using the compound of the present invention in a semiconductor active layer, an organic transistor having high carrier mobility can be obtained.

[0019] In order to improve the solubility in a general organic solvent, it is effective to introduce a group represented by Formula (W) into the compound. It is preferable that the compound represented by Formula (1-1) or (1-2) exhibits high solubility in an organic solvent.

[0020] Furthermore, It is preferable that the organic transistor of the present invention using the compound represented by Formula (1-1) or (1-2) shows only a slight threshold voltage shift after repeated driving. In order to reduce the threshold voltage shift after repeated driving, HOMO of the organic semiconductor material needs not to be too shallow or too deep. Furthermore, the chemical stability (particularly, resistance against air oxidation and stability against oxidation and reduction) of the organic semiconductor material, the heat stability of the film state, the high film density which makes it difficult for air or moisture to permeate the film, the film quality by which the film has small defectiveness such that charge accumulation does not easily occur, and the like are required. It is considered that because the compound represented by the Formula (1-1) or (1-2) satisfies the aforementioned requirements, the organic transistor shows only a slight threshold voltage shift after repeated driving. That is, in the organic transistor showing only a slight threshold voltage shift after repeated driving, the semiconductor active layer has high chemical stability, high film density, and the like, and thus the organic transistor can effectively function as a transistor over a long period of time.

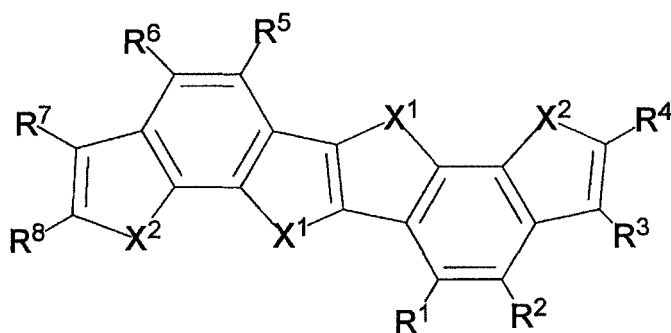
[0021] Being useful as an organic EL element material does not mean being useful as a semiconductor material for an organic transistor, because the characteristics required for the organic compound vary between the organic EL element and the organic transistor. In the organic EL element, charges need to be transported in the film thickness direction (generally, several nanometers to hundreds of nanometers) of a general film. In contrast, in the organic transistor, charges (carriers) need to be transported a long distance between electrodes (generally, several micrometers to hundreds of micrometers) in the film plane direction, and hence extremely high carrier mobility is required. Accordingly, as the semiconductor material for an organic transistor, an organic compound showing highly ordered molecular arrangement and having high crystallinity is required. Furthermore, for the expression of high carrier mobility, the π -conjugate plane thereof is preferably upright against a substrate. On the other hand, for the organic EL element, in order to improve the luminous efficiency, an element having high luminous efficiency and uniformly emitting light in plane is required. Generally, an organic compound having high crystallinity causes luminescence defectiveness such as nonuniform in-plane electric field intensity, nonuniform luminescence, and quenching of luminescence. Therefore, as the material for an organic EL element, those having low crystallinity but having high amorphousness are desirable. Consequently, the use of the organic compound constituting the organic EL element material as an organic semiconductor material does not ensure that excellent transistor characteristics can be obtained.

[0022] Hereinafter, preferred aspects of the compound and the organic transistor of the present invention will be described.

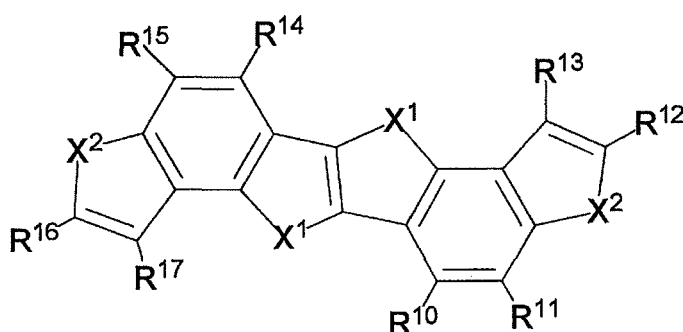
<Compound represented by Formula (1-1) or (1-2)>

[0023] The organic transistor of the present invention contains the compound represented by Formula (1-1) or (1-2) in a semiconductor active layer which will be described later. Among compounds represented by Formula (1-1), a compound represented by Formula (1-1A) which will be described later and a compound represented by Formula (1-2) are novel compounds. The compound represented by Formula (1-1A) and the compound represented by Formula (1-2) are collectively called the compound of the present invention. The compound represented by Formula (1-1) or (1-2), particularly, the compound of the present invention is contained in a semiconductor active layer, which will be described later, in the organic transistor of the present invention. That is, the compound represented by Formula (1-1) or (1-2), particularly, the compound of the present invention can be used as a material for an organic transistor. Among the compound represented by Formula (1-1) and the compound represented by Formula (1-2), the compound represented by Formula (1-1) can be preferably used in a semiconductor active layer of the organic transistor.

Formula (1-1)



Formula (1-2)



[0024] In Formulae (1-1) and (1-2), each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹, and each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom. From the viewpoint of the ease of synthesis, it is preferable that each of X¹ and X² is independently an oxygen atom or a sulfur atom. In contrast, from the viewpoint of improving the carrier mobility, it is preferable that at least one of X¹ or X² is a sulfur atom. X¹ and X² are preferably the same linking group. Both of X¹ and X² are more preferably a sulfur atom.

[0025] R⁹ represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an acyl group, or a group represented by the following Formula (W) which will be described later. R⁹ is preferably a hydrogen atom or an alkyl group, more preferably an alkyl group having 5 to 12 carbon atoms, and particularly preferably an alkyl group having 8 to 10 carbon atoms.

[0026] In a case where R⁹ represents an alkyl group, the alkyl group may be a linear, branched, or cyclic alkyl group. However, from the viewpoint of the overlapping of HOMO, R⁹ is preferably a linear alkyl group.

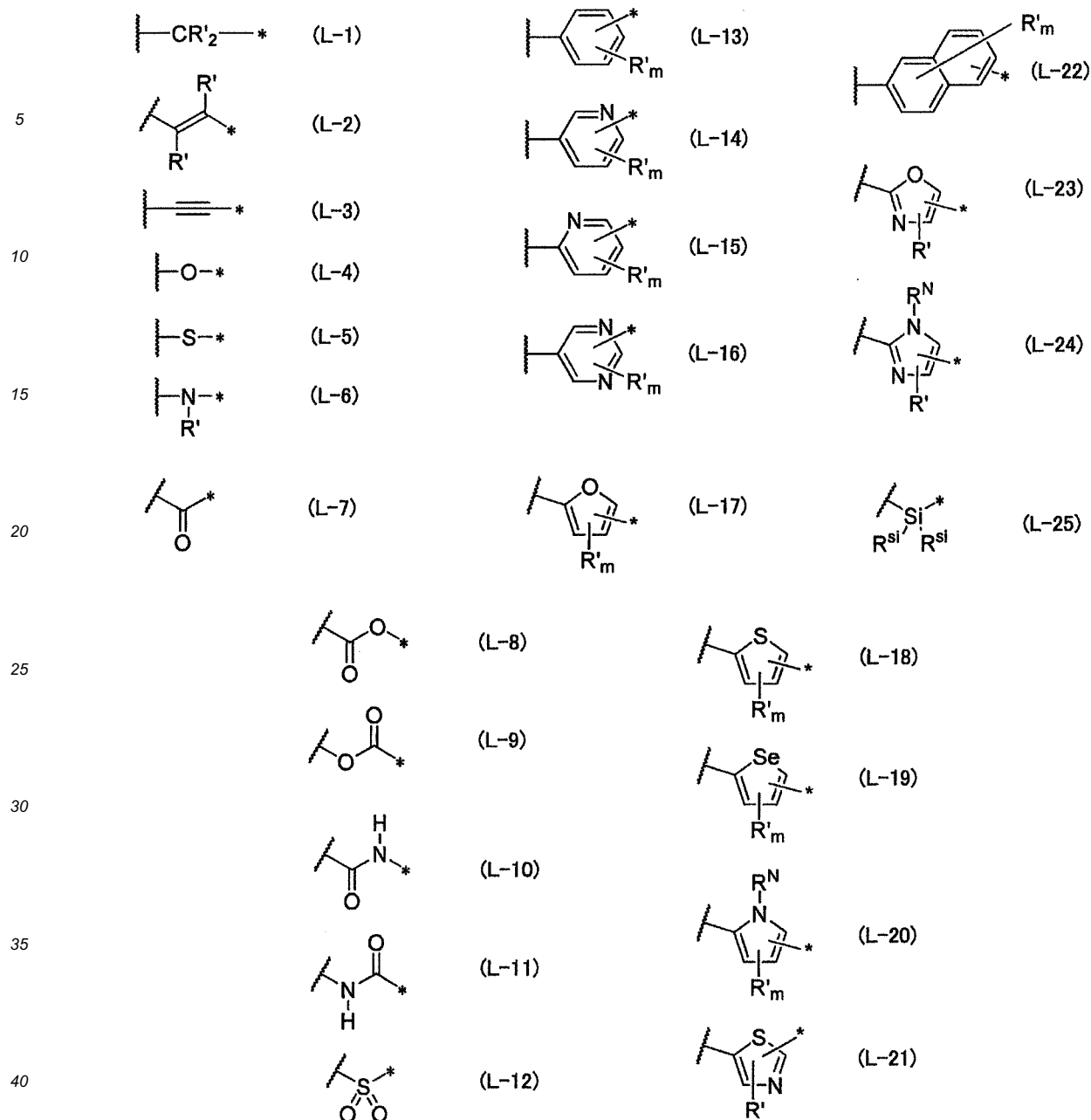
[0027] In Formula (1-1), each of R¹ to R⁹ independently represents a hydrogen atom or a substituent, and at least one of R¹, R², R³, R⁴, R⁵, R⁶, R⁷, R⁸, or R⁹ is a substituent represented by the following Formula (W).

[0028] Furthermore, in Formula (1-2), each of R⁹ to R¹⁷ represents a hydrogen atom or a substituent, and at least one of R⁹, R¹⁰, R¹¹, R¹², R¹³, R¹⁴, R¹⁵, R¹⁶, or R¹⁷ is a substituent represented by the following Formula (W).

-L-R Formula (W)

[0029] In Formula (W), L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and

[0030] R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group:



in Formulae (L-1) to (L-25), the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
 m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20)
 represents 2, m in Formula (L-22) represents 6,
 each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent,
 R^N represents a hydrogen atom or a substituent, and
 each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[0031] Examples of the substituent that each of R¹ to R⁹ in Formula (1-1) and each of R⁹ to R¹⁷ in Formula (1-2) can
 independently represent include a halogen atom, an alkyl group (including an alkyl group having 1 to 40 carbon atoms
 such as a methyl group, an ethyl group, a propyl group, a butyl group, a pentyl group, a hexyl group, a heptyl group, an
 octyl group, a nonyl group, a decyl group, an undecyl group, a dodecyl group, a tridecyl group, a tetradecyl group, or a
 pentadecyl group; here, the alkyl group also includes a 2,6-dimethyloctyl group, a 2-decyltetradecyl group, a 2-hexyl-
 dodecyl group, a 2-ethyloctyl group, a 2-decyltetradecyl group, a 2-butyldodecyl group, a 1-octylnonyl group, a 2-ethyloctyl
 group, a 2-octyltetradecyl group, a 2-ethylhexyl group, a cycloalkyl group, a bicycloalkyl group, a tricycloalkyl group, and
 the like), an alkenyl group (including a 1-pentenyl group, a cycloalkenyl group, a bicycloalkenyl group, and the like), an
 alkynyl group (including a 1-pentylnyl group, a trimethylsilylethynyl group, a triethylsilylethynyl group, a tri-*i*-propylsi-

lylethynyl group, a 2-p-propylphenylethynyl group, and the like), an aryl group (including an aryl group having 6 to 20 carbon atoms such as a phenyl group, a naphthyl group, a p-pentylphenyl group, a 3,4-dipentylphenyl group, a p-heptoxyphenyl group, a 3,4-diheptoxyphenyl group, and the like), a hetero ring group (may be referred to as a heterocyclic group as well, including a 2-hexylfuranyl group and the like), a cyano group, a hydroxyl group, a nitro group, an acyl group (including a hexanoyl group, a benzoyl group, and the like), an alkoxy group (including a butoxy group and the like), an aryloxy group, a silyloxy group, a heterocyclic oxy group, an acyloxy group, a carbamoyloxy group, an amino group (including an anilino group), an acylamino group, an aminocarbonylamino group (including a ureide group), alkoxy- and aryloxy carbonylamino groups, alkyl- and aryl sulfonylamino groups, a mercapto group, alkyl- and arylthio groups (including a methylthio group, an octylthio group, and the like), a heterocyclic thio group, a sulfamoyl group, a sulfo group, alkyl- and aryl sulfmyl groups, alkyl- and aryl sulfonyl groups, alkyloxy- and aryloxy carbonyl groups, a carbamoyl group, aryl- and heterocyclic azo group, an imide group, a phosphino group, a phosphinyl group, a phosphinyloxy group, a phosphinylamino group, a phosphono group, a silyl group (a ditrimethylsiloxy methylbutoxy group), a hydrazino group, a ureide group, a boronic acid group ($-B(OH)_2$), a phosphate group ($-OPO(OH)_2$), a sulfate group ($-OSO_3H$), and other known substituents.

[0032] These substituents may further have the above substituents. In addition, in a case where the compound represented by Formula (1-1) or (1-2) is a polymer compound having a repeating structure, each of R^1 to R^9 in Formula (1-1) and each of R^9 to R^{17} in Formula (1-2) may have a group derived from a polymerizable group.

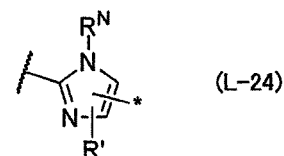
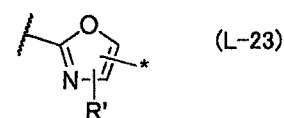
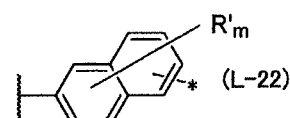
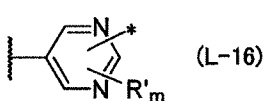
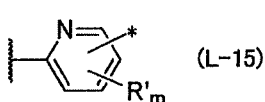
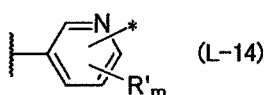
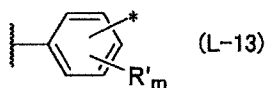
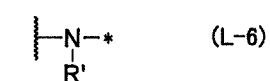
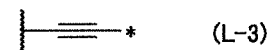
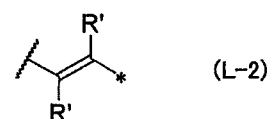
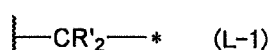
[0033] Among these, as the substituent that each of R^1 to R^9 in Formula (1-1) and each of R^9 to R^{17} in Formula (1-2) can independently represent, an alkyl group, an aryl group, an alkenyl group, an alkynyl group, a heterocyclic group, an alkoxy group, an alkylthio group, and a group represented by Formula (W) which will be described later are preferable; an alkyl group having 1 to 18 carbon atoms, an aryl group having 6 to 20 carbon atoms, an alkenyl group having 2 to 12 carbon atoms, an alkynyl group having 2 to 12 carbon atoms, an alkoxy group having 1 to 11 carbon atoms, a heterocyclic group having 5 to 12 carbon atoms, an alkylthio group having 1 to 12 carbon atoms, and a group represented by Formula (W) which will be described later are more preferable; a group having a linking group chain length, which will be described later, of equal to or less than 3.7 Å and a group represented by Formula (W) which will be described later are particularly preferable; and a group represented by Formula (W) which will be described later is more particularly preferable.

[0034] The group represented by Formula (W) will be described.

-L-R Formula (W)

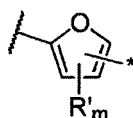
[0035] In Formula (W), L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25), and

[0036] R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group:

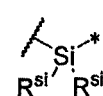




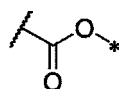
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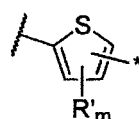
(L-17)



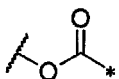
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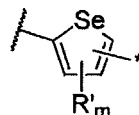
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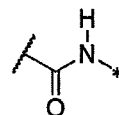
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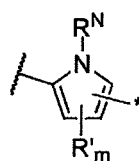
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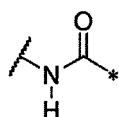
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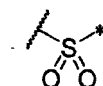
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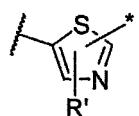
(L-20)



(L-11)



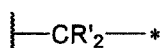
(L-12)



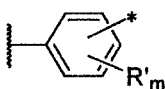
(L-21)

in Formulae (L-1) to (L-25), the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton, m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6, each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent, R^N represents a hydrogen atom or a substituent, and each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

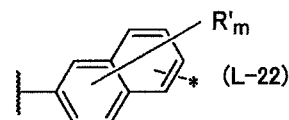
[0037] In Formula (W), L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other.



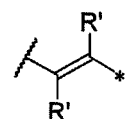
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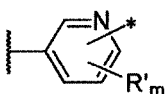
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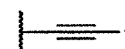
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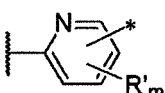
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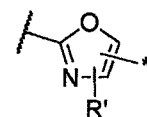
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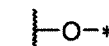
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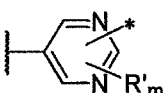
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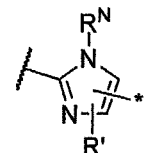
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(L-4)



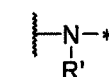
(L-16)



(L-24)



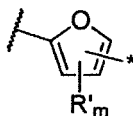
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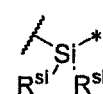
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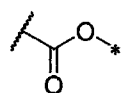
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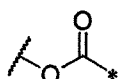
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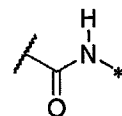
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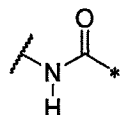
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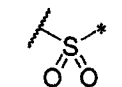
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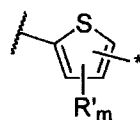
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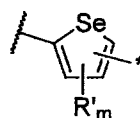
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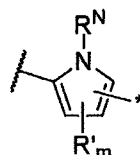
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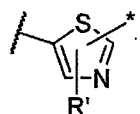
(L-18)



(L-19)



(L-20)



(L-21)

[0038] In Formulae (L-1) to (L-25), the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton. Here, in a case where L represents a divalent linking group in which two or more divalent linking groups represented by any of Formulae (L-1) to (L-25) are bonded to each other, the portion of a wavy line represents a position of bonding to * of the divalent linking group represented by any of Formulae (L-1) to (L-25).

[0039] * represents a position of bonding to either the divalent linking group represented by any of Formulae (L-1) to (L-25) or R.

[0040] m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, and m in Formula (L-22) represents 6.

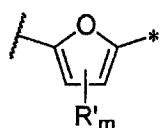
[0041] Each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent.

[0042] R^N represents a hydrogen atom or a substituent.

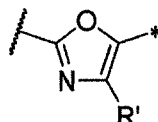
[0043] Each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[0044] Each R' in Formulae (L-1) and (L-2) may form a condensed ring by being bonded to R adjacent to L.

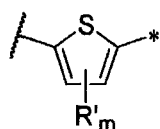
[0045] The divalent linking group represented by any of Formulae (L-19) to (L-21), (L-23), and (L-24) is more preferably a divalent linking group represented by any of the following Formulae (L-19A) to (L-21A), (L-23A), and (L-24A).



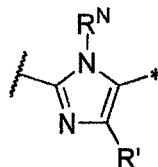
(L-17A)



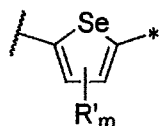
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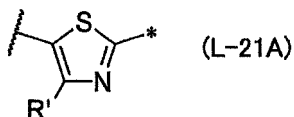
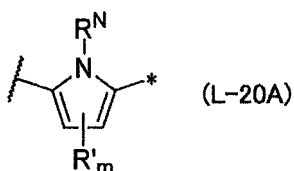
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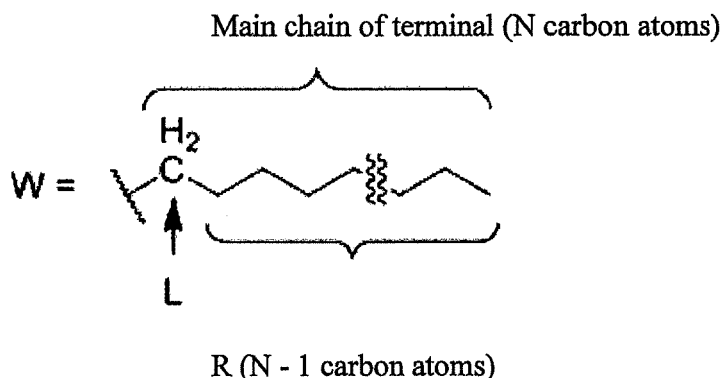


(L-19A)



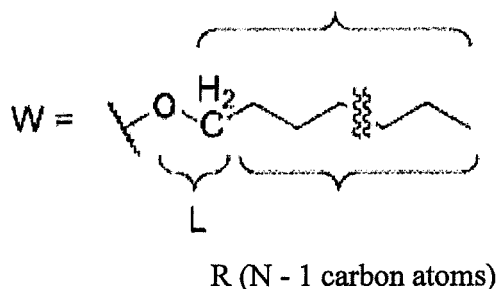
[0046] In a case where a substituted or unsubstituted alkyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group is present on the terminal of the substituent represented by Formula (W), the substituent can be interpreted as either a substituent consisting of only -R in Formula (W) or a substituent consisting of -R-L in Formula (W).

[0047] In the present invention, in a case where a substituted or unsubstituted alkyl group whose main chain consists of N carbon atoms is present on the terminal of the substituent represented by Formula (W), the substituent is interpreted as -L-R in Formula (W) by including as much linking groups represented by $-CR^{R_2}-$ as possible in R from the terminal of the substituent represented by Formula (W), and is not interpreted as a substituent composed solely of -R. R^R represents a hydrogen atom or a substituent. Specifically, the substituent is interpreted as a substituent in which "one (L-1) corresponding to L in Formula (W)" is bonded to "a substituted or unsubstituted alkyl group corresponding to R in Formula (W) having a main chain consisting of $(N - 1)$ carbon atoms". For example, in a case where a n -octyl group as an alkyl group having 8 carbon atoms is present on the terminal of the substituent, the substituent is interpreted as a substituent in which one (L-1), wherein two R's are hydrogen atoms, is bonded to a n -heptyl group having 7 carbon atoms. In a case where the substituent represented by Formula (W) is an alkyl group, for example, how to make a differentiation between L and R is as follows, and L represents a divalent linking group represented by Formula (L-1).

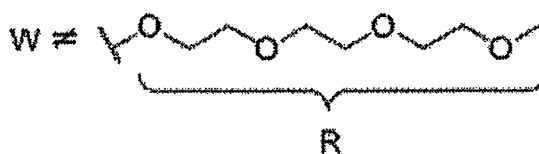
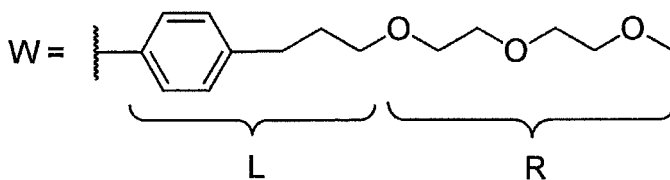
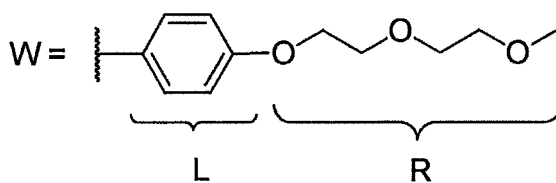


[0048] In a case where the substituent represented by Formula (W) is an alkoxy group having 8 carbon atoms, the alkoxy group is interpreted as a substituent in which one linking group represented by Formula (L-4) that is -O-, one linking group represented by Formula (L-1) in which two R's are hydrogen atoms, and a n -heptyl group having 7 carbon atoms are bonded to each other. In a case where the substituent represented by Formula (W) is a group other than an alkyl group, how to make a differentiation between L and R is as follows, and L represents a divalent linking group in which "a divalent linking group other than the linking group represented by Formula (L-1)" and "a divalent linking group represented by Formula (L-1)" are bonded to each other.

Main chain of terminal (N carbon atoms)



[0049] In contrast, in the present invention, in a case where an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group is present on the terminal of the substituent represented by Formula (W), the substituent is interpreted as a substituent consisting solely of R in Formula (W) including as much linking groups as possible in R from the terminal of the substituent represented by Formula (W) but is not interpreted as -L-R. For example, in a case where a $-(\text{OCH}_2\text{CH}_2)-(\text{OCH}_2\text{CH}_2)-(\text{OCH}_2\text{CH}_2)-\text{OCH}_3$ group is present on the terminal of the substituent, the substituent is interpreted as a substituent consisting of only an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is 2. In a case where an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group is present on the terminal of the substituent represented by Formula (W), how to make a differentiation between L and R is as follows, for example.



[0050] In a case where L forms a linking group in which divalent linking groups represented by any of Formulae (L-1) to (L-25) are bonded to each other, the number of the divalent linking groups bonded to each other represented by any of Formulae (L-1) to (L-25) is preferably 2 to 4, and more preferably 2 or 3.

[0051] Examples of the substituent R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) include those exemplified above as the substituents that can be adopted as R¹ to R⁸ in Formula (1-1) or (1-2) described above. Among these, the substituent R' in Formula (L-6) is preferably an alkyl group. In a case where R' in (L-6) is an alkyl group, the number of carbon atoms of the alkyl group is preferably 1 to 18, more preferably 5 to 12 from the viewpoint of the chemical stability and the carrier transport properties, and even more preferably 8 to 10. In a case where R' in (L-6) is an alkyl group, the alkyl group is preferably a linear alkyl group because then the carrier mobility can be improved.

[0052] R^N represents a hydrogen atom or a substituent, and examples of R^N include those exemplified above as substituents that can be adopted as R¹ to R⁸ in Formula (1-1) or (1-2) described above. Among these, a hydrogen atom or a methyl group is preferable as R^N.

[0053] Each R^{Si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group, and is preferably an alkyl group. The alkyl group that can be adopted as R^{Si} is not particularly limited, and the preferred

range of the alkyl group that can be adopted as R^{Si} is the same as the preferred range of an alkyl group that can be adopted as a silyl group in a case where R is a silyl group. The alkenyl group that can be adopted as R^{Si} is not particularly limited. However, the alkenyl group is preferably a substituted or unsubstituted alkenyl group and more preferably a branched alkenyl group, and the number of carbon atoms of the alkenyl group is preferably 2 or 3. The alkynyl group that can be adopted as R^{Si} is not particularly limited. However, the alkynyl group is preferably a substituted or unsubstituted alkynyl group and more preferably a branched alkynyl group, and the number of carbon atoms of the alkynyl group is preferably 2 or 3.

[0054] In a case where L includes divalent linking groups represented by Formulae (L-13) to (L-25), it is preferable that any one of the divalent linking groups represented by Formulae (L-13) to (L-25) is linked to R through a divalent linking group represented by Formula (L-1).

[0055] L is preferably a divalent linking group represented by any of Formulae (L-1) to (L-5), (L-13), (L-17), and (L-18) or a divalent linking group in which two or more divalent linking groups represented by any of Formulae (L-1) to (L-5), (L-13), (L-17), and (L-18) are bonded to each other, more preferably a divalent linking group represented by any of Formulae (L-1), (L-3), (L-13), and (L-18) or a divalent linking group in which two or more divalent linking groups represented by any of Formulae (L-1), (L-3), (L-13), and (L-18) are bonded to each other, and particularly preferably a divalent linking group represented by (L-1), (L-3), (L-13), or (L-18) or a divalent linking group in which a divalent linking group represented by one of Formulae (L-3), (L-13), and (L-18) is bonded to a divalent linking group represented by Formula (L-1). It is preferable that the divalent linking group represented by Formula (L-1) is bonded to the R side of a divalent linking group in which the divalent linking group represented by any one of Formulae (L-3), (L-13), and (L-18) is bonded to the divalent linking group represented by Formula (L-1).

[0056] From the viewpoint of the chemical stability and the carrier transport properties, L is particularly preferably a divalent linking group including the divalent linking group represented by Formula (L-1), more particularly preferably a divalent linking group represented by Formula (L-1). Even more particularly preferably, the substituent represented by Formula (W) is a group in which L is a divalent linking group represented by Formula (L-1), and R is a substituted or unsubstituted alkyl group.

[0057] In Formula (W), R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted silyl group.

[0058] In Formula (W), in a case where L adjacent to R is a divalent linking group represented by Formula (L-1), R is preferably a substituted or unsubstituted alkyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, or an oligosiloxane group having two or more silicon atoms, and more preferably a substituted or unsubstituted alkyl group.

[0059] In Formula (W), in a case where L adjacent to R is a divalent linking group represented by any of Formulae (L-2) and (L-4) to (L-25), R is more preferably a substituted or unsubstituted alkyl group.

[0060] In Formula (W), in a case where L adjacent to R is a divalent linking group represented by Formula (L-3), R is preferably a substituted or unsubstituted alkyl group or a substituted or unsubstituted silyl group.

[0061] In a case where R is a substituted or unsubstituted alkyl group, the number of carbon atoms thereof is preferably 1 to 18, more preferably 5 to 12 from the viewpoint of the chemical stability and the carrier transport properties, and even more preferably 8 to 10. If R is a long-chain alkyl group within the above range, the alkyl group is particularly preferably a long-chain linear alkyl group because then the linearity of the molecule is improved, and hence the carrier mobility can be improved.

[0062] In a case where R represents an alkyl group, the alkyl group may be a linear, branched, or cyclic alkyl group. However, from the viewpoint of the overlapping of HOMO, the alkyl group is preferably a linear alkyl group.

[0063] Among these, from the viewpoint of improving the carrier mobility, R and L in Formula (W) are preferably combined such that L is a divalent linking group represented by Formula (L-1), and R is a linear alkyl group having 1 to 18 carbon atoms; or that L is a divalent linking group in which a divalent linking group represented by any one of Formulae (L-3), (L-13), and (L-18) is bonded to a divalent linking group represented by Formula (L-1), and R is a linear alkyl group.

[0064] In a case where L is a divalent linking group represented by Formula (L-1), and R is a linear alkyl group having 1 to 18 carbon atoms, from the view point of improving the carrier mobility, R is more preferably a linear alkyl group having 5 to 12 carbon atoms, and particularly preferably a linear alkyl group having 8 to 10 carbon atoms.

[0065] In a case where L is a divalent linking group in which a divalent linking group represented by any one of Formulae (L-3), (L-13), and (L-18) is bonded to a divalent linking group represented by Formula (L-1), and R is a linear alkyl group, R is more preferably a linear alkyl group having 1 to 12 carbon atoms, even more preferably a linear alkyl group having 5 to 12 carbon atoms from the viewpoint of the chemical stability and the carrier transport properties, and particularly preferably a linear alkyl group having 8 to 10 carbon atoms from the viewpoint of improving the carrier mobility.

[0066] In contrast, from the viewpoint of improving the solubility in an organic solvent, R is preferably a branched alkyl group.

[0067] In a case where R is an alkyl group having a substituent, examples of the substituent include a halogen atom and the like (at this time, R becomes a haloalkyl group), and among these, a fluorine atom is preferable. In a case where R is an alkyl group having a fluorine atom, a perfluoroalkyl group may be formed by the substitution of all of the hydrogen atoms of the alkyl group with the fluorine atom. Here, R is preferably an unsubstituted alkyl group.

[0068] In the present specification, in a case where the R is an ethyleneoxy group or an oligo-ethyleneoxy group in which a repetition number v of an oxyethylene group is equal to or greater than 2, the "oligo-oxyethylene group" represented by R refers to a group represented by $-(OCH_2CH_2)_vOY$ (the repetition number v of an oxyethylene unit represents an integer of equal to or greater than 2, and Y on the terminal represents a hydrogen atom or a substituent). In a case where Y on the terminal of the oligo-oxyethylene group is a hydrogen atom, the terminal becomes a hydroxy group. The repetition number v of the oxyethylene unit is preferably 2 to 4, and more preferably 2 or 3. It is preferable that the hydroxy group on the terminal of the oligo-oxyethylene group is sealed. That is, it is preferable that Y represents a substituent. In this case, the hydroxy group is preferably sealed with an alkyl group having 1 to 3 carbon atoms. In other words, Y is preferably an alkyl group having 1 to 3 carbon atoms, more preferably a methyl group or an ethyl group, and particularly preferably a methyl group.

[0069] In a case where R is a siloxane group or an oligosiloxane group having two or more silicon atoms, the repetition number of the siloxane unit is preferably 2 to 4, and more preferably 2 or 3. Furthermore, it is preferable that hydrogen atoms or alkyl groups are bonded to the Si atoms. In a case where alkyl groups are bonded to the Si atoms, the number of carbon atoms of each alkyl group is preferably 1 to 3. For example, it is preferable that methyl groups or ethyl groups are bonded to the Si atoms. The same alkyl groups may be bonded to the Si atoms, or different alkyl groups or hydrogen atoms may be bonded to the Si atoms. In addition, all of the siloxane units constituting the oligosiloxane group may be the same as or different from each other, but it is preferable that they are the same as each other.

[0070] In a case where L adjacent to R is a divalent linking group represented by Formula (L-3), R is preferably a substituted or unsubstituted silyl group. In a case where R is a substituted or unsubstituted silyl group, a substituted silyl group is preferable as R. The substituent of the silyl group is not particularly limited. However, the substituent is preferably a substituted or unsubstituted alkyl group, and more preferably a branched alkyl group. In a case where R is a trialkylsilyl group, the number of carbon atoms of each alkyl group bonded to the Si atoms is preferably 1 to 3. For example, it is preferable that methyl groups, ethyl groups, or isopropyl groups are bonded to the Si atoms. The same alkyl groups or different alkyl groups may be bonded to the Si atoms. In a case where R is a trialkylsilyl group further having a substituent on the alkyl group, the substituent is not particularly limited.

[0071] In Formula (W), the total number of carbon atoms contained in L and R is preferably 5 to 18. If the total number of carbon atoms contained in L and R is equal to or greater than the lower limit of the above range, the carrier mobility is improved, and the driving voltage is reduced. If the total number of carbon atoms contained in L and R is equal to or less than the upper limit of the above range, the solubility in an organic solvent is improved.

[0072] The total number of carbon atoms contained in L and R is preferably 5 to 14, more preferably 6 to 14, particularly preferably 6 to 12, and more particularly preferably 8 to 12.

[0073] In the compound represented by the Formula (1-1), the number of groups adopted as one of R^1 to R^9 and represented by Formula (W) is preferably 1 to 4 from the viewpoint of improving the carrier mobility and the solubility in an organic solvent, more preferably 1 or 2, and particularly preferably 2.

[0074] The group represented by the Formula (W) is positioned in any of R^1 to R^9 without particular limitation. However, from the viewpoint of improving the carrier mobility and the solubility in an organic solvent, the group is preferably positioned in R^4 or R^8 , and more preferably positioned in R^4 and R^8 .

[0075] In the compound represented by the Formula (1-2), the number of groups adopted as R^9 to R^{17} and represented by Formula (W) is preferably 1 to 4 from the viewpoint of improving the carrier mobility and the solubility in an organic solvent, more preferably 1 or 2, and particularly preferably 2.

[0076] The group represented by Formula (W) is positioned in any of R^9 to R^{17} without particular limitation. However, from the viewpoint of improving the carrier mobility and the solubility in an organic solvent, the group is preferably positioned in R^{12} or R^{16} , and more preferably positioned in R^{12} and R^{16} .

[0077] The number of substituents that are adopted as R^1 to R^9 in Formula (1-1) but other than the group represented by the Formula (W) is preferably 0 to 4, more preferably 0 to 2, particularly preferably 0 or 1, and more particularly preferably 0.

[0078] The number of substituents that are adopted as R^9 to R^{17} in Formula (1-2) but other than the group represented by the Formula (W) is preferably 0 to 4, more preferably 0 to 2, particularly preferably 0 or 1, and more particularly preferably 0.

[0079] In a case where each of R^1 to R^{17} is a substituent other than the substituent represented by Formula (W), the substituent as each of R^1 to R^{17} is preferably a group having a linking group chain length of equal to or less than 3.7 Å, more preferably a group having a linking group chain length of 1.0 Å to 3.7 Å, and even more preferably a group having a linking group chain length of 1.0 Å to 2.1 Å.

[0080] The linking group chain length refers to a length from a C atom to the terminal of the substituent R^0 in a C- R^0

bond. Structural optimization calculation can be performed using a density functional method (Gaussian 03 (Gaussian Inc.)/basis function: 6-31G*, exchange-correlation functional: B3LYP/LANL2DZ). The molecular lengths of typical substituents are 4.6 Å for a propyl group, 4.6 Å for a pyrrole group, 4.5 Å for a propynyl group, 4.6 Å for a propenyl group, 4.5 Å for an ethoxy group, 3.7 Å for a methylthio group, 3.4 Å for an ethenyl group, 3.5 Å for an ethyl group, 3.6 Å for an ethynyl group, 3.3 Å for a methoxy group, 2.1 Å for a methyl group, and 1.0 Å for a hydrogen atom.

[0081] In a case where each of R¹ to R¹⁷ is a substituent other than the substituent represented by Formula (W), each of the substituents as R¹ to R¹⁷ is preferably independently a substituted or unsubstituted alkyl group having 2 or less carbon atoms, a substituted or unsubstituted alkynyl group having 2 or less carbon atoms, a substituted or unsubstituted alkenyl group having 2 or less carbon atoms, or a substituted or unsubstituted acyl group having two or less carbon atoms, and more preferably independently a substituted or unsubstituted alkyl group having 2 or less carbon atoms.

[0082] In a case where each of R¹ to R¹⁷ is a substituent other than the substituent represented by Formula (W), and each of the substituents as R¹ to R¹⁷ independently represents a substituted alkyl group having 2 or less carbon atoms, examples of the substituent that the alkyl group can have include a cyano group, a fluorine atom, a deuterium atom, and the like, and among these, a cyano group is preferable. In a case where each of R¹ to R¹⁷ is a substituent other than the substituent represented by Formula (W), the substituted or unsubstituted alkyl group having 2 or less carbon atoms that is represented by the substituent as each of R¹ to R¹⁷ is preferably a methyl group, an ethyl group, or a methyl group substituted with a cyano group, more preferably a methyl group or a methyl group substituted with a cyano group, and particularly preferably a methyl group substituted with a cyano group.

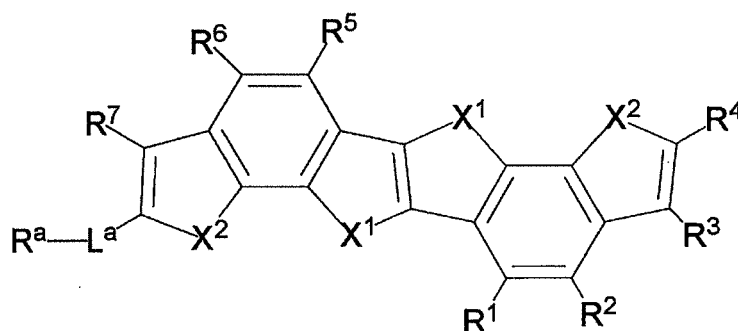
[0083] In a case where each of R¹ to R¹⁷ is a substituent other than the substituent represented by Formula (W), and each of the substituents as R¹ to R¹⁷ independently represents a substituted alkynyl group having 2 or less carbon atoms, examples of the substituent that the alkynyl group can have include a deuterium atom and the like. In a case where each of R¹ to R¹⁷ is a substituent other than the substituent represented by Formula (W), examples of the substituted or unsubstituted alkynyl group having 2 or less carbon atoms that is represented by the substituent as each of R¹ to R¹⁷ include an ethynyl group and an acetylene group substituted with a deuterium atom, and among these, an ethynyl group is preferable.

[0084] In a case where each of R¹ to R¹⁷ is a substituent other than the substituent represented by Formula (W), and each of the substituents as R¹ to R¹⁷ independently represents a substituted alkenyl group having 2 or less carbon atoms, examples of the substituent that the alkenyl group can have include a deuterium atom and the like. In a case where each of R¹ to R¹⁷ is a substituent other than the substituent represented by Formula (W), examples of a substituted or unsubstituted alkenyl group having 2 or less carbon atoms that is represented by the substituent as each of R¹ to R¹⁷ include an ethenyl group and an ethenyl group substituted with a deuterium atom, and among these, an ethenyl group is preferable.

[0085] In a case where each of R¹ to R¹⁷ is a substituent other than the substituent represented by Formula (W), and each of the substituents as R¹ to R¹⁷ independently represents a substituted acyl group having 2 or less carbon atoms, examples of the substituent that the acyl group can have include a fluorine atom and the like. In a case where each of R¹ to R¹⁷ is a substituent other than the substituent represented by Formula (W), examples of a substituted or unsubstituted acyl group having 2 or less carbon atoms that is represented by the substituent as each of R¹ to R¹⁷ include a formyl group, an acetyl group, and an acetyl group substituted with fluorine, and among these, a formyl group is preferable.

[0086] The compound represented by Formula (1-1) is preferably a compound represented by the following Formula (2-1-1) or (2-1-2), and is particularly preferably a compound represented by Formula (2-1-2) from the viewpoint of high mobility.

Formula (2-1-1)



In Formula (2-1-1),

each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,

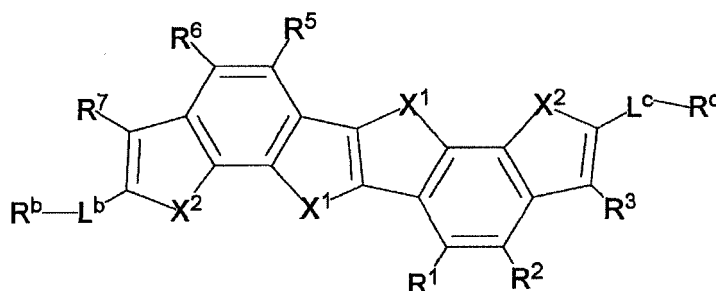
each of R¹ to R⁷ and R⁹ independently represents a hydrogen atom or a substituent, R⁸

each of R¹ to R⁷ and R⁹ independently represents a hydrogen atom or a substituent, R⁴ is not a group represented by -L^a-R^a,

L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and

R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oilgosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

Formula (2-1-2)



in Formula (2-1-2),

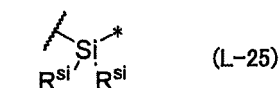
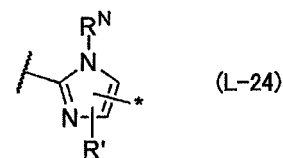
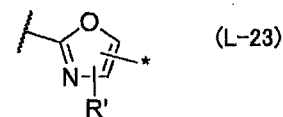
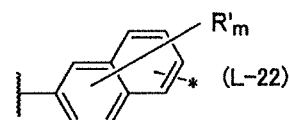
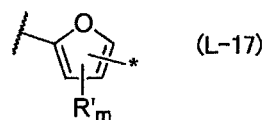
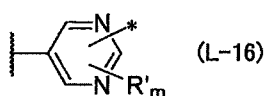
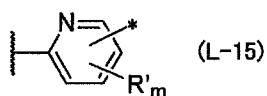
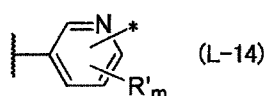
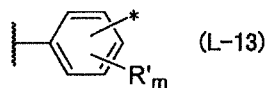
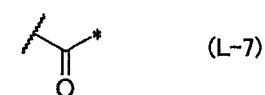
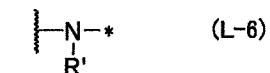
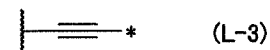
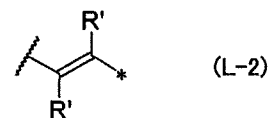
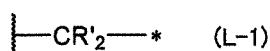
each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,

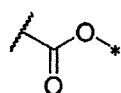
each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,

each of R¹ to R³, R⁵ to R⁷, and R⁹ independently represents a hydrogen atom or a substituent,

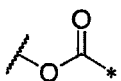
each of L^b and L^c independently represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and

each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

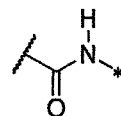




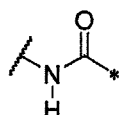
(L-8)



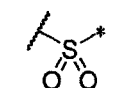
(L-9)



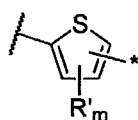
(L-10)



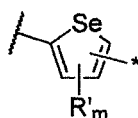
(L-11)



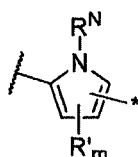
(L-12)



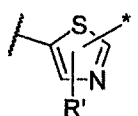
(L-18)



(L-19)



(L-20)



(L-21)

in Formulae (L-1) to (L-25), the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton, m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6, each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent, R^N represents a hydrogen atom or a substituent, and each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[0087] Each of X¹ and X² in Formula (2-1-1) independently represents an oxygen atom or a sulfur atom. The preferred range of X¹ and X² in Formula (2-1-1) is the same as the preferred range of X¹ and X² in Formula (1-1).

[0088] Each of R¹ to R⁷ and R⁹ in Formula (2-1-1) independently represents a hydrogen atom or a substituent. Here, R⁴ is not a group represented by -L^a-R^a. In a case where each of R¹ to R⁷ and R⁸ in Formula (2-1-1) represents a substituent, the preferred range of the substituent is the same the preferred range of the substituent that is represented by each of R¹ to R⁹ in Formula (1-1) and other than the substituent represented by Formula (W).

[0089] L^a in Formula (2-1-1) represents a divalent linking group represented by any of Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other. R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group. The preferred range of L^a and R^a in Formula (2-1-1) is the same as the preferred range of L and R in Formula (1-1).

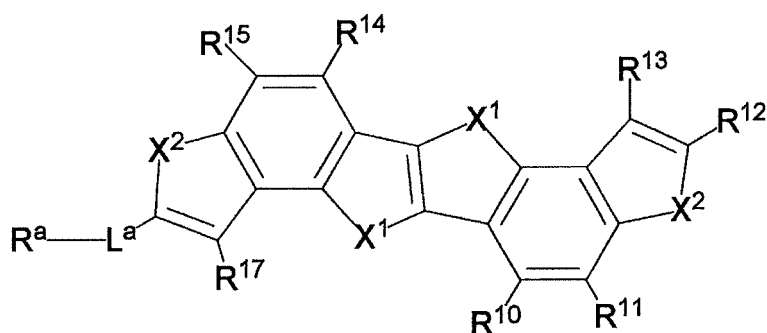
[0090] Each of X¹ and X² in Formula (2-1-2) independently represents an oxygen atom or a sulfur atom. The preferred range of X¹ and X² in Formula (2-1-2) is the same as the preferred range of X¹ and X² in Formula (1-1).

[0091] Each of R¹ to R³, R⁵ to R⁷, and R⁹ in Formula (2-1-2) independently represents a hydrogen atom or a substituent. In a case where each of R¹ to R³, R⁵ to R⁷, and R⁹ in Formula (2-1-2) represents a substituent, the preferred range of the substituent is the same as the preferred range of the substituent that is represented by each of R¹ to R⁹ in Formula (1-1) and other than the substituent represented by Formula (W).

[0092] Each of L^b and L^c in Formula (2-1-2) represents a divalent linking group represented by any of Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other. Each of R^b and R^c represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group. The preferred range of L^b, L^c, R^b, and R^c in Formula (2-1-2) is the same as the preferred range of L and R in Formula (1-1).

[0093] The compound represented by Formula (1-2) is preferably a compound represented by the following Formula (2-2-1) or (2-2-2), and particularly preferably a compound represented by Formula (2-2-2) from the viewpoint of high mobility.

Formula (2-2-1)



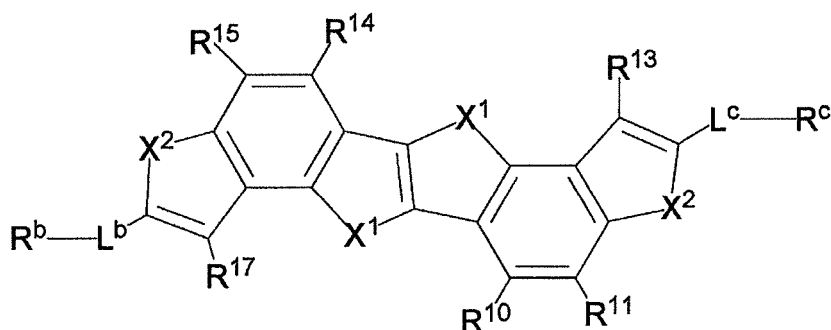
In Formula (2-2-1),

each X^1 independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR^9 ,
 each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R^{10} , R^{12} to R^{15} , and R^{17} independently represents a hydrogen atom or a substituent, R^{12} is not a group
 represented by $-L^a-R^a$,

L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent
 linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-
 25) are bonded to each other, and

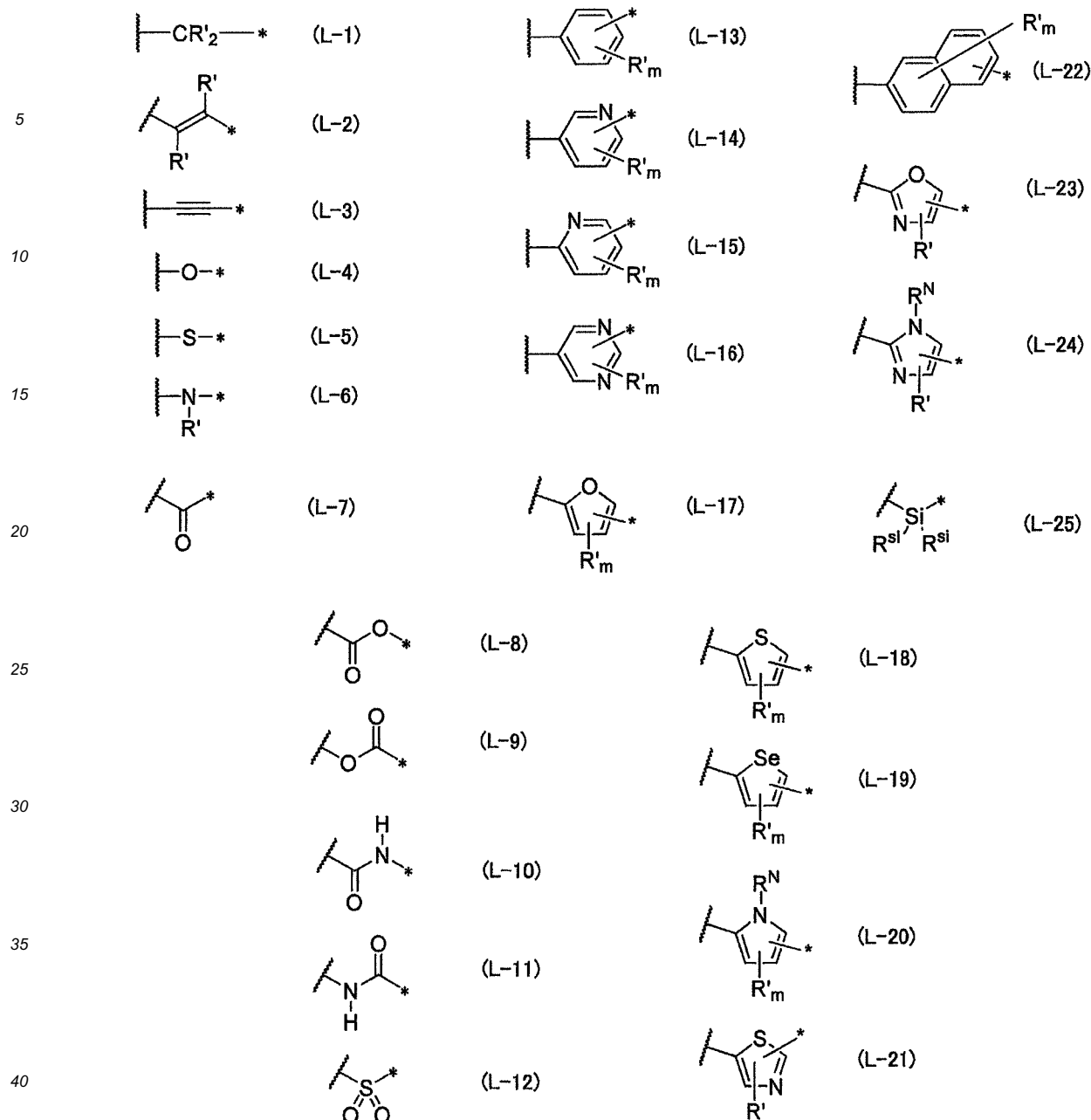
R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyeth-
 ylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater
 than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted
 trialkylsilyl group;

Formula (2-2-2)



in Formula (2-2-2),

each X^1 independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR^9 ,
 each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R^{10} , R^{11} , R^{13} to R^{15} , and R^{17} independently represents a hydrogen atom or a substituent,
 each of L^b and L^c independently represents a divalent linking group represented by any of the following Formulae
 (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the
 following Formulae (L-1) to (L-25) are bonded to each other, and
 each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group,
 an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene
 unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a
 substituted or unsubstituted trialkylsilyl group;



in Formulae (L-1) to (L-25), the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton, m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6, each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent, R^N represents a hydrogen atom or a substituent, and each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

[0094] Each of X¹ and X² in Formula (2-2-1) independently represents an oxygen atom or a sulfur atom. The preferred range of X¹ and X² in Formula (2-1-1) is the same as the preferred range of X¹ and X² in Formula (1-2).

[0095] Each of R¹⁰, R¹² to R¹⁵, and R¹⁷ in Formula (2-2-1) independently represents a hydrogen atom or a substituent. Here, R¹² is not a group represented by -L^a-R^a. In a case where each of R¹⁰, R¹² to R¹⁵, and R¹⁷ in Formula (2-2-1) represents a substituent, the preferred range of the substituent is the same as the preferred range of the substituent that is represented by each of R⁹ to R¹⁷ in Formula (1-2) and is other than the substituent represented by Formula (W).

[0096] L^a in Formula (2-2-1) represents a divalent linking group represented by any of Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other. R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl

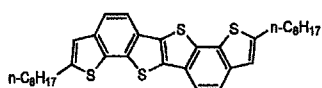
group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group. The preferred range of L^a and R^a in Formula (2-2-1) is the same as the preferred range of L and R in Formula (1-2).

[0097] Each of X^1 and X^2 in Formula (2-2-2) independently represents an oxygen atom or a sulfur atom. The preferred range of X^1 and X^2 in Formula (2-2-2) is the same as the preferred range of X^1 and X^2 in Formula (1-2).

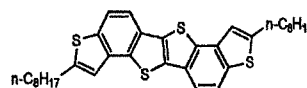
[0098] Each of R^{10} , R^{11} , R^{13} to R^{15} , and R^{17} in Formula (2-2-2) independently represents a hydrogen atom or a substituent. In a case where each of R^{10} , R^{11} , R^{13} to R^{15} , and R^{17} in Formula (2-2-2) represents a substituent, the preferred range of the substituent is the same as the preferred range of the substituent that is represented by each of R^9 to R^{17} in Formula (1-2) and other than the substituent represented by Formula (W).

[0099] Each of L^b and L^c in Formula (2-2-2) represents a divalent linking group represented by any of Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other. Each of R^b and R^c represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group. The preferred range of L^b , L^c , R^b , and R^c in Formula (2-2-2) is the same as the preferred range of L and R in Formula (1-2).

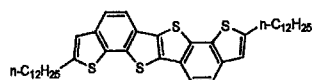
[0100] Specific examples of the compound represented by the Formula (1-1) or (1-2) are shown below, but the compound represented by Formula (1-1) or (1-2) that can be used in the present invention is not limited to the specific examples.



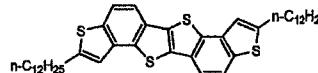
Compound 1



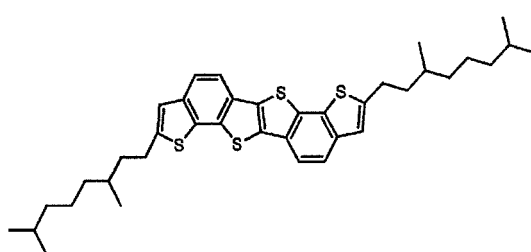
Compound 2



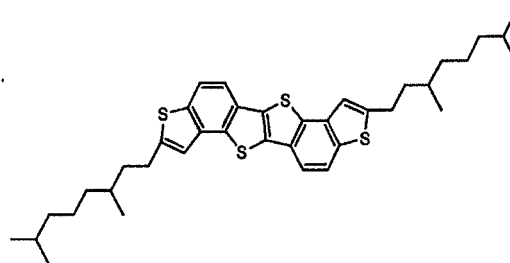
Compound 3



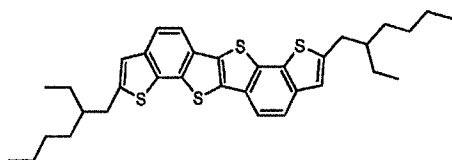
Compound 4



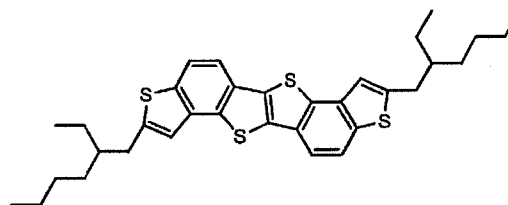
Compound 5



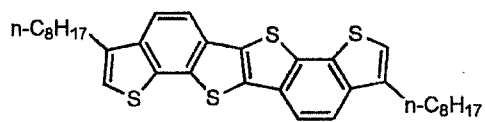
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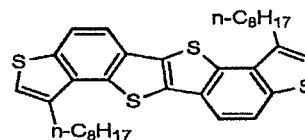
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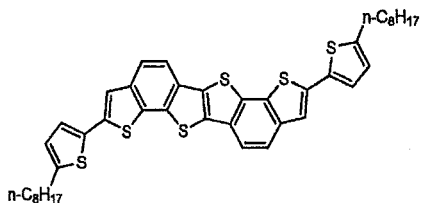
Compound 8



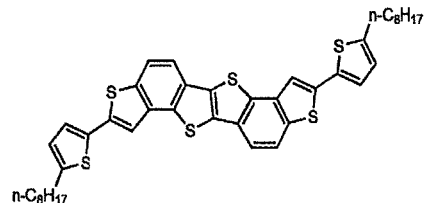
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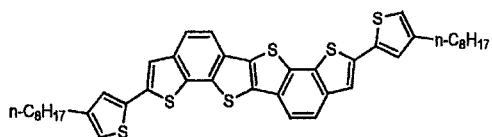
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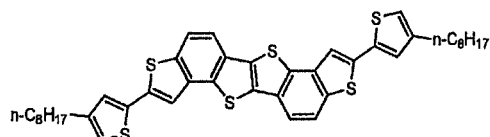
Compound 11



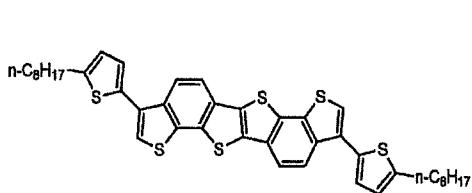
Compound 12



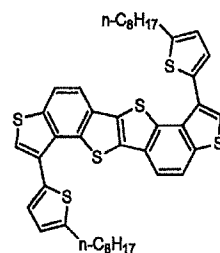
Compound 13



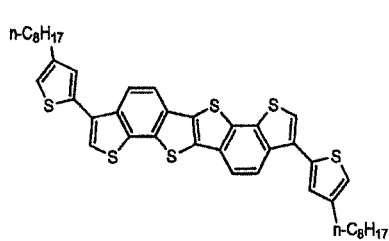
Compound 14



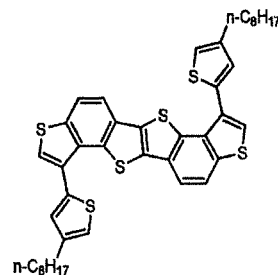
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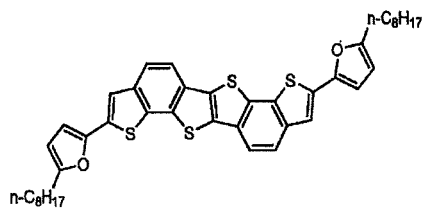
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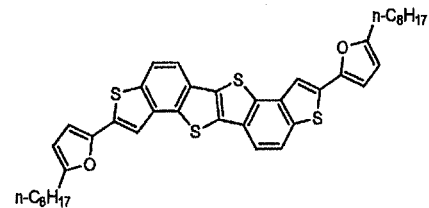
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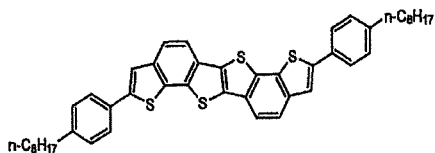
Compound 18



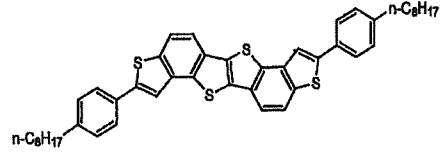
Compound 19



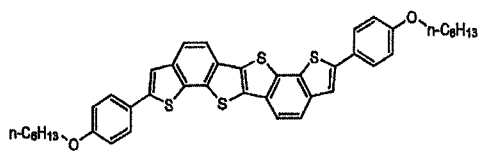
Compound 20



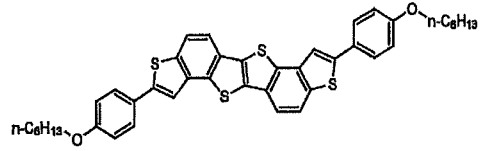
Compound 21



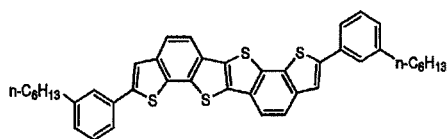
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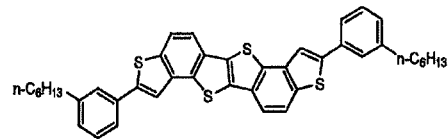
Compound 23



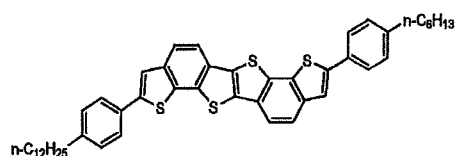
Compound 24



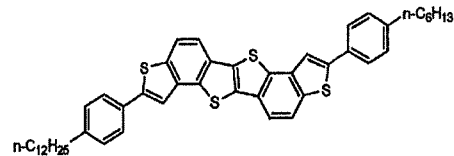
Compound 25



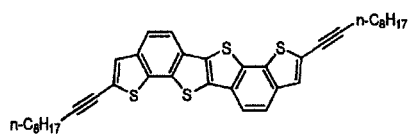
Compound 26



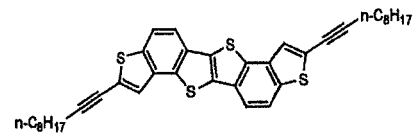
Compound 27



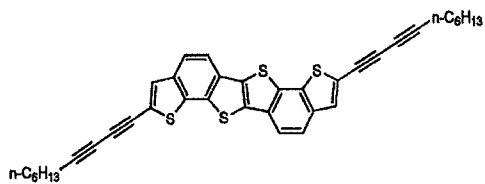
Compound 28



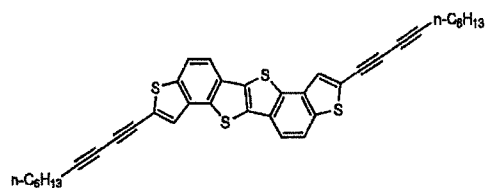
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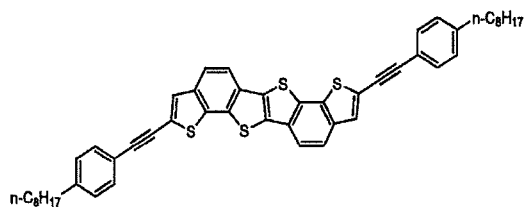
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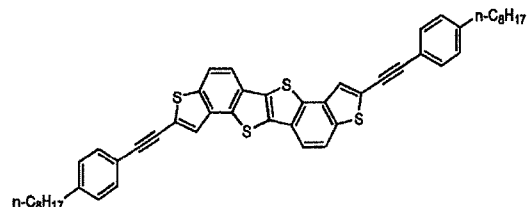
Compound 31



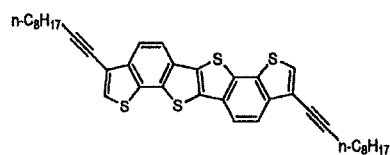
Compound 32



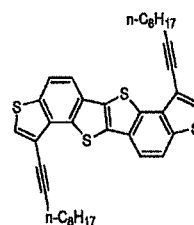
Compound 33



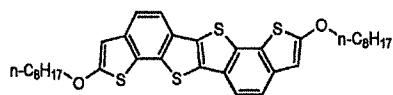
Compound 34



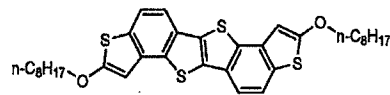
Compound 35



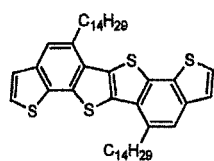
Compound 36



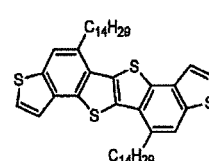
Compound 37



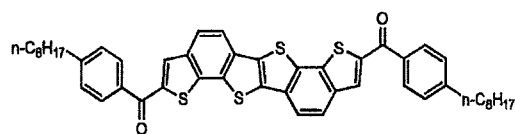
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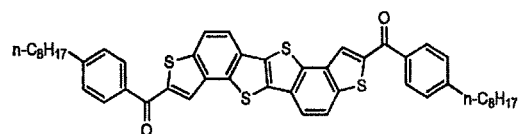
Compound 39



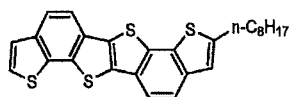
Compound 40



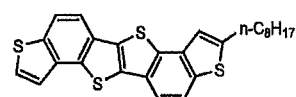
Compound 41



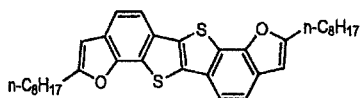
Compound 42



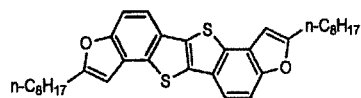
Compound 43



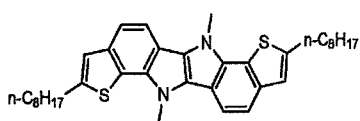
Compound 44



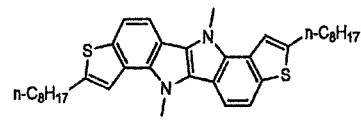
Compound 45



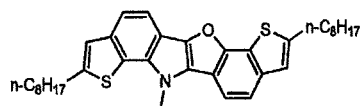
Compound 46



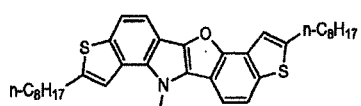
Compound 47



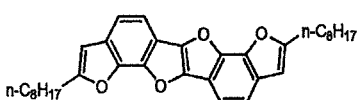
Compound 48



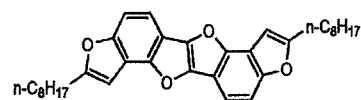
Compound 49



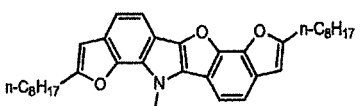
Compound 50



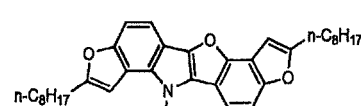
Compound 51



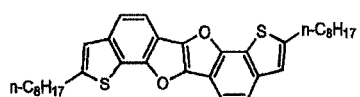
Compound 52



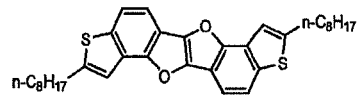
Compound 53



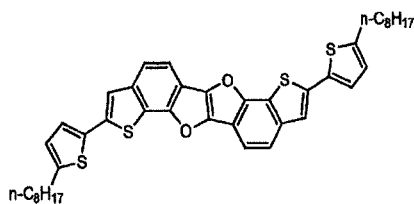
Compound 54



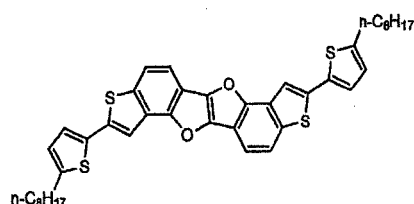
Compound 55



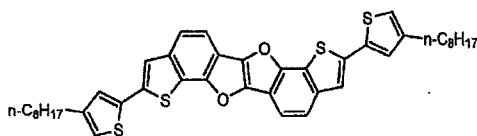
Compound 56



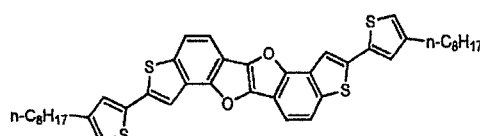
Compound 57



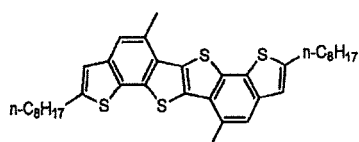
Compound 58



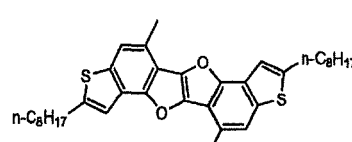
Compound 59



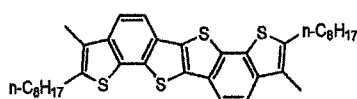
Compound 60



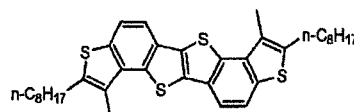
Compound 61



Compound 62



Compound 63



Compound 64

[0101] The compound represented by the Formula (1-1) or (1-2) may have a repeating structure and may be a low-molecular weight compound or a polymer compound. In a case where the compound represented by the Formula (1-1) or (1-2) is a low-molecular weight compound, the molecular weight thereof is preferably equal to or less than 3,000, more preferably equal to or less than 2,000, even more preferably equal to or less than 1,000, and particularly preferably equal to or less than 850. It is preferable that the molecular weight is equal to or less than the upper limit described above because then the solubility in a solvent can be improved.

[0102] In contrast, from the viewpoint of the stability of the film quality, the molecular weight is preferably equal to or greater than 400, more preferably equal to or greater than 450, and even more preferably equal to or greater than 500.

[0103] Furthermore, in a case where the compound represented by Formula (1-1) or (1-2) is a polymer compound having a repeating structure, the weight average molecular weight thereof is preferably equal to or greater than 30,000, more preferably equal to or greater than 50,000, and even more preferably equal to or greater than 100,000. In a case where the compound represented by Formula (1-1) or (1-2) is a polymer compound having a repeating structure, it is preferable that the weight average molecular weight thereof is equal to or greater than the lower limit described above because then the intermolecular interaction can be enhanced, and hence high mobility is obtained.

[0104] Examples of the polymer compound having a repeating structure include a π -conjugated polymer having a repeating structure in which the compound represented by Formula (1-1) or (1-2) represents at least one or more arylene groups or heteroarylene groups (thiophene or bithiophene), and a pendant-type polymer in which the compound represented by Formula (1-1) or (1-2) is bonded to the main chain of the polymer via the side chain. As the main chain of the polymer, polyacrylate, polyvinyl, polysiloxane, or the like is preferable, and as the side chain, an alkylene group, a polyethylene oxide group, or the like is preferable.

[0105] The compound represented by the Formula (1-1) can be synthesized with reference to known documents (Macromolecules, 2010, 43, 6264-6267, J. Am. Chem. Soc. 2012, 134, 16548-16550) by using, as a starting material, a compound described in scheme 1 which will be described later.

[0106] Furthermore, the compound represented by Formula (1-2) can be synthesized with reference to the known

documents described above by using, as a starting material, a compound described in scheme 2 which will be described later.

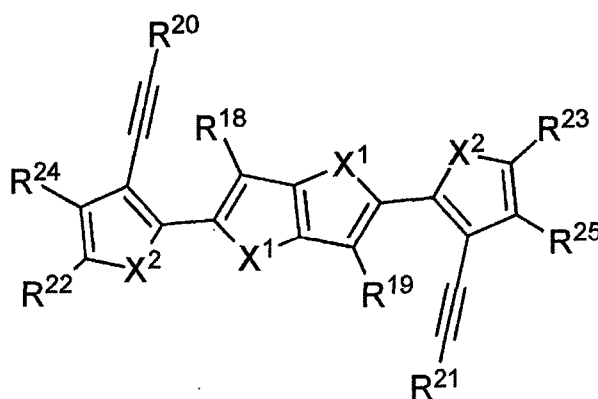
[0107] In synthesizing the compound of the present invention, any of reaction conditions may be used. As a reaction solvent, any solvent may be used. Furthermore, in order to accelerating a ring forming reaction, an acid or a base is preferably used, and a base is particularly preferably used. The optimal reaction conditions vary with the structure of the intended compound, but can be set with reference to the specific reaction conditions described in the above documents.

<Intermediate compound>

[0108] The synthetic intermediate having various substituents can be synthesized using known reactions in combination. Furthermore, various substituents may be introduced into the intermediate at any stage. After the intermediate is synthesized, it is preferable to purify the intermediate by column chromatography, recrystallization, or the like and then further purify it by sublimation. By the sublimation purification, it is possible to separate organic impurities and to effectively remove an inorganic salt, a residual solvent, and the like.

[0109] The present invention also relates to a compound represented by the following Formula (3-1) and a compound represented by the following Formula (3-2).

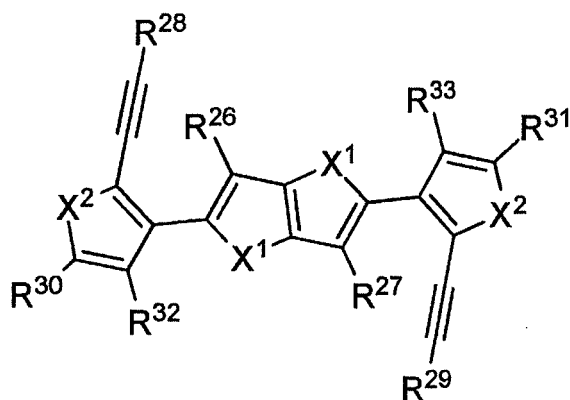
Formula (3-1)



In Formula (3-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R⁹ and R¹⁸ to R²⁵ independently represents a hydrogen atom or a substituent, and at least either R²² or R²³ represents an alkyl group, an alkenyl group, an alkynyl group, a substituted or unsubstituted aryl group, a substituted or unsubstituted heteroaryl group, an alkylcarbonyl group, or a substituted or unsubstituted arylcarbonyl group;

Formula (3-2)



in Formula (3-2),

each X^1 independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR^9 ,
 each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R^9 and R^{26} to R^{33} independently represents a hydrogen atom or a substituent, and at least either R^{30} or R^{31} represents an alkyl group, an alkenyl group, an alkynyl group, a substituted or unsubstituted aryl group, a substituted or unsubstituted heteroaryl group, an alkylcarbonyl group, or a substituted or unsubstituted arylcarbonyl group.

[0110] It is preferable that the compound represented by Formula (3-1) described above is an intermediate compound of the compound represented by Formula (1-1) described above. Furthermore, it is preferable that the compound represented by Formula (3-2) described above is an intermediate compound of the compound represented by Formula (1-2) described above.

[0111] The compound represented by Formula (1-1) described above can be synthesized according to the scheme 1, which will be described later, through a process in which the compound represented by Formula (3-1) described above is synthesized as an intermediate compound thereof.

[0112] In addition, the compound represented by Formula (1-2) described above can be synthesized according to the scheme 2, which will be described later, through a process in which the compound represented by Formula (3-2) described above is synthesized as an intermediate compound thereof.

[0113] Each of X^1 and X^2 in Formula (3-1) has the same definition as each of X^1 and X^2 in Formula (1-1), and the preferred range thereof is also the same.

[0114] Each of R^9 and R^{18} to R^{23} in Formula (3-1) independently represents a hydrogen atom or a substituent. At least either R^{22} or R^{23} represents an alkyl group, an alkenyl group, an alkynyl group, an alkylcarbonyl group, or a substituted or unsubstituted arylcarbonyl group.

[0115] In a case where each of R^9 and R^{18} to R^{23} in Formula (3-1) represents a substituent, the preferred range of the substituent is the same as the preferred range of the substituent that is represented by each of R^1 to R^8 in Formula (1-1) and other than the substituent represented by Formula (W).

[0116] In a case where each of R^{22} and R^{23} in Formula (3-1) represents an alkyl group, the alkyl group is preferably an alkyl group having 1 to 18 carbon atoms, more preferably an alkyl group having 5 to 12 carbon atoms, and particularly preferably an alkyl group having 8 to 10 carbon atoms.

[0117] In a case where each of R^{22} and R^{23} in Formula (3-1) represents an alkenyl group, the alkenyl group is preferably an alkenyl group having 2 to 18 carbon atoms, and more preferably an alkenyl group having 5 to 12 carbon atoms.

[0118] In a case where each of R^{22} and R^{23} in Formula (3-1) represents an alkynyl group, the alkynyl group is preferably an alkynyl group having 2 to 18 carbon atoms, and more preferably an alkynyl group having 5 to 12 carbon atoms.

[0119] In a case where each of R^{22} and R^{23} in Formula (3-1) represents a substituted or unsubstituted aryl group, examples of the aryl group include a benzene ring, a naphthalene ring, an anthracene ring, a tetracene ring, a pentacene ring, a phenanthrene ring, a chrysene ring, a triphenylene ring, a pyrene ring, and the like. Among these, an aryl group having 6 to 18 carbon atoms is preferable, an aryl group having 6 to 10 carbon atoms is more preferable, and an aryl group having 6 carbon atoms is particularly preferable. Examples of the substituent that the substituted aryl group represented by R^{22} and R^{23} may have include the substituent that can be adopted as R^1 to R^9 in Formula (1-1).

[0120] In a case where each of R^{22} and R^{23} in Formula (3-1) represents a substituted or unsubstituted heteroaryl group, examples of the heteroaryl group include rings formed when carbon atoms forming the aforementioned aromatic rings are partially or totally substituted with a heteroatom such as an oxygen atom, a nitrogen atom, or a sulfur atom, a furan ring, a thiophene ring, a pyrrole ring, and the like. Furthermore, the aforementioned aromatic rings or heterocyclic aromatic rings may be condensed with each other or may be further condensed with an oxazole ring, a thiazole ring, an imidazole ring, a thiadiazole ring, and the like. Examples of the heterocyclic aromatic ring as a condensed heterocyclic aromatic ring include a quinoline ring, an isoquinoline ring, a naphthyridine ring, a quinoxaline ring, an acridine ring, a phenazine ring, a benzothiazole ring, a naphthobisthiadiazole ring, a thieno[3,2-b]thiophene ring, a carbazole ring, and the like. Among these, a heteroaryl group having 5 to 18 carbon atoms is preferable, a heteroaryl group having 5 to 10 carbon atoms is more preferable, and a heteroaryl group having 5 carbon atoms is particularly preferable. Examples of the substituent that the substituted heteroaryl group represented by R^{22} and R^{23} may have include the substituents that can be adopted as R^1 to R^9 in Formula (1-1).

[0121] In a case where each of R^{22} and R^{23} in Formula (3-1) represents an alkylcarbonyl group, the alkylcarbonyl group is preferably an alkylcarbonyl group having 2 to 18 carbon atoms, more preferably an alkylcarbonyl group having 5 to 12 carbon atoms, and particularly preferably an alkylcarbonyl group having 8 to 10 carbon atoms.

[0122] In a case where each of R^{22} and R^{23} in Formula (3-1) represents an aryl carbonyl group, the arylcarbonyl group is preferably an arylcarbonyl group having 7 to 25 carbon atoms, more preferably an arylcarbonyl group having 12 to 19 carbon atoms, and particularly preferably an arylcarbonyl group having 15 to 17 carbon atoms.

[0123] Each of X^1 and X^2 in Formula (3-2) has the same definition as each of X^1 and X^2 in Formula (1-2), and the preferred range thereof is also the same.

[0124] Each of R^9 and R^{26} to R^{33} in Formula (3-2) independently represents a hydrogen atom or a substituent. At least either R^{30} or R^{31} represents an alkyl group, an alkenyl group, an alkynyl group, a substituted or unsubstituted aryl group, a substituted or unsubstituted heteroaryl group, an alkylcarbonyl group, or a substituted or unsubstituted arylcarbonyl group.

[0125] In a case where each of R^9 and R^{26} to R^{33} in Formula (3-2) represents a substituent, the preferred range of the substituent is the same as the preferred range of the substituent that is represented by each of R^{10} to R^{17} in Formula (1-2) and other than the substituent represented by Formula (W).

[0126] In a case where each of R^{30} and R^{31} in Formula (3-2) represents an alkyl group, an alkenyl group, an alkynyl group, a substituted or unsubstituted aryl group, a substituted or unsubstituted heteroaryl group, an alkylcarbonyl group, or a substituted or unsubstituted arylcarbonyl group, the specific examples and preferred range of these groups are the same as the specific examples and preferred range of the groups represented by R^{22} and R^{23} in Formula (3-1).

<Structure of organic transistor>

[0127] The organic transistor of the present invention has a semiconductor active layer containing the compound represented by the Formula (1-1) or (1-2).

[0128] The organic transistor of the present invention may further have layers other than the semiconductor active layer.

[0129] The organic transistor of the present invention is preferably used as an organic field effect transistor (FET), and is more preferably used as an insulated gate-type FET in which the gate is insulated from channels.

[0130] Hereinafter, preferred structural aspects of the organic transistor of the present invention will be specifically described by using drawings, but the present invention is not limited to the aspects.

(Lamination structure)

[0131] The lamination structure of an organic field effect transistor is not particularly limited, and various known structures can be adopted.

[0132] For example, the organic transistor of the present invention can adopt a structure (bottom gate/top contact type) in which an electrode, an insulator layer, a semiconductor active layer (organic semiconductor layer), and two electrodes are arranged in this order on the upper surface of a substrate which is a lower most layer. In this structure, the electrode on the upper surface of the substrate as the lower most layer is provided in a portion of the substrate, and the insulator layer is so disposed that it comes into contact with the substrate in a portion other than the electrode. The two electrodes provided on the upper surface of the semiconductor active layer are arranged in a state of being separated from each other.

[0133] Fig. 1 shows the constitution of a bottom gate/top contact-type element. Fig. 1 is a schematic view showing a section of an exemplary structure of the organic transistor of the present invention. In the organic transistor shown in Fig. 1, a substrate 11 is disposed as a lower most layer, an electrode 12 is provided in a portion of the upper surface thereof, and an insulator layer 13 is provided such that it covers the electrode 12 and comes into contact with the substrate 11 in a portion other than the electrode 12. On the upper surface of the insulator layer 13, a semiconductor active layer 14 is provided, and in a portion of the upper surface thereof, two electrodes 15a and 15b separated from each other are arranged.

[0134] In the organic transistor shown in Fig. 1, the electrode 12 is a gate, and the electrode 15a and the electrode 15b are a drain and a source respectively. The organic transistor shown in Fig. 1 is an insulated gate-type FET in which a channel as a path of electric currents between the drain and the source is insulated from the gate.

[0135] As an example of the structure of the organic transistor of the present invention, a bottom gate/bottom contact-type element can be exemplified.

[0136] Fig. 2 shows the constitution of the bottom gate/bottom contact-type element. Fig. 2 is a schematic view showing a section of the structure of an organic transistor manufactured as a substrate for measuring FET characteristics in examples of the present invention. In the organic transistor shown in Fig. 2, a substrate 31 is disposed as a lower most layer, an electrode 32 is provided in a portion of the upper surface thereof, and an insulator layer 33 is provided such that it covers the electrode 32 and comes into contact with the substrate 31 in a portion other than the electrode 32. Furthermore, a semiconductor active layer 35 is provided on the upper surface of the insulator layer 33, and electrodes 34a and 34b are in a lower portion of the semiconductor active layer 35.

[0137] In the organic transistor shown in Fig. 2, the electrode 32 is a gate, and the electrode 34a and the electrode 34b are a drain and a source respectively. The organic transistor shown in Fig. 2 is an insulated gate-type FET in which a channel as a path of electric currents between the drain and the source is insulated from the gate.

[0138] As the structure of the organic transistor of the present invention, a top gate/top contact-type element in which

an insulator and a gate electrode are in the upper portion of a semiconductor active layer or a top gate/bottom contact-type element can also be preferably used.

(Thickness)

[0139] In a case where the organic transistor of the present invention needs to be a thinner transistor, the total thickness of the transistor is preferably, for example, 0.1 μm to 0.5 μm .

(Sealing)

[0140] In order to improve the preservation stability of the organic transistor element by blocking the organic transistor element from the atmosphere or moisture, the entirety of the organic transistor element may be sealed with a metal sealing can, glass, an inorganic material such as silicon nitride, a polymer material such as parylene, a low-molecular weight material, or the like.

[0141] Hereinafter, preferred aspects of the respective layers of the organic transistor of the present invention will be described, but the present invention is not limited to the aspects.

<Substrate>

(Material)

[0142] The organic transistor of the present invention preferably includes a substrate.

[0143] The material of the substrate is not particularly limited, and known materials can be used. Examples of the material include a polyester film such as polyethylene naphthalate (PEN) or polyethylene terephthalate (PET), a cycloolefin polymer film, a polycarbonate film, a triacetylcellulose (TAC) film, a polyimide film, a material obtained by bonding these polymer films to extremely thin glass, ceramics, silicon, quartz, glass, and the like. Among these, silicon is preferable.

<Electrode>

(Material)

[0144] The organic transistor of the present invention preferably includes an electrode.

[0145] As the material constituting the electrode, known conductive materials such as a metal material like Cr, Al, Ta, Mo, Nb, Cu, Ag, Au, Pt, Pd, In, Ni, or Nd, an alloy material of these, a carbon material, and a conductive polymer can be used without particular limitation.

(Thickness)

[0146] The thickness of the electrode is not particularly limited, but is preferably 10 nm to 50 nm.

[0147] A gate width (or a channel width) W and a gate length (or a channel length) L are not particularly limited. However, a ratio of W/L is preferably equal to or greater than 10, and more preferably equal to or greater than 20.

<Insulating layer>

(Material)

[0148] The material constituting the insulating layer is not particularly limited as long as an insulating effect is obtained as required. Examples of the material include silicon dioxide, silicon nitride, a fluorine polymer-based insulating material such as PTFE or CYTOP, a polyester insulating material, a polycarbonate insulating material, an acryl polymer-based insulating material, an epoxy resin-based insulating material, a polyimide insulating material, a polyvinyl phenol resin-based insulating material, a poly p-xylene resin-based insulating material, and the like.

[0149] A surface treatment may be performed on the upper surface of the insulating layer. For example, it is possible to preferably use an insulating layer in which the silicon dioxide surface thereof is subjected to the surface treatment by being coated with hexamethyldisilazane (HMDS) or octadecyltrichlorosilane (OTS).

(Thickness)

[0150] The thickness of the insulating layer is not particularly limited. However, in a case where the film needs to be thinned, the thickness of the insulating layer is preferably 10 nm to 400 nm, more preferably 20 nm to 200 nm, and particularly preferably 50 nm to 200 nm.

<Semiconductor active layer>

(Material)

[0151] In the organic transistor of the present invention, the semiconductor active layer contains a compound represented by Formula (1-1) or (1-2), that is, the compound of the present invention.

[0152] The semiconductor active layer may be a layer consisting of the compound of the present invention or a layer further containing a polymer binder, which will be described later, in addition to the compound of the present invention. Furthermore, the semiconductor active layer may contain a residual solvent used at the time of forming a film.

[0153] The content of the polymer binder in the semiconductor active layer is not particularly limited. However, the content of the polymer binder is preferably within a range of 0% by mass to 95% by mass, more preferably within a range of 10% by mass to 90% by mass, even more preferably within a range of 20% by mass to 80% by mass, and particularly preferably within a range of 30% by mass to 70% by mass.

(Thickness)

[0154] The thickness of the semiconductor active layer is not particularly limited. However, in a case where the film needs to be thinned, the thickness of the semiconductor active layer is preferably 10 nm to 400 nm, more preferably 10 nm to 200 nm, and particularly preferably 10 nm to 100 nm.

[Organic semiconductor material for non-light-emitting organic semiconductor device]

[0155] The present invention also relates to an organic semiconductor material for a non-light-emitting organic semiconductor device containing the compound represented by Formula (1-1) or (1-2), that is, the compound of the present invention.

(Non-light-emitting organic semiconductor device)

[0156] In the present specification, a "non-light-emitting organic semiconductor device" refers to a device which is not used for the purpose of emitting light. The non-light-emitting organic semiconductor device preferably uses an electronic element having a layered structure consisting of films. The non-light-emitting organic semiconductor device includes an organic transistor, an organic photoelectric conversion element (a solid-state imaging element used for a photosensor, a solar cell used for energy conversion, or the like), a gas sensor, an organic rectifying element, an organic inverter, an information recording element, and the like. The organic photoelectric conversion element can be used for both a photosensor (solid-state imaging element) and for energy conversion (a solar cell). Among these, an organic photoelectric conversion element and an organic transistor are preferable, and an organic transistor is more preferable. That is, the organic semiconductor material for a non-light-emitting organic semiconductor device of the present invention is preferably a material for an organic transistor as described above.

(Organic semiconductor material)

[0157] In the present specification, the "organic semiconductor material" is an organic material showing characteristics of a semiconductor. Just as the semiconductor composed of an inorganic material, the organic semiconductor is classified into a p-type (hole-transporting) organic semiconductor material conducting holes as carriers and an n-type (electron-transporting) organic semiconductor material conducting electrons as carriers.

[0158] The compound of the present invention may be used as any of the p-type organic semiconductor material and the n-type organic semiconductor material, but is preferably used as the p-type. The ease with which the carriers flow in the organic semiconductor is represented by a carrier mobility μ . The higher the carrier mobility μ , the better. The carrier mobility μ is preferably equal to or greater than $1 \times 10^{-3} \text{ cm}^2/\text{Vs}$, more preferably equal to or greater than $5 \times 10^{-3} \text{ cm}^2/\text{Vs}$, particularly preferably equal to or greater than $1 \times 10^{-2} \text{ cm}^2/\text{Vs}$, more particularly preferably equal to or greater than $5 \times 10^{-2} \text{ cm}^2/\text{Vs}$, even more particularly preferably equal to or greater than $1 \times 10^{-1} \text{ cm}^2/\text{Vs}$, and still more particularly preferably equal to or greater than $3 \times 10^{-1} \text{ cm}^2/\text{Vs}$. The carrier mobility μ can be determined by the char-

acteristics of the prepared field effect transistor (FET) element or by a time-of-flight (TOF) measurement method.

[Organic semiconductor film for non-light-emitting organic semiconductor device]

5 (Material)

[0159] The present invention also relates to an organic semiconductor film for a non-light-emitting organic semiconductor device containing the compound represented by Formula (1-1) or (1-2) described above, that is, the compound of the present invention.

10 **[0160]** As the organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention, an aspect is also preferable in which the organic semiconductor film contains the compound represented by Formula (1-1) or (1-2) and does not contain a polymer binder.

[0161] Furthermore, the organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention may contain the compound represented by Formula (1-1) or (1-2) and a polymer binder.

15 **[0162]** Examples of the polymer binder include an insulating polymer such as polystyrene, polycarbonate, polyarylate, polyester, polyamide, polyimide, polyurethane, polysiloxane, polysulfone, polymethyl methacrylate, polymethyl acrylate, cellulose, polyethylene, or polypropylene, a copolymer of these, a photoconductive polymer such as polyvinylcarbazole or polysilane, a conductive polymer such as polythiophene, polypyrrole, polyaniline, or poly p-phenylenevinylene, and a semiconductor polymer.

20 **[0163]** One kind of the aforementioned polymer binder may be used singly, or plural kinds thereof may be used concurrently.

[0164] The organic semiconductor material may be uniformly mixed with the polymer binder. Alternatively, the organic semiconductor material and the polymer binder may be totally or partially in a phase separation state. From the viewpoint of the charge mobility, a structure, in which the organic semiconductor and the binder are in a phase separation state along the film thickness direction in the film, is the most preferable because then the binder does not hinder the organic semiconductor from moving a charge.

[0165] Considering the mechanical strength of the film, a polymer binder having a high glass transition temperature is preferable. Furthermore, considering the charge mobility, a polymer binder having a structure not containing a polar group, a photoconductive polymer, and a conductive polymer are preferable.

30 **[0166]** The amount of the polymer binder used is not particularly limited. However, in the organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention, the amount of the polymer binder used is preferably within a range of 0% by mass to 95% by mass, more preferably within a range of 10% by mass to 90% by mass, even more preferably within a range of 20% by mass to 80% by mass, and particularly preferably within a range of 30% by mass to 70% by mass.

35 **[0167]** In the present invention, by adopting the aforementioned structure as the structure of the compound, an organic film having excellent film quality can be obtained. Specifically, because the compound obtained in the present invention has excellent crystallinity, a sufficient film thickness can be obtained, and the obtained organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention has excellent quality.

40 (Film forming method)

[0168] The compound of the present invention may be formed into a film on a substrate by any method.

[0169] At the time of forming the film, the substrate may be heated or cooled. By varying the temperature of the substrate, it is possible to control the film quality or the packing of molecules in the film. The temperature of the substrate is not particularly limited. However, it is preferably between 0°C to 200°C, more preferably between 15°C to 100°C, and particularly preferably between 20°C to 95°C.

[0170] The compound of the present invention can be formed into a film on a substrate by a vacuum process or a solution process, and both of the processes are preferable.

50 **[0171]** Specific examples of the film forming method by a vacuum process include a physical vapor deposition method such as a vacuum vapor deposition method, a sputtering method, an ion plating method, or a molecular beam epitaxy (MBE) method and a chemical vapor deposition (CVD) method such as plasma polymerization, and it is particularly preferable to use a vacuum vapor deposition method.

[0172] Herein, the film forming method by a solution process refers to a method of dissolving an organic compound in a solvent which can dissolve the compound and forming a film by using the solution. Specifically, it is possible to use general methods like a coating method such as a casting method, a dip coating method, a die coater method, a roll coater method, a bar coater method, or a spin coating method, various printing methods such as an ink jet method, a screen printing method, a gravure printing method, a flexographic printing method, an offset printing method, or a micro-contact printing method, and a Langmuir-Blodgett (LB) method. It is particularly preferable to use a casting method, a

spin coating method, an ink jet method, a gravure printing method, a flexographic printing method, an offset printing method, or a micro-contact printing method.

[0173] The organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention is preferably prepared by a solution coating method. In a case where the organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention contains a polymer binder, it is preferable to prepare a coating solution by dissolving or dispersing a material, which will be formed into a layer, and a polymer binder in an appropriate solvent and to form the organic semiconductor film by various coating methods.

[0174] Hereinafter, a coating solution for a non-light-emitting organic semiconductor device of the present invention that can be used for forming a film by a solution process will be described.

[Coating solution for non-light-emitting organic semiconductor device]

[0175] The present invention also relates to a coating solution for a non-light-emitting organic semiconductor device containing the compound represented by Formula (1-1) or (1-2).

[0176] In a case where a film is formed on a substrate by using a solution process, a material which will be formed into a layer is dissolved or dispersed in either or both of an appropriate organic solvent (for example, a hydrocarbon-based solvent such as hexane, octane, decane, toluene, xylene, mesitylene, ethylbenzene, decalin, or 1-methylnaphthalene, a ketone-based solvent such as acetone, methyl ethyl ketone, methyl isobutyl ketone, or cyclohexanone, a halogenated hydrocarbon-based solvent such as dichloromethane, chloroform, tetrachloromethane, dichloroethane, trichloroethane, tetrachloroethane, chlorobenzene, dichlorobenzene, or chlorotoluene, an ester-based solvent such as ethyl acetate, butyl acetate, or amyl acetate, an alcohol-based solvent such as methanol, propanol, butanol, pentanol, hexanol, cyclohexanol, methyl cellosolve, ethyl cellosolve, or ethylene glycol, an ether-based solvent such as dibutylether, tetrahydrofuran, dioxane, or anisole, an amide-imide-based solvent such as N,N-dimethylformamide, N,N-dimethylacetamide, 1-methyl-2-pyrrolidone, or 1-methyl-2-imidazolidinone, a sulfoxide-based solvent such as dimethyl sulfoxide, or a nitrile-based solvent such as acetonitrile) and water so as to obtain a coating solution, and a film can be formed by various coating methods by using the coating solution. One kind of the solvent may be used singly, or plural kinds thereof may be used in combination. Among these, a hydrocarbon-based solvent, a halogenated hydrocarbon-based solvent, and an ether-based solvent are preferable, toluene, xylene, mesitylene, tetralin, dichlorobenzene, and anisole are more preferable, and toluene, xylene, tetralin, and anisole are particularly preferable. The concentration of the compound represented by Formula (1-1) or (1-2) in the coating solution is preferably 0.1% by mass to 80% by mass, more preferably 0.1% by mass to 10% by mass, and particularly preferably 0.5% by mass to 10% by mass. In this way, a film having an arbitrary thickness can be formed.

[0177] In order to form a film by a solution process, the material needs to dissolve in the solvent exemplified above, but simply dissolving in a solvent is not good enough. Generally, even the material formed into a film by a vacuum process can dissolve in a solvent to some extent. The solution process includes a step of coating a substrate with a material by dissolving the material in a solvent and then forming a film by evaporating the solvent, and many of the materials not suitable for being formed into a film by the solution process have high crystallinity. Therefore, the material is inappropriately crystallized (aggregated) in the aforementioned step, and hence it is difficult to form an excellent film. The compound represented by Formula (1-1) or (1-2) is also excellent in the respect that it is not easily crystallized (aggregated).

[0178] As the coating solution for a non-light-emitting organic semiconductor device of the present invention, an aspect is also preferable in which the coating solution contains the compound represented by Formula (1-1) or (1-2) and does not contain a polymer binder.

[0179] Furthermore, the coating solution for a non-light-emitting organic semiconductor device of the present invention may contain the compound represented by Formula (1-1) or (1-2) and a polymer binder. In this case, a material, which will be formed into a layer, and a polymer binder are dissolved or dispersed in an appropriate solvent described above so as to prepare a coating solution, and by using the coating solution, a film can be formed by various coating methods. The polymer binder can be selected from those described above.

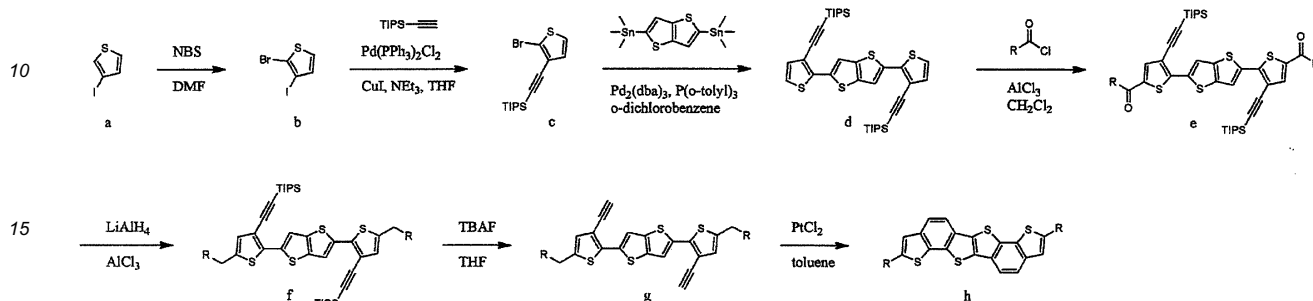
Examples

[0180] Hereinafter, the characteristics of the present invention will be more specifically explained by describing examples and comparative examples. The materials, the amount thereof used, the proportion thereof, the content of treatment, the treatment procedure, and the like described in the following examples can be appropriately modified within a range that does not depart from the gist of the present invention. Accordingly, the scope of the present invention is not limited to the following specific examples.

[Example 1]

<Synthesis example 1> Synthesis of compounds 1, 3, 5, 9, 29, 37, 39, 43, and 51 and an intermediate compound g

5 **[0181]** According to a specific synthesis procedure shown in the following scheme 1, compounds 1, 3, 5, 29, 37, 39, 43, and 51 as the compound represented by Formula (1-1) and intermediate compound g were synthesized.



15 **[0182]** A process will be specifically described in which an intermediate compound g represented by Formula (3-1) and then a compound h represented by Formula (1-1) are synthesized from the compound a described above. In the following synthesis example, a case where R in the scheme 1 is a n-octyl group, that is, a case where the compound h is the compound 1 will be specifically described.

Synthesis of compound b;

25 **[0183]** 4.66 g of N-bromosuccinimide was added to 120 mL of a dimethylformamide solution containing 5.00 g of the compound a, followed by stirring for 12 hours at room temperature. Then, distilled water was added to the mixture, the mixture was moved to a liquid-separating funnel, and an organic layer was extracted using hexane. Subsequently, the organic layer was dried over sodium sulfate and concentrated under reduced pressure. Thereafter, the obtained residue was separated by silica gel chromatography (SiO₂; hexane). In this way, 6.70 g of a product (compound b, yield: 93%) was obtained.

Synthesis of compound c;

35 **[0184]** In a nitrogen atmosphere, a mixed solution of 4.00 g of the compound b, 3.41 mL of triisopropylsilyl acetylene, 0.39 g of bis(triphenylphosphine)palladium (II) dichloride, 0.11 g of copper iodide, 40 mL of triethylamine, and 15 mL of THF was stirred for 12 hours at room temperature. Then, distilled water was added to the mixture, the mixture was moved to a liquid-separating funnel, and an organic layer was extracted using hexane. Subsequently, the organic layer was dried over sodium sulfate and concentrated under reduced pressure. Thereafter, the obtained residue was separated by silica gel chromatography (SiO₂; hexane). In this way, 3.90 g of a product (compound c, yield: 82%) was obtained.

Synthesis of compound d;

45 **[0185]** In a nitrogen atmosphere, 30 mL of a chlorobenzene solution containing 1.80 g of the compound c, 1.2 g of 2,5-bis(trimethylstannyl)thieno[3,2-b]thiophene, 0.058 g of tris(dibenzylideneacetone)dipalladium (0), and 0.078 g of tris(2-methylphenyl)phosphine was heated to 130°C. Then, distilled water was added to the mixture, the mixture was moved to a liquid-separating funnel, and an organic layer was extracted using chloroform. Subsequently, the organic layer was dried over sodium sulfate and concentrated under reduced pressure. Thereafter, the obtained residue was separated by silica gel chromatography (SiO₂; hexane:dichloromethane = 100:2). In this way, 3.90 g of a product (compound d, yield: 82%) was obtained.

Synthesis of compound e;

55 **[0186]** In a nitrogen atmosphere, 0.59 g of n-octanoyl chloride was added to 15 mL of a dichloromethane solution containing 1.00 g of the compound d and 0.95 g of aluminum chloride at room temperature, followed by stirring at room temperature. After 4 hours, methanol, water, and dilute hydrochloric acid (1N) were added thereto in this order so as to stop the reaction, and the precipitated solid was separated by filtration. The obtained solid was separated by silica gel chromatography (SiO₂; hexane:toluene = 5:1). In this way, 0.91 g of a product (compound e, yield: 66%) was obtained.

Synthesis of compound f;

[0187] In a nitrogen atmosphere, 0.66 g of lithium aluminum hydride was added to 30 mL of a tetrahydrofuran solution containing 0.80 g of the compound e and 0.61 g of aluminum chloride, followed by stirring for 6 hours at room temperature. Then, methanol, water, and dilute hydrochloric acid (1 N) were added thereto in this order so as to stop the reaction, and the precipitated solid was separated by filtration. The obtained solid was separated by silica gel chromatography (SiO_2 ; hexane:toluene = 10:1). In this way, 0.70 g of a product (compound f, yield: 90%) was obtained.

Synthesis of compound g;

[0188] 0.70 g of the compound f was added to 15 mL of a tetrahydrofuran solution containing tetra-n-butylammonium fluoride, and the resulting mixture was heated to 60°C for 1 hour. Then, distilled water was added to the mixture, the mixture was moved to a liquid-separating funnel, and an organic layer was extracted using chloroform. In this way, 0.42 g of a product (compound g, yield: 92%) was obtained.

[0189] The structure of the compound g was identified by $^1\text{H-NMR}$. The result is shown in Fig. 3.

Synthesis of compound h;

[0190] In a nitrogen atmosphere, a toluene solution containing 0.42 g of the compound g and 0.038 g of platinum (II) chloride was heated to 90°C for 12 hours. Then, the distilled water was added to the mixture, the mixture was moved to a liquid-separating funnel, and an organic layer was extracted using chloroform. The obtained solid was separated by silica gel chromatography (SiO_2 ; hexane:dichloromethane = 9:1). In this way, 0.20 g of a product (compound h, yield: 47%) was obtained.

[0191] The compound h in which R represents a n-octyl group was denoted as a compound 1. The structure of the compound 1 was identified by $^1\text{H-NMR}$. The result is shown in Fig. 4.

[0192] The compounds represented by Formula (1-1) other than the compound 1 were synthesized in the same manner as used for synthesizing the compound 1. That is, through the compound g, the compounds 3, 5, 29, 37, 39, 43, and 51 represented by Formula (1-1) were synthesized according to the scheme 1 described above.

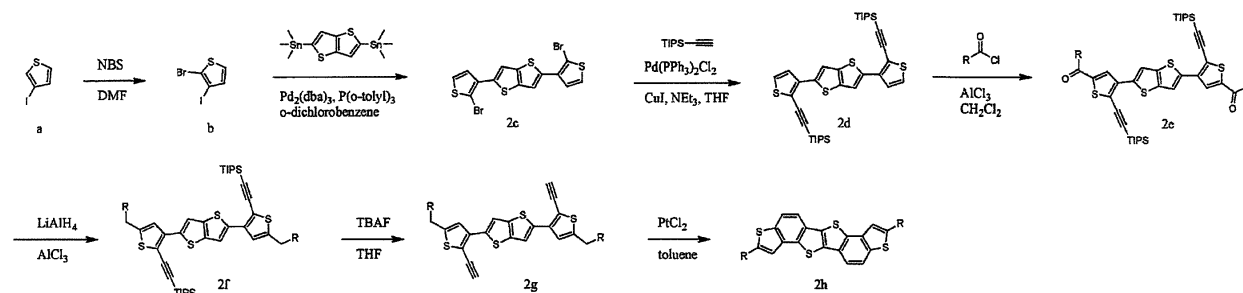
[0193] Each of the obtained compounds represented by Formula (1-1) was identified by elementary analysis, NMR, and MASS spectrometry.

<Synthesis example 2> Synthesis of compounds 2, 4, 30, 38, 40, and 44 and intermediate compound 2g

[0194] According to a specific synthesis procedure shown in the following scheme 2, compounds 2, 4, 30, 38, 40, and 44 as the compound represented by Formula (1-2) and an intermediate compound 2g were synthesized.

Scheme 2

[0195]



[0196] A process will be specifically described in which an intermediate compound 2g represented by Formula (3-2) and then a compound 2h represented by Formula (1-2) are synthesized from the compound b described above. In the following synthesis example, a case where R in the scheme 2 is a n-octyl group, that is, a case where the compound 2h is the compound 2 will be specifically described.

Synthesis of compound 2c;

[0197] In a nitrogen atmosphere, 300 mL of a dimethylacetamide solution containing 8.60 g of the compound b, 7.00 g of 2,5-bis(trimethylstannyl)thieno[3,2-b]thiophene, and 1.05 g of bis(triphenylphosphine)palladium (II) dichloride was heated to 60°C. Then, distilled water was added to the mixture, the mixture was moved to a liquid-separating funnel, and an organic layer was extracted using ethyl acetate. Subsequently, the organic layer was dried over sodium sulfate and concentrated under reduced pressure. Thereafter, the obtained residue was separated by silica gel chromatography (SiO₂; hexane:dichloromethane = 100:5). In this way, 3.00 g of a product (compound 2c, yield: 43%) was obtained.

Synthesis of compound 2d;

[0198] In a nitrogen atmosphere, a mixed solution of 3.00 g of the compound 2c, 3.19 mL of triisopropylsilyl acetylene, 0.36 g of bis(triphenylphosphine)palladium (II) dichloride, 0.99 g of copper iodide, 40 mL of triethylamine, and 15 mL of THF was stirred for 12 hours at room temperature. Then, distilled water was added to the mixture, the mixture was moved to a liquid-separating funnel, and an organic layer was extracted using hexane. Subsequently, the organic layer was dried over sodium sulfate and concentrated under reduced pressure. Thereafter, the obtained residue was separated by silica gel chromatography (SiO₂; hexane). In this way, 3.10 g of a product (compound 2d, yield: 71 %) was obtained.

Synthesis of compound 2e;

[0199] In a nitrogen atmosphere, 1.76 g of n-octanoyl chloride was added to 45 mL of a dichloromethane solution containing 3.00 g of the compound 2d and 2.86 g of aluminum chloride at room temperature, followed by stirring at room temperature. After 4 hours, methanol, water, and dilute hydrochloric acid (1N) were added thereto in this order so as to stop the reaction, and the precipitated solid was separated by filtration. The obtained solid was separated by silica gel chromatography (SiO₂; hexane:toluene = 5:1). In this way, 2.48 g of a product (compound 2e, yield: 60%) was obtained.

Synthesis of compound 2f;

[0200] In a nitrogen atmosphere, 1.66 g of lithium aluminum hydride was added to 80 mL of a tetrahydrofuran solution containing 2.00 g of the compound 2e and 1.29 g of aluminum chloride, followed by stirring for 6 hours at room temperature. Then, methanol, water, and dilute hydrochloric acid (1 N) were added thereto in this order so as to stop the reaction, and the precipitated solid was separated by filtration. The obtained solid was separated by silica gel chromatography (SiO₂; hexane:toluene = 10:1). In this way, 1.71 g of a product (compound 2f, yield: 88%) was obtained.

Synthesis of compound 2g;

[0201] 1.50 g of the compound 2f was added to 30 mL of a tetrahydrofuran solution containing tetra-n-butylammonium fluoride, and the resulting mixture was heated to 60°C for 1 hour. Then, distilled water was added to the mixture, the mixture was moved to a liquid-separating funnel, and an organic layer was extracted using chloroform. In this way, 0.89 g of a product (compound 2g, yield: 92%) was obtained.

Synthesis of compound 2h;

[0202] In a nitrogen atmosphere, a toluene solution containing 0.80 g of the compound g and 0.073 g of platinum (II) chloride was heated to 90°C for 12 hours. Then, distilled water was added to the mixture, the mixture was moved to a liquid-separating funnel, and an organic layer was extracted using chloroform. The obtained solid was separated by silica gel chromatography (SiO₂; hexane:dichloromethane = 9:1). In this way, 0.32 g of a product (compound 2h, yield: 40%) was obtained.

[0203] The compound 2h in which R represents a n-octyl group was denoted as a compound 2.

[0204] The compounds represented by Formula (1-2) other than the compound 2 were synthesized in the same manner as used for synthesizing the compound 2. That is, through the compound 2g, the compounds 4, 30, 38, 40, and 44 represented by Formula (1-2) were synthesized according to the scheme 2 described above.

[0205] Each of the obtained compounds represented by Formula (1-2) was identified by elementary analysis, NMR, and MASS spectrometry.

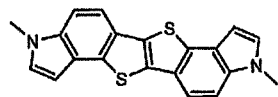
<Synthesis of comparative compounds>

[0206] The structures of comparative compounds 1 to 4 used in the semiconductor active layer (organic semiconductor

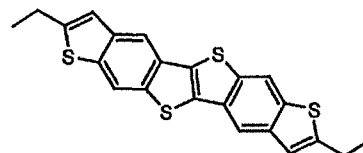
layer) of comparative elements are shown below.

[0207] The comparative compound 3 is Bis-InBTBT (16) described in WO2013/078407A, and the comparative compounds 1 and 3 were synthesized according to the method described in WO2013/078407A.

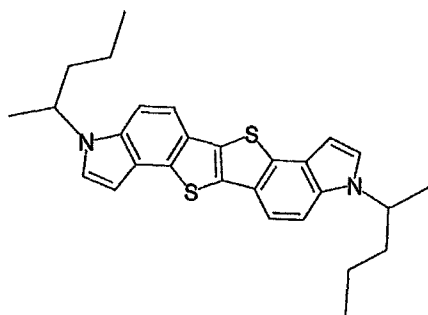
[0208] The comparative compound 4 is a compound 5 used in Example 1 of US2008/0142792A, and the comparative compounds 2 and 4 were synthesized as described in US2008/0142792A.



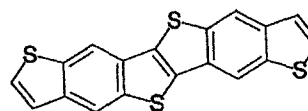
Comparative compound 1



Comparative compound 2



Comparative compound 3



Comparative compound 4

[Example 2]

<Preparation/evaluation of element>

[0209] All of the materials used for preparing elements were purified by sublimation. Through high-performance liquid chromatography (TOSOH CORPORATION, TSKgel ODS-100Z), it was confirmed that the materials had purity (area ratio for absorption intensity at 254 nm) of equal to or higher than 99.5%.

<Formation of semiconductor active layer (organic semiconductor layer) by using compound alone>

[0210] Each of the compounds of the present invention or the comparative compounds (1 mg each) was mixed with toluene (1 mL) and heated to 100°C, thereby obtaining a coating solution for a non-light-emitting organic semiconductor device. In a nitrogen atmosphere, the coating solution was cast onto a substrate for measuring FET characteristics that was heated to 90°C, thereby forming an organic semiconductor film for a non-light-emitting organic semiconductor device. In this way, an organic transistor element of Example 2 for measuring FET characteristics was obtained. As the substrate for measuring FET characteristics, a silicon substrate comprising a bottom gate/bottom contact structure was used which included chromium/gold (gate width W = 100 nm, gate length L = 100 μm) arranged to form a comb pattern as source and drain electrodes and included SiO₂ (film thickness: 200 nm) as an insulating layer (the structure is schematically shown in Fig. 2).

[Evaluation]

[0211] By using a semiconductor parameter analyzer (4156C manufactured by Agilent Technologies) connected to a semi-automatic prober (AX-2000 manufactured by Vector Semiconductor Co., Ltd.), the FET characteristics of the organic transistor element of Example 2 were evaluated under a normal pressure/nitrogen atmosphere, from the viewpoint of the carrier mobility and the threshold voltage shift after repeated driving.

[0212] The obtained results are shown in the following Table 1.

(a) Carrier mobility

[0213] Between the source electrode and the drain electrode of each organic film transistor element (FET element), a voltage of -80 V was applied, and the gate voltage was varied within a range of 20 V to -100 V. In this way, a carrier mobility μ was calculated using the following equation showing a drain current I_d .

$$I_d = (w/2L)\mu C_i(V_g - V_{th})^2$$

[0214] In the equation, L represents a gate length, W represents a gate width, C_i represents a capacity of the insulating layer per unit area, V_g represents a gate voltage, and V_{th} represents a threshold voltage.

[0215] Herein, because the characteristics of the element having a carrier mobility of less than $1 \times 10^{-5} \text{ cm}^2/\text{Vs}$ were too poor, the element was not subjected to the evaluation of (b) threshold voltage shift after repeated driving described below.

(b) Threshold voltage shift after repeated driving

[0216] Between the source electrode and the drain electrode of each organic transistor element (FET element), a voltage of -80 V was applied, and the element was repeatedly driven 100 times by varying the gate voltage within a range of +20 V to -100 V. In this way, the element was measured in the same manner as in the section (a), and a difference between a threshold voltage V_{before} before the repeated driving and a threshold voltage V_{after} after the repeated driving ($|V_{\text{after}} - V_{\text{before}}|$) was evaluated into 3 levels as below. The smaller the difference, the higher the stability of the element against repeated driving. Therefore, the smaller the difference, the more preferable.

A: $|V_{\text{after}} - V_{\text{before}}| \leq 5 \text{ V}$

B: $5 \text{ V} < |V_{\text{after}} - V_{\text{before}}| \leq 10 \text{ V}$

C: $|V_{\text{after}} - V_{\text{before}}| > 10 \text{ V}$

(c) Solubility

[0217] Each of the compounds of the present invention or the comparative examples (20 mg each) was mixed with toluene (1 mL), and the solubility was evaluated into 2 levels as shown below.

A: Completely dissolved.

B: Incompletely dissolved.

[Table 1]

Element No.	Organic semiconductor material	Carrier mobility (cm^2/Vs)	Threshold voltage shift after repeated driving	Solubility	Note
Element 1	Compound 1	0.49	A	A	Present invention
Element 2	Compound 2	0.32	A	A	Present invention
Element 3	Compound 3	0.25	A	A	Present invention
Element 4	Compound 4	0.16	A	A	Present invention
Element 5	Compound 5	7.9×10^{-2}	A	A	Present invention
Element 6	Compound 29	1.5×10^{-2}	A	A	Present invention

(continued)

Element No.	Organic semiconductor material	Carrier mobility (cm ² /Vs)	Threshold voltage shift after repeated driving	Solubility	Note
Element 7	Compound 30	1.5×10^{-2}	A	A	Present invention
Element 8	Compound 37	8.7×10^{-3}	A	A	Present invention
Element 9	Compound 38	5.0×10^{-3}	A	A	Present invention
Element 10	Compound 39	4.4×10^{-3}	A	A	Present invention
Element 11	Compound 40	4.2×10^{-3}	A	A	Present invention
Element 12	Compound 43	4.0×10^{-3}	A	A	Present invention
Element 13	Compound 44	3.8×10^{-3}	A	A	Present invention
Element 14	Compound 51	3.1×10^{-3}	A	A	Present invention
Comparative element 1	Comparative compound 1	4.4×10^{-4}	C	B	Comparative example
Comparative element 2	Comparative compound 2	8.4×10^{-5}	B	B	Comparative example
Comparative element 3	Comparative compound 3	1.2×10^{-6}	C	B	Comparative example
Comparative element 4	Comparative compound 4	4.8×10^{-5}	B	B	Comparative example

[0218] As is evident from the above Table 1, the compound of the present invention exhibits excellent solubility in an organic solvent. Furthermore, it was understood that the organic transistor element using the compound of the present invention has high carrier mobility. Therefore, it was understood that the compound of the present invention can be preferably used as an organic semiconductor material for a non-light-emitting organic semiconductor device.

[0219] In contrast, the organic transistor elements using the comparative compounds 1 to 4 had low carrier mobility.

[0220] Herein, the organic transistor element using the compound of the present invention showed only a slight threshold voltage shift after repeated driving, and the compound of the present invention exhibited high solubility in an organic solvent.

[Example 3]

<Formation of semiconductor active layer (organic semiconductor layer) by using compound and binder together>

[0221] Each of the compounds of the present invention or the comparative compounds (1 mg each) was mixed with 1 mg of P α MS (poly(α -methylstyrene, Mw = 300,000), manufactured by Sigma-Aldrich Co, LLC.) and toluene (1 mL), and the mixture was heated to 100°C, thereby obtaining a coating solution. Organic transistor elements for measuring FET characteristics were prepared and evaluated in the same manner as in Example 2, except that the coating solution obtained as above was used.

[0222] The obtained results are shown in the following Table 2.

[Table 2]

Element No.	Organic semiconductor material	Carrier mobility (cm ² /Vs)	Threshold voltage shift after repeated driving	Note
Element 15	Compound 1	0.63	A	Present invention
Element 16	Compound 2	0.42	A	Present invention
Element 17	Compound 3	0.32	A	Present invention
Element 18	Compound 4	0.25	A	Present invention
Element 19	Compound 5	8.6×10^{-2}	A	Present invention
Element 20	Compound 29	2.5×10^{-2}	A	Present invention
Element 21	Compound 30	2.0×10^{-2}	A	Present invention
Comparative element 5	Comparative compound 1	6.3×10^{-4}	C	Comparative example
Comparative element 6	Comparative compound 2	1.0×10^{-4}	B	Comparative example

[0223] From the above Table 2, it was understood that the organic transistor element including a semiconductor active layer formed using the compound of the present invention with a binder has high carrier mobility. Therefore, it was understood that the compound of the present invention can be preferably used as an organic semiconductor material for a non-light-emitting organic semiconductor device.

[0224] In contrast, the organic transistor element including a semiconductor active layer formed using the comparative compounds 1 and 2 with a binder had low carrier mobility.

[0225] Herein, the organic transistor element using the compound of the present invention showed only a slight threshold voltage shift after repeated driving.

[0226] Each of the organic transistor elements obtained in Example 3 was observed by unaided eyes and an optical microscope. As a result, it was understood that all of the films using P α MS as a binder have extremely high smoothness and uniformity.

[0227] From the above results, it was understood that in a case where the semiconductor active layer for the comparative element is formed using a binder and a comparative compound in combination, the carrier mobility becomes extremely low; however, in a case where the semiconductor active layer for the organic transistor element of the present invention is formed using the compound of the present invention with a binder, excellent carrier mobility is exhibited, and preferably, it is possible to obtain an element which shows only a slight threshold voltage shift after repeated driving and has extremely high smoothness/uniformity of the film.

[Example 4]

<Formation of semiconductor active layer (organic semiconductor layer)>

[0228] The surface of a silicon wafer, which comprised SiO₂ (film thickness: 370 nm) as a gate insulating film, was treated with octyltrichlorosilane.

[0229] Each of the compounds of the present invention or the comparative compounds (1 mg each) was mixed with toluene (1 mL), and the mixture was heated to 100°C, thereby preparing a coating solution for a non-light-emitting organic semiconductor device. In a nitrogen atmosphere, the coating solution was cast onto the silicon wafer which had been heated to 90°C and undergone surface treatment with octylsilane, thereby forming an organic semiconductor film for a non-light-emitting organic semiconductor device.

[0230] Furthermore, gold was deposited onto the surface of the film by using a mask so as to prepare source and drain electrodes, thereby obtaining an organic transistor element having a bottom gate/top contact structure with a gate width W = 5 mm and a gate length L = 80 μ m (the structure is schematically shown in Fig. 1).

[0231] By using a semiconductor parameter analyzer (4156C manufactured by Agilent Technologies) connected to a semi-automatic prober (AX-2000 manufactured by Vector Semiconductor Co., Ltd.), the FET characteristics of the organic transistor element of Example 4 were evaluated in the same manner as in Example 2 under a normal pressure/nitrogen atmosphere.

[0232] The obtained results are shown in the following Table 3.

[Table 3]

Element No.	Organic semiconductor material	Carrier mobility (cm ² /Vs)	Threshold voltage shift after repeated driving	Note
Element 22	Compound 1	0.64	A	Present invention
Element 23	Compound 2	0.44	A	Present invention
Element 24	Compound 5	9.1×10^{-2}	A	Present invention
Element 25	Compound 29	3.3×10^{-2}	A	Present invention
Element 26	Compound 30	2.4×10^{-2}	A	Present invention
Comparative element 7	Comparative compound 1	4.8×10^{-5}	C	Comparative example

[0233] From the above Table 3, it was understood that the organic transistor element using the compound of the present invention has high carrier mobility. Therefore, it was understood that the compound of the present invention can be preferably used as an organic semiconductor material for a non-light-emitting organic semiconductor device.

[0234] In contrast, the organic transistor element using the comparative compound 1 had low carrier mobility.

[0235] Herein, the organic transistor element using the compound of the present invention showed only a slight threshold voltage shift after repeated driving.

Explanation of References

[0236]

11: substrate

12: electrode

13: insulator layer

14: semiconductor active layer (organic substance layer, organic semiconductor layer)

15a, 15b: electrode

31: substrate

32: electrode

33: insulator layer

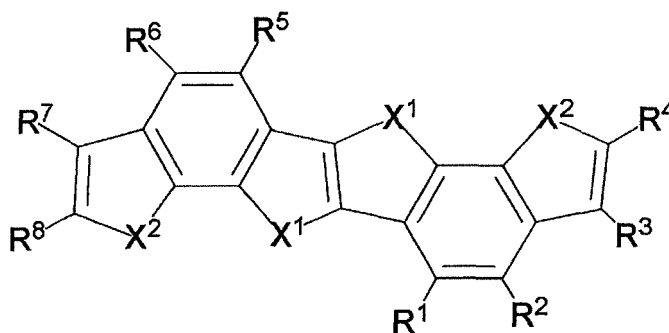
34a, 34b: electrode

35: semiconductor active layer (organic substance layer, organic semiconductor layer)

Claims

1. An organic transistor comprising a compound represented by the following Formula (1-1) or (1-2) in a semiconductor active layer;

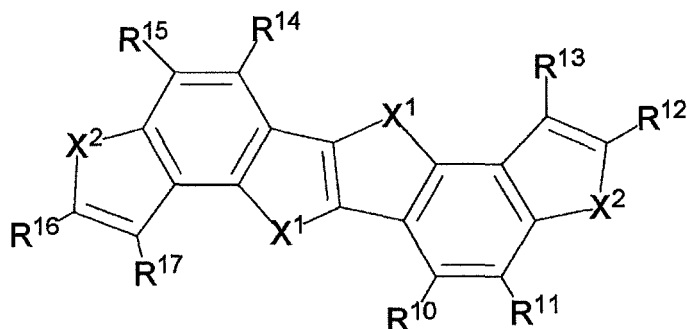
Formula (1-1)



in Formula (1-1),

each X^1 independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR^9 ,
 each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R^1 to R^9 independently represents a hydrogen atom or a substituent, and at least one of R^1 , R^2 , R^3 , R^4 , R^5 , R^6 , R^7 , R^8 , and R^9 is a substituent represented by the following Formula (W);

Formula (1-2)



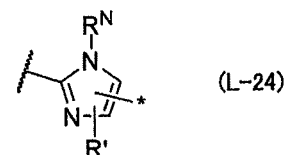
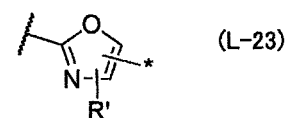
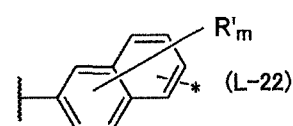
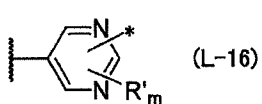
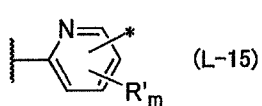
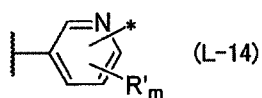
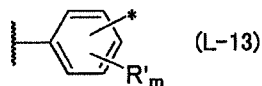
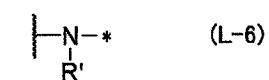
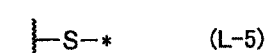
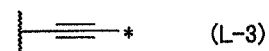
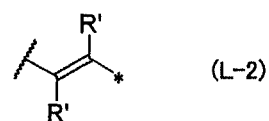
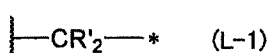
in Formula (1-2),

each X^1 independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR^9 ,
 each X^2 independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R^9 to R^{17} independently represents a hydrogen atom or a substituent, and at least one of R^9 , R^{10} , R^{11} , R^{12} , R^{13} , R^{14} , R^{15} , R^{16} , and R^{17} is a substituent represented by the following Formula (W);

-L-R Formula (W)

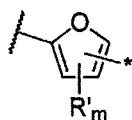
in Formula (W), L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and

R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

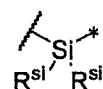




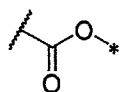
(L-7)



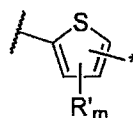
(L-17)



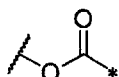
(L-25)



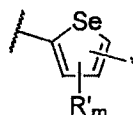
(L-8)



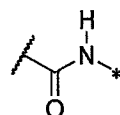
(L-18)



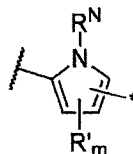
(L-9)



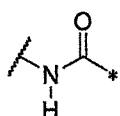
(L-19)



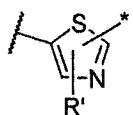
(L-10)



(L-20)



(L-11)



(L-21)



(L-12)

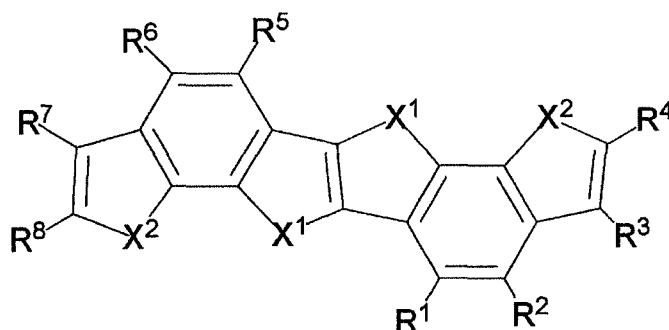
in Formulae (L-1) to (L-25),

the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
 m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6,
 each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent,
 R^N represents a hydrogen atom or a substituent, and
 each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

2. The organic transistor according to claim 1,

wherein the compound represented by the Formula (1-1) is a compound represented by the following Formula (1-1A);

Formula (1-1A)



in Formula (1-1A),

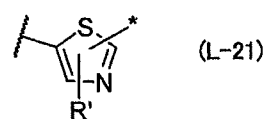
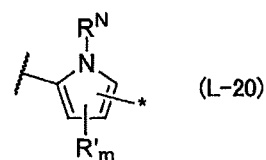
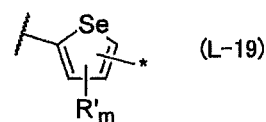
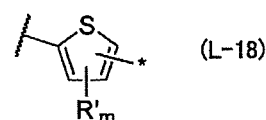
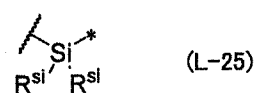
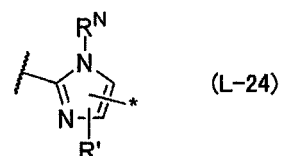
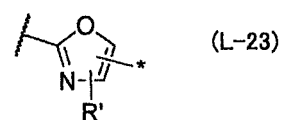
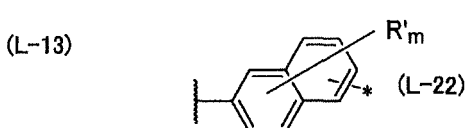
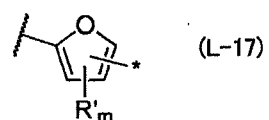
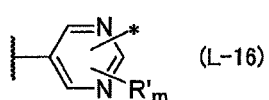
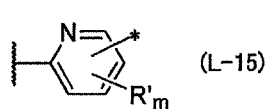
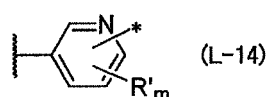
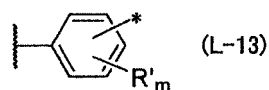
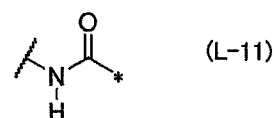
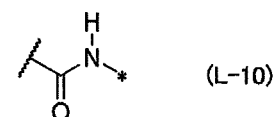
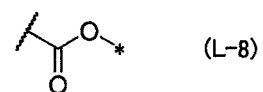
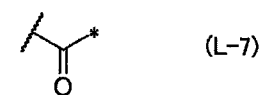
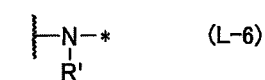
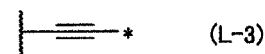
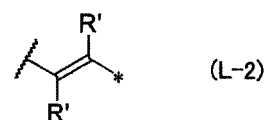
each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,

each of R^1 to R^9 independently represents a hydrogen atom or a substituent, and at least one of R^3 , R^4 , R^7 , and R^8 is a substituent represented by the following Formula (W):

-L-R Formula (W)

in Formula (W),

L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;



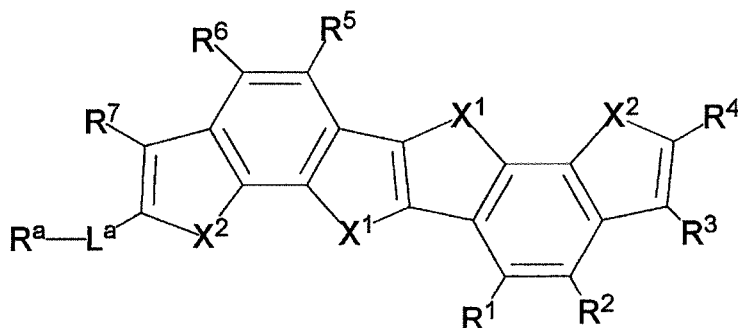
in Formulae (L-1) to (L-25),

the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
 m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to
 (L-20) represents 2, m in Formula (L-22) represents 6,
 each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or
 a substituent,
 R^N represents a hydrogen atom or a substituent, and
 each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

3. The organic transistor according to claim 1 or 2,

wherein the compound represented by the Formula (1-1) or (1-1A) is a compound represented by the following
 Formula (2-1-1) or (2-1-2), and
 the compound represented by the Formula (1-2) is a compound represented by the following Formula (2-2-1)
 or (2-2-2);

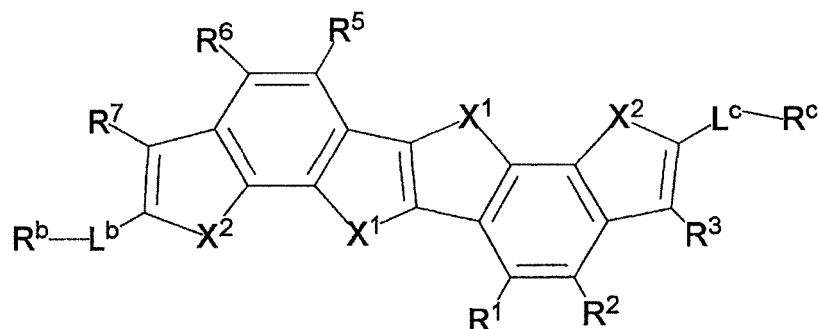
Formula (2-1-1)



in Formula (2-1-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R⁷ and R⁹ independently represents a hydrogen atom or a substituent, R⁴ is not a group
 represented by -L^a-R^a,
 L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a
 divalent linking group in which two or more divalent linking groups represented by any of the following
 Formulae (L-1) to (L-25) are bonded to each other, and
 R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group,
 an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is
 equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or
 a substituted or unsubstituted trialkylsilyl group;

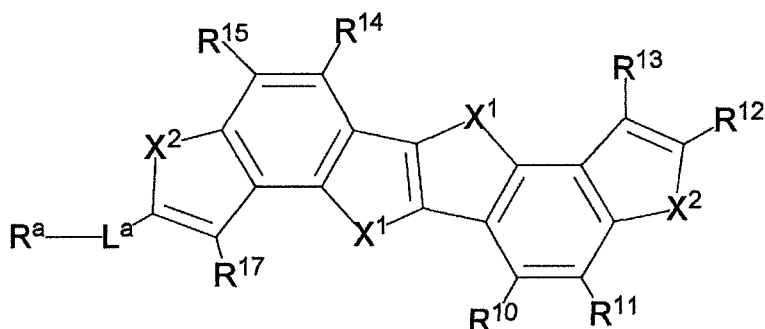
Formula (2-1-2)



in Formula (2-1-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R³, R⁵ to R⁷, and R⁹ independently represents a hydrogen atom or a substituent,
 each of L^b and L^c independently represents a divalent linking group represented by any of the following
 Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented
 by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
 each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a
 vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition
 number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group
 having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

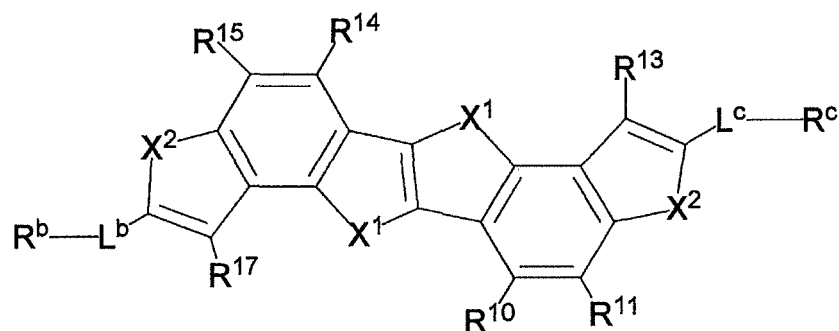
Formula (2-2-1)



in Formula (2-2-1),

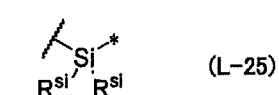
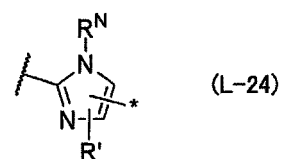
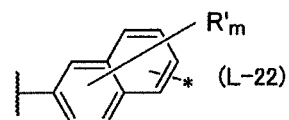
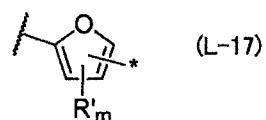
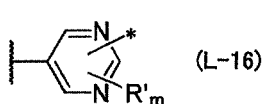
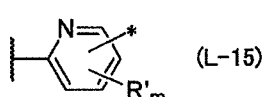
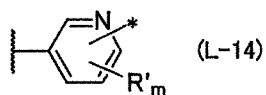
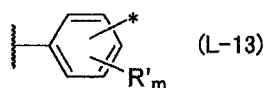
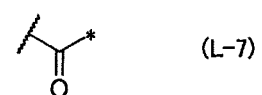
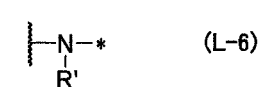
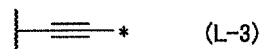
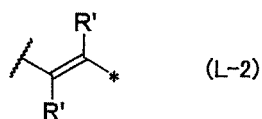
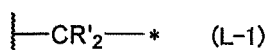
each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹⁰, R¹² to R¹⁵, and R¹⁷ independently represents a hydrogen atom or a substituent, R¹² is not a
 group represented by -L^a-R^a,
 L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a
 divalent linking group in which two or more divalent linking groups represented by any of the following
 Formulae (L-1) to (L-25) are bonded to each other, and
 R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group,
 an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is
 equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or
 a substituted or unsubstituted trialkylsilyl group;

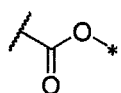
Formula (2-2-2)



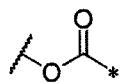
in Formula (2-2-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹⁰, R¹¹, R¹³ to R¹⁵, and R¹⁷ independently represents a hydrogen atom or a substituent,
 each of L^b and L^c independently represents a divalent linking group represented by any of the following
 Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented
 by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
 each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a
 vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition
 number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group
 having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

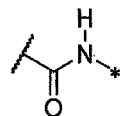




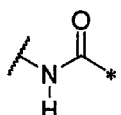
(L-8)



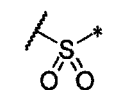
(L-9)



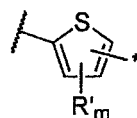
(L-10)



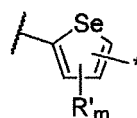
(L-11)



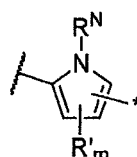
(L-12)



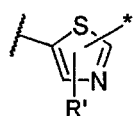
(L-18)



(L-19)



(L-20)



(L-21)

in Formulae (L-1) to (L-25),

the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to
(L-20) represents 2, m in Formula (L-22) represents 6,
each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or
a substituent,

R^N represents a hydrogen atom or a substituent, and

each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

4. The organic transistor according to any one of claims 1 to 3,

wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of L, L^a, L^b, and L^c is
independently a divalent linking group represented by any of the Formulae (L-1) to (L-5), (L-13), (L-17), and (L-
18) or a divalent linking group in which two or more divalent linking groups represented by any of the Formulae
(L-1) to (L-5), (L-13), (L-17), and (L-18) are bonded to each other.

5. The organic transistor according to any one of claims 1 to 4,

wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of L, L^a, L^b, and L^c is
independently a divalent linking group represented by any of the Formulae (L-1), (L-3), (L-13), and (L-18) or a
divalent linking group in which a divalent linking group represented by any of the Formulae (L-3), (L-13), and
(L-18) is bonded to a divalent linking group represented by the Formula (L-1).

6. The organic transistor according to any one of claims 1 to 5,

wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of R, R^a, R^b, and R^c is
independently a substituted or unsubstituted alkyl group.

7. The organic transistor according to any one of claims 1 to 6,

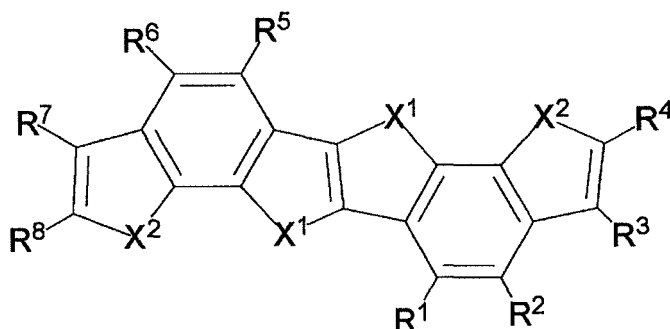
wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of R, R^a, R^b, and R^c is
independently a linear alkyl group.

8. The organic transistor according to any one of claims 1 to 7,

wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), both of X¹ and X² are a sulfur
atom.

9. A compound represented by the following Formula (1-1A) or (1-2);

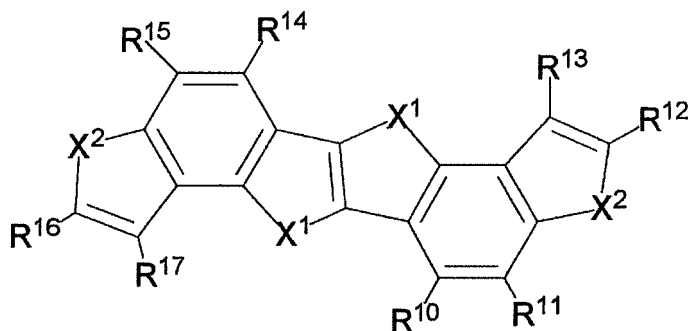
Formula (1-1A)



in Formula (1-1A),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R⁹ independently represents a hydrogen atom or a substituent, and at least one of R³, R⁴, R⁷,
 and R⁸ is a substituent represented by the following Formula (W);

Formula (1-2)

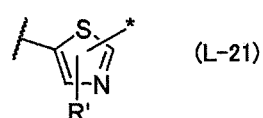
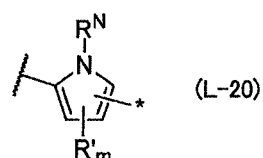
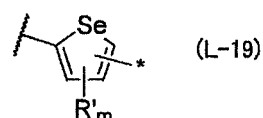
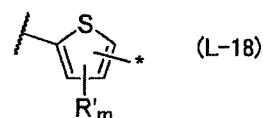
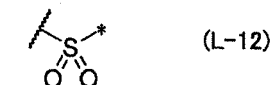
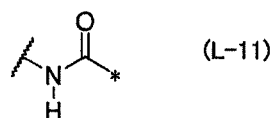
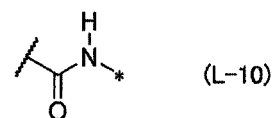
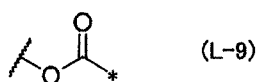
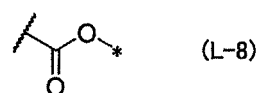
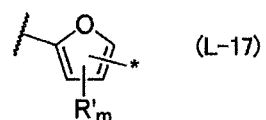
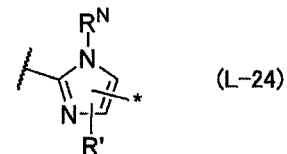
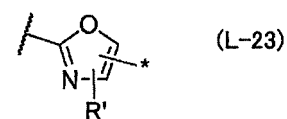
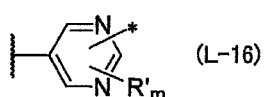
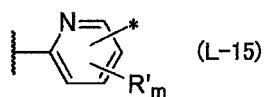
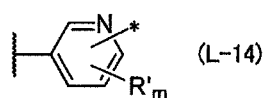
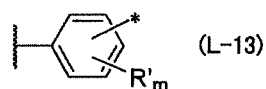
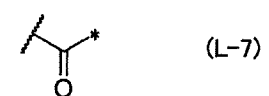
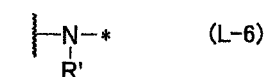
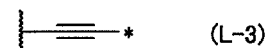
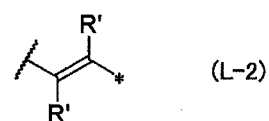
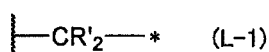


in Formula (1-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R⁹ to R¹⁷ independently represents a hydrogen atom or a substituent, and at least one of R⁹, R¹⁰, R¹¹,
 R¹², R¹³, R¹⁴, R¹⁵, R¹⁶, and R¹⁷ is a substituent represented by the following Formula (W);

-L-R Formula (W)

in Formula (W), L represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
 R represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;



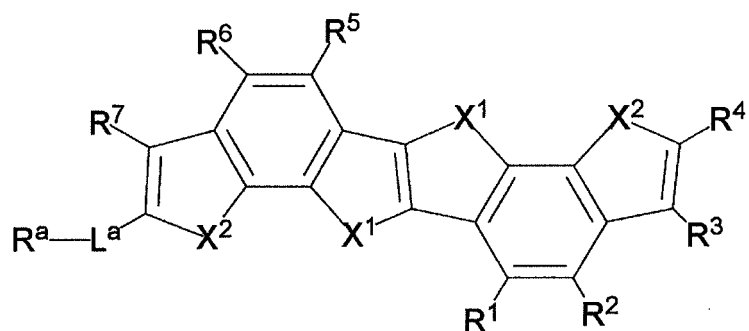
in Formulae (L-1) to (L-25),

the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
 m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to (L-20) represents 2, m in Formula (L-22) represents 6,
 each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or a substituent,
 R^N represents a hydrogen atom or a substituent, and
 each R^{Si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

10. The compound according to claim 9,

wherein the compound represented by the Formula (1-1A) or (1-2) is a compound represented by any of the following Formulae (2-1-1) to (2-2-2);

Formula (2-1-1)



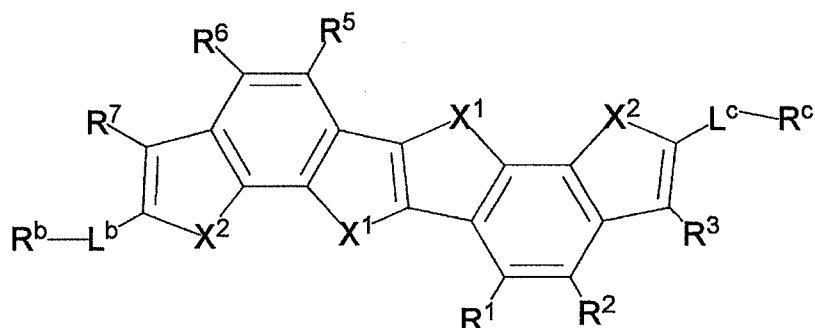
in Formula (2-1-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R⁷ and R⁹ independently represents a hydrogen atom or a substituent, R⁴ is not a group
 represented by -L^a-R^a,

L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a
 divalent linking group in which two or more divalent linking groups represented by any of the following
 Formulae (L-1) to (L-25) are bonded to each other, and

R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group,
 an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is
 equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or
 a substituted or unsubstituted trialkylsilyl group;

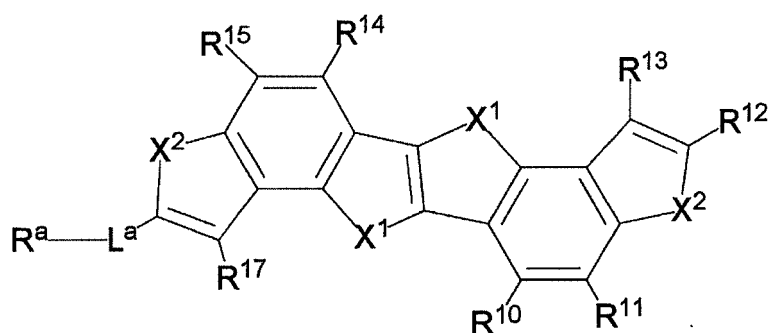
Formula (2-1-2)



in Formula (2-1-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹ to R³, R⁵ to R⁷, and R⁹ independently represents a hydrogen atom or a substituent,
 each of L^b and L^c independently represents a divalent linking group represented by any of the following
 Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented
 by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
 each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a
 vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition
 number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group
 having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;

Formula (2-2-1)



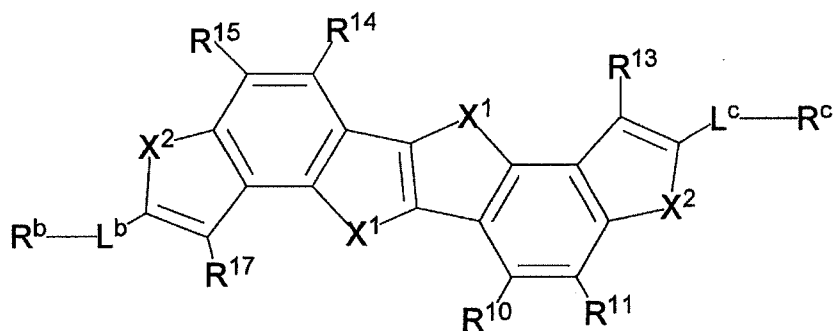
in Formula (2-2-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹⁰, R¹² to R¹⁵, and R¹⁷ independently represents a hydrogen atom or a substituent, R¹² is not a
 group represented by -L^a-R^a,

L^a represents a divalent linking group represented by any of the following Formulae (L-1) to (L-25) or a
 divalent linking group in which two or more divalent linking groups represented by any of the following
 Formulae (L-1) to (L-25) are bonded to each other, and

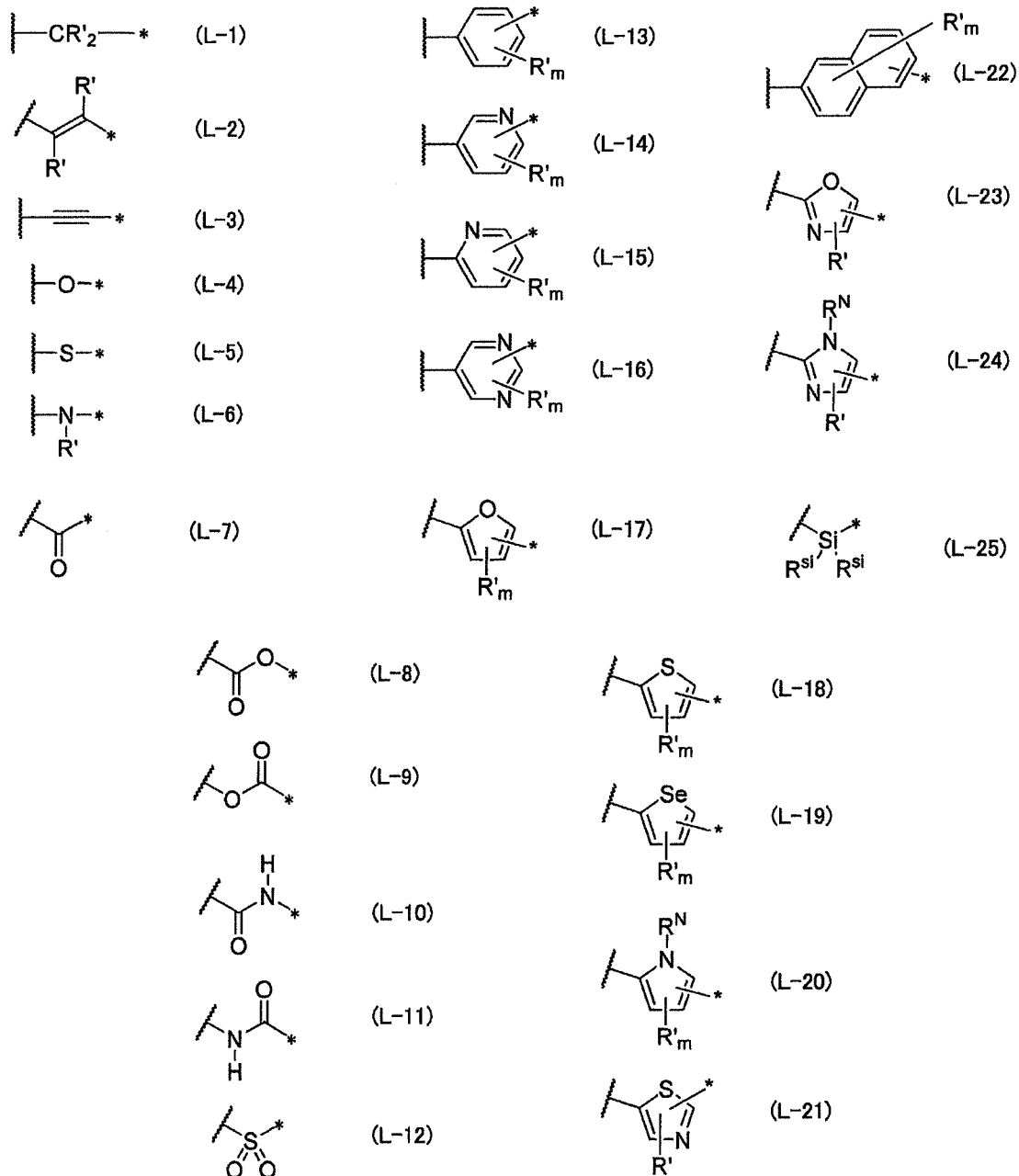
R^a represents a substituted or unsubstituted alkyl group, a cyano group, a vinyl group, an ethynyl group,
 an oxyethylene group, an oligo-oxyethylene group in which a repetition number v of an oxyethylene unit is
 equal to or greater than 2, a siloxane group, an oligosiloxane group having two or more silicon atoms, or
 a substituted or unsubstituted trialkylsilyl group;

Formula (2-2-2)



in Formula (2-2-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R¹⁰, R¹¹, R¹³ to R¹⁵, and R¹⁷ independently represents a hydrogen atom or a substituent,
 each of L^b and L^c independently represents a divalent linking group represented by any of the following
 Formulae (L-1) to (L-25) or a divalent linking group in which two or more divalent linking groups represented
 by any of the following Formulae (L-1) to (L-25) are bonded to each other, and
 each of R^b and R^c independently represents a substituted or unsubstituted alkyl group, a cyano group, a
 vinyl group, an ethynyl group, an oxyethylene group, an oligo-oxyethylene group in which a repetition
 number v of an oxyethylene unit is equal to or greater than 2, a siloxane group, an oligosiloxane group
 having two or more silicon atoms, or a substituted or unsubstituted trialkylsilyl group;



In Formulae (L-1) to (L-25),

the portion of a wavy line represents a position of bonding to a condensed cyclic skeleton,
 m in Formula (L-13) represents 4, m in Formulae (L-14) and (L-15) represents 3, m in Formulae (L-16) to
 (L-20) represents 2, m in Formula (L-22) represents 6,
 each R' in Formulae (L-1), (L-2), (L-6), and (L-13) to (L-24) independently represents a hydrogen atom or
 a substituent,

R^N represents a hydrogen atom or a substituent, and

each R^{si} independently represents a hydrogen atom, an alkyl group, an alkenyl group, or an alkynyl group.

11. The compound according to claim 9 or 10,

wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of L, L^a, L^b, and L^c is
 independently a divalent linking group represented by any of the Formulae (L-1) to (L-5), (L-13), (L-17), and (L-
 18) or a divalent linking group in which two or more divalent linking groups represented by any of the Formulae
 (L-1) to (L-5), (L-13), (L-17), and (L-18) are bonded to each other.

12. The compound according to any one of claims 9 to 11,

wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of L, L^a, L^b, and L^c is a divalent linking group represented by any of the Formulae (L-1), (L-3), (L-13), and (L-18) or a divalent linking group in which a divalent linking group represented by any one of the Formulae (L-3), (L-13), and (L-18) is bonded to a divalent linking group represented by the Formula (L-1).

13. The compound according to any one of claims 9 to 12,

wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of R, R^a, R^b, and R^c is independently a substituted or unsubstituted alkyl group.

14. The compound according to any one of claims 9 to 13,

wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), each of R, R^a, R^b, and R^c is independently a linear alkyl group.

15. The compound according to any one of claims 9 to 14,

wherein in the Formulae (1-1), (1-2), (1-1A), (2-1-1), (2-1-2), (2-2-1), and (2-2-2), both of X¹ and X² are a sulfur atom.

16. An organic semiconductor material for a non-light-emitting organic semiconductor device, comprising the compound represented by the Formula (1-1) or (1-2) according to any one of claims 1 to 8.

17. A material for an organic transistor, comprising the compound represented by the Formula (1-1) or (1-2) according to any one of claims 1 to 8.

18. A coating solution for a non-light-emitting organic semiconductor device, comprising the compound represented by the Formula (1-1) or (1-2) according to any one of claims 1 to 8.

19. A coating solution for a non-light-emitting organic semiconductor device, comprising:

the compound represented by the Formula (1-1) or (1-2) according to any one of claims 1 to 8; and a polymer binder.

20. An organic semiconductor film for a non-light-emitting organic semiconductor device, comprising the compound represented by the Formula (1-1) or (1-2) according to any one of claims 1 to 8.

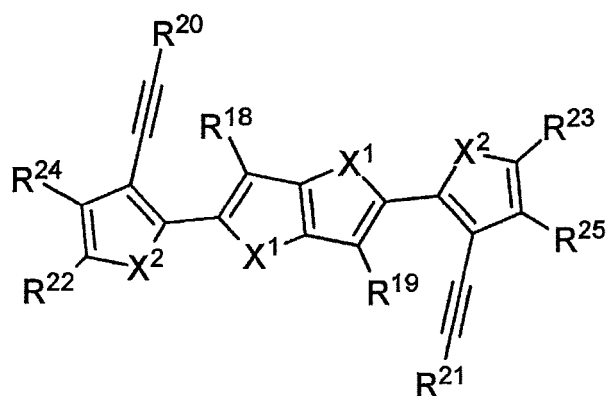
21. An organic semiconductor film for a non-light-emitting organic semiconductor device, comprising:

the compound represented by the Formula (1-1) or (1-2) according to any one of claims 1 to 8; and a polymer binder.

22. The organic semiconductor film for a non-light-emitting organic semiconductor device according to claim 20 or 21 that is prepared by a solution coating method.

23. A compound represented by the following Formula (3-1) or (3-2);

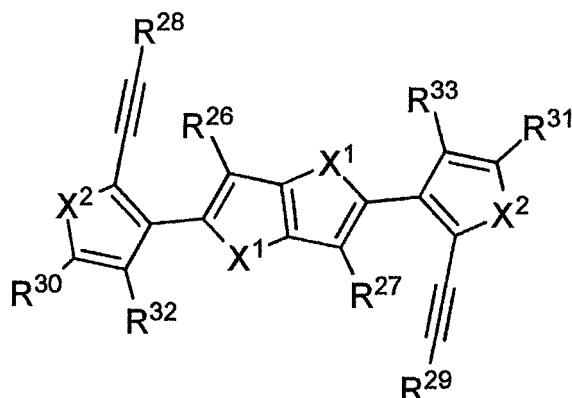
Formula (3-1)



in Formula (3-1),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R⁹ and R¹⁸ to R²⁵ independently represents a hydrogen atom or a substituent, and at least one of R²²
 and R²³ represents an alkyl group, an alkenyl group, an alkynyl group, a substituted or unsubstituted aryl group,
 a substituted or unsubstituted heteroaryl group, an alkylcarbonyl group, or a substituted or unsubstituted aryl-
 carbonyl group;

Formula (3-2)



in Formula (3-2),

each X¹ independently represents a sulfur atom, an oxygen atom, a selenium atom, or NR⁹,
 each X² independently represents a sulfur atom, an oxygen atom, or a selenium atom,
 each of R⁹ and R²⁶ to R³³ independently represents a hydrogen atom or a substituent, and at least one of R³⁰
 and R³¹ represents an alkyl group, an alkenyl group, an alkynyl group, a substituted or unsubstituted aryl group,
 a substituted or unsubstituted heteroaryl group, an alkylcarbonyl group, or a substituted or unsubstituted aryl-
 carbonyl group.

- 24.** The compound according to claim 23 that is an intermediate compound of the compound represented by the Formula (1-1) or (1-2) according to any one of claims 1 to 8.

FIG. 1

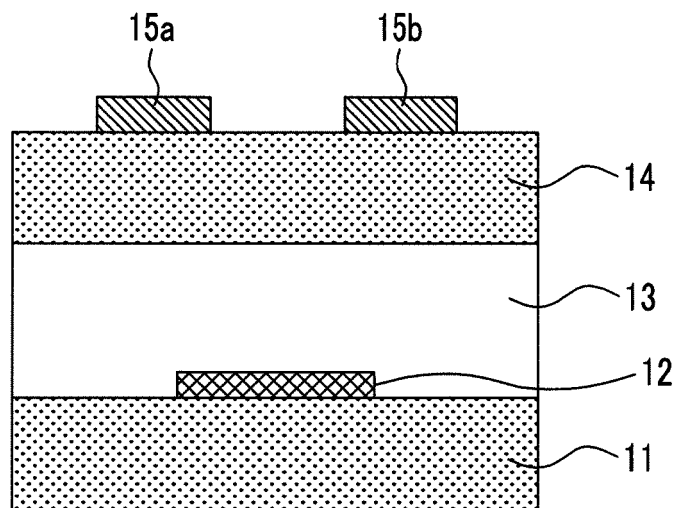


FIG. 2

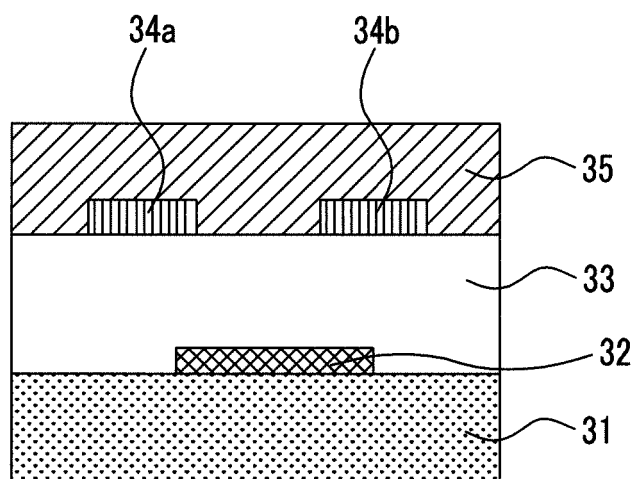
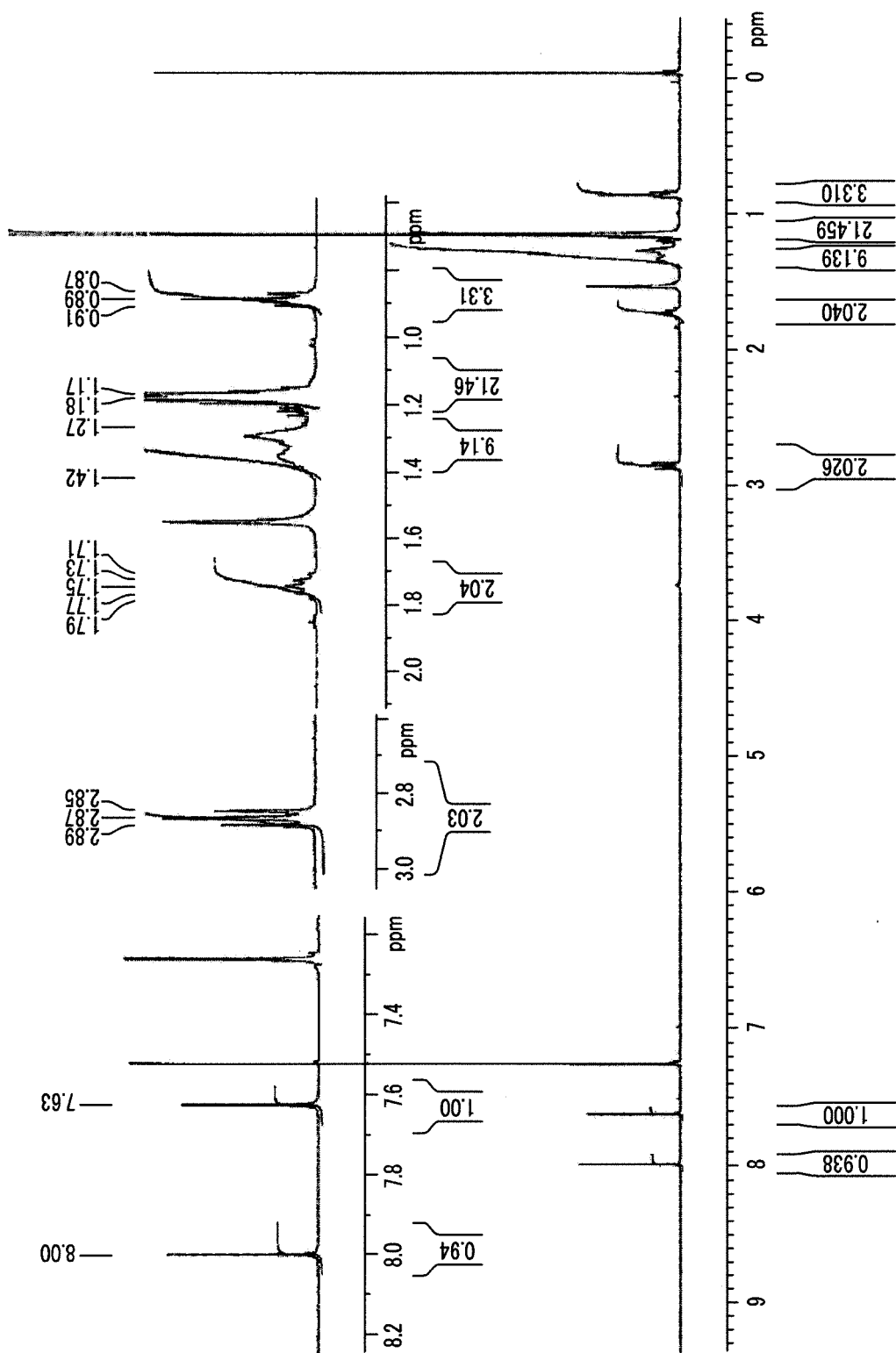
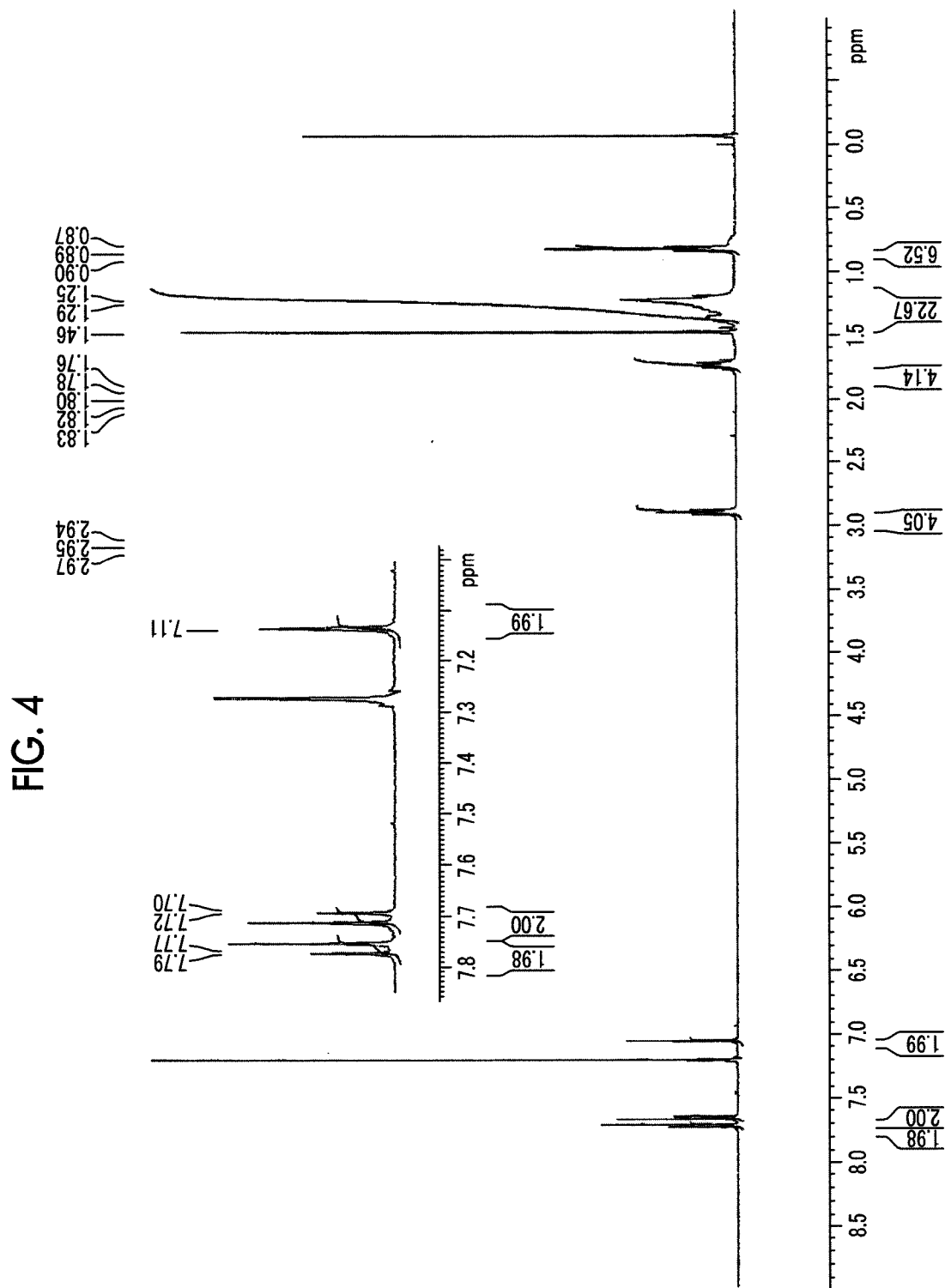


FIG. 3





INTERNATIONAL SEARCH REPORT

International application No.

PCT/JP2015/051488

A. CLASSIFICATION OF SUBJECT MATTER

H01L51/30(2006.01)i, C07D495/04(2006.01)i, C07D495/22(2006.01)i,
H01L21/336
(2006.01)i, H01L29/786(2006.01)i, H01L51/05(2006.01)i,
H01L51/40(2006.01)i,

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

H01L51/30, C07D495/04, C07D495/22, H01L21/336, H01L29/786, H01L51/05,
H01L51/40, C07D493/04, C07D493/22

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Jitsuyo Shinan Koho 1922-1996 Jitsuyo Shinan Toroku Koho 1996-2015
Kokai Jitsuyo Shinan Koho 1971-2015 Toroku Jitsuyo Shinan Koho 1994-2015

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

CAplus/REGISTRY (STN)

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
P, X	WO 2014/087300 A1 (BASF (CHINA) CO.), 12 June 2014 (12.06.2014), page 16, line 4 to page 31, line 18; fig. 1 (Family: none)	1-18, 20, 22-24
X	JP 2013-512975 A (BASF SE), 18 April 2013 (18.04.2013),	1-18, 20, 22-24
Y	claim 1; paragraphs [0050], [0064] to [0088] & US 2012/0289672 A1 & EP 2507286 A & WO 2011/067192 A2 & CN 102639591 A & KR 10-2012-0116427 A	19, 21
X	Laure BINIEK, "New Fused Bis- Thienobenzothienothiophene Copolymers and Their Use in Organic Solar Cells and Transistors", Macromolecules, Vol. 46, Issue 3, American Chemical Society, 2013.01.31, pp. 727-735	9, 11-15

☒ Further documents are listed in the continuation of Box C.☐ See patent family annex.

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Date of the actual completion of the international search
13 February 2015 (13.02.15)Date of mailing of the international search report
03 March 2015 (03.03.15)Name and mailing address of the ISA/
Japan Patent Office
3-4-3, Kasumigaseki, Chiyoda-ku,
Tokyo 100-8915, Japan

Authorized officer

Telephone No.

INTERNATIONAL SEARCH REPORT

International application No.

PCT/JP2015/051488

C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	Ralph RIEGER et al., "Tetrathiahexacene as Building Block for Solution-Processable Semiconducting Polymers: Exploring the Monomer Size Limit", <i>Macromolecules</i> , Vol. 43, Issue 15, American Chemical Society, 2010.07.14, pp. 6264-6267	9, 11-15, 23
Y	JP 2013-087118 A (Xerox Corp.), 13 May 2013 (13.05.2013), paragraphs [0046] to [0055] & US 8372312 B1 & CN 103044445 A & KR 10-2013-0041750 A	19, 21
A	WO 2013/078407 A1 (POLYELA CORP.), 30 May 2013 (30.05.2013), entire text; all drawings & US 2013/0146851 A1 & CN 104126235 A & JP 2015-502937 A	1-24

Form PCT/ISA/210 (continuation of second sheet) (July 2009)

REFERENCES CITED IN THE DESCRIPTION

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Patent documents cited in the description

- WO 2013078407 A [0003] [0005] [0006] [0016] [0207]
- US 20080142792 A1 [0004] [0005] [0006] [0017]
- US 20080142792 A [0208]

Non-patent literature cited in the description

- *Macromolecules*, 2010, vol. 43, 6264-6267 [0105]
- *J. Am. Chem. Soc.*, 2012, vol. 134, 16548-16550 [0105]

专利名称(译)	用于非发光有机半导体器件的有机晶体管，化合物，有机半导体材料，用于有机晶体管的材料，用于非发光有机半导体器件的涂覆溶液，以及用于非发光有机半导体器件的有机半导体膜		
公开(公告)号	EP3101704A4	公开(公告)日	2017-02-08
申请号	EP2015740592	申请日	2015-01-21
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IPC分类号	H01L51/30 C07D495/04 C07D495/22 H01L21/336 H01L29/786 H01L51/05 H01L51/40 C07D493/04 C07D493/22 H01L51/54 H01L51/46		
CPC分类号	C07D491/22 C07D493/22 C07D495/04 C07D495/22 H01L51/0003 H01L51/0065 H01L51/0068 H01L51/0071 H01L51/0072 H01L51/0073 H01L51/0074 H01L51/0545 H01L51/0558 H01L51/0566 C09D5/24		
优先权	2014012058 2014-01-27 JP		
其他公开文献	EP3101704A1 EP3101704B1		
外部链接	Espacenet		

摘要(译)

本发明提供一种具有高载流子迁移率的有机晶体管，其在半导体有源层中含有由式 (1-1) 或 (1-2) 表示的化合物;化合物;用于非发光有机半导体器件的有机半导体材料;有机晶体管的材料;用于非发光有机半导体器件的涂层溶液;用于非发光有机半导体器件的有机半导体膜 (X 1代表S，O，Se或NR 9; X 2代表S，O或Se; R 1至R 9各自代表氢原子或取代基; R 1，R 2，R 3，R 4 R 5，R 6，R 7，R 8和R 9中的至少一个表示-LR; R 9至R 17中的每一个表示氢原子或取代基; R 9 R 10，R 11，R 12，R 13，R 14，R 15，R 16和R 17中的至少一个表示-LR; L表示特定的二价连接基团;并且R表示烷基基团，氰基，乙烯基，乙炔基，氧乙烯基，低聚氧乙烯基，硅氧烷基，低聚硅氧烷基或三烷基甲硅烷基。